RL78/I1D

RENESAS MCU

R01DS0244EJ0240
Rev. 2.40
Mar 20, 2023

True low-power platform (58.3 μA/MHz, and 0.64 μA for operation with only RTC2 and LVD) for the general-purpose applications, with 1.6-V to 3.6-V operation, 8- to 32-Kbyte code flash memory, and 33 DMIPS at 24 MHz

1. OUTLINE

1.1 Features

Ultra-low power consumption technology

- V_{DD} = 1.6 V to 3.6 V
- HALT mode
- STOP mode
- SNOOZE mode

RL78 CPU core

- CISC architecture with 3-stage pipeline
- Minimum instruction execution time: Can be changed from high speed (0.04167 μs: @ 24 MHz operation with high-speed on-chip oscillator) to ultra-low speed (66.6 μs: @ 15 kHz operation with low-speed on-chip oscillator clock)
- Multiply/divide/multiply & accumulate instructions are supported.
- Address space: 1 MB
- General-purpose registers: (8-bit register × 8) × 4 banks
- On-chip RAM: 0.7 to 3 KB

Code flash memory

- Code flash memory: 8 to 32 KB
- Block size: 1 KB
- Prohibition of block erase and rewriting (security function)
- On-chip debug function
- Self-programming (with boot swap function/flash shield window function)

Data flash memory

- Data flash memory: 2 KB
- Back ground operation (BGO): Instructions can be executed from the program memory while rewriting the data flash memory.
- Number of rewrites: 1,000,000 times (TYP.)
- Voltage of rewrites: V_{DD} = 1.8 to 3.6 V

High-speed on-chip oscillator

- Select from 24 MHz, 16 MHz, 12 MHz, 8 MHz, 6 MHz, 4 MHz, 3 MHz, 2 MHz, and 1 MHz
- High accuracy: ±1.0% (V_{DD} = 1.8 to 3.6 V, T_A = -20 to +85°C)

Middle-speed on-chip oscillator

- Selectable from 4 MHz, 2 MHz, and 1 MHz.

Operating ambient temperature

- T_A = -40 to +105°C (G: Industrial applications)

Power management and reset function

- On-chip power-on-reset (POR) circuit
- On-chip voltage detector (LVD) (Select interrupt and reset from 12 levels)

Data transfer controller (DTC)

- Transfer modes: Normal transfer mode, repeat transfer mode, block transfer mode
- Activation sources: Activated by interrupt sources.
- Chain transfer function

Event link controller (ELC)

- Event signals of 20 types can be linked to the specified peripheral function.

Serial interfaces

- Simplified SPI (CSI[Note]): 1 or 2 channels
- UART: 1 channel
- I^2C/simplified I^2C: 1 or 2 channels

Timers

- 16-bit timer: 4 channels
- 12-bit interval timer: 1 channel
- 8-bit interval timer: 4 channels
- Real-time clock: 1 channel (calendar for 99 years, alarm function, and clock correction function)
- Watchdog timer: 1 channel

A/D converter

- 8/12-bit resolution A/D converter (V_{DD} = 1.6 to 3.6 V)
- Analog input: 6 to 17 channels
- Internal reference voltage (1.45 V) and temperature sensor

Comparator

- 2 channels
- Operating modes: Comparator high-speed mode, comparator low-speed mode, window mode

Operational amplifier

- 4 channels

I/O ports

- I/O port: 14 to 42 (N-ch open drain I/O [withstand voltage of 6 V]: 4, N-ch open drain I/O [V_{DD} withstand voltage]: 3 to 7)
- Can be set to N-ch open drain, TTL input buffer, and on-chip pull-up resistor
- Different potential interface: Can connect to a 1.8/2.5 V device
- On-chip key interrupt function
- On-chip clock output/buzzer output controller

Others

- On-chip BCD (binary-coded decimal) correction circuit
- On-chip data operation circuit

(**Note** and **Remark** are listed on the next page.)

<R> **Note** Although the CSI function is generally called SPI, it is also called CSI in this product, so it is referred to as such in this manual.

Remark The functions mounted depend on the product. See **1.6 Outline of Functions**.

○ ROM, RAM capacities

Flash ROM	Data flash	RAM	RL78/I1D				
			20 pins	24 pins	30 pins	32 pins	48 pins
32 KB	2 KB	3 KB Note	—	—	R5F117AC	R5F117BC	R5F117GC
16 KB	2 KB	2 KB	R5F1176A	R5F1177A	R5F117AA	R5F117BA	R5F117GA
8 KB	2 KB	0.7 KB	R5F11768	R5F11778	R5F117A8	—	—

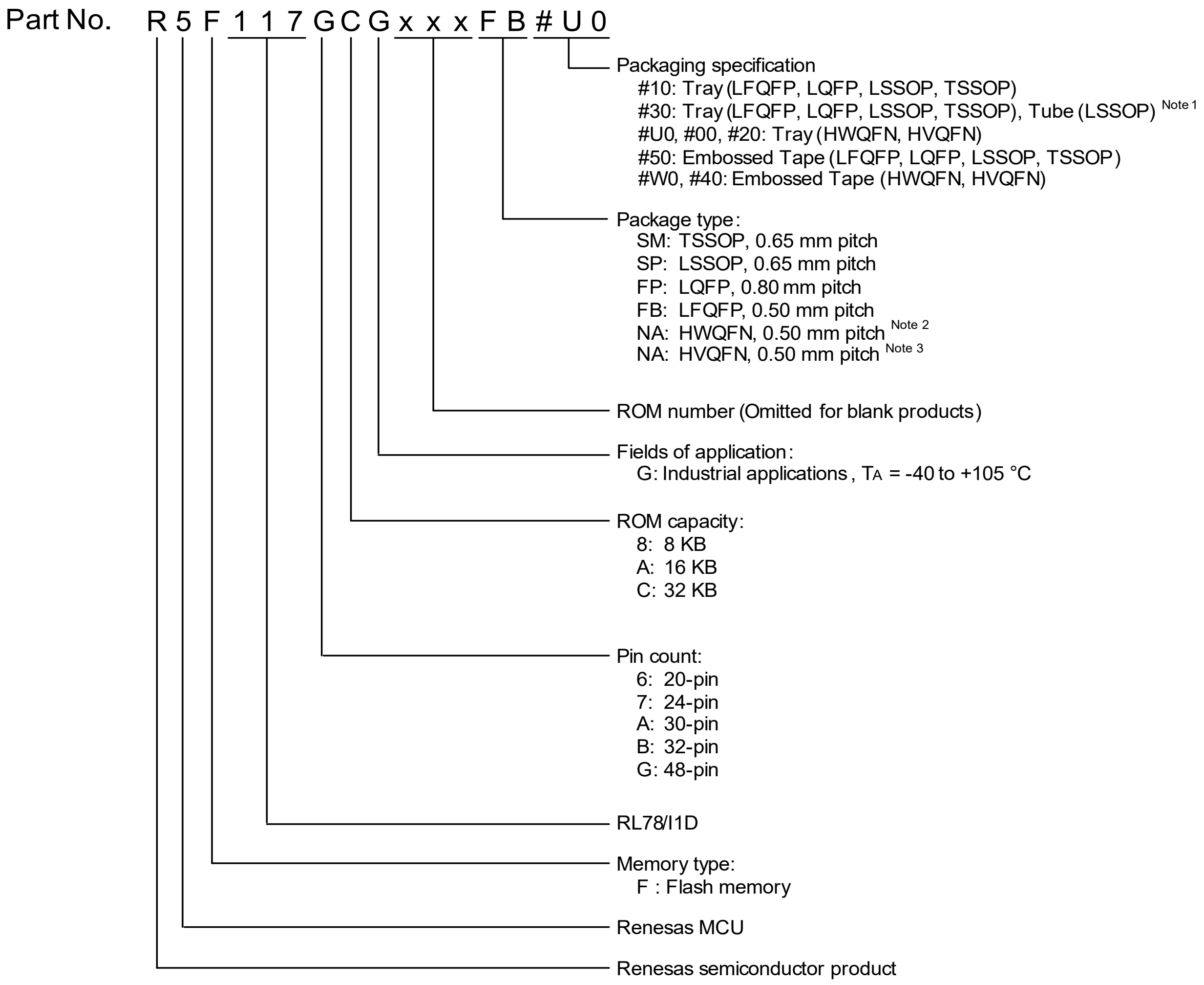
Note The flash library uses RAM in self-programming and rewriting of the data flash memory.
The target products and start address of the RAM areas used by the flash library are shown below.

R5F117xC (x = A, B, G): Start address FF300H

For the RAM areas used by the flash library, see **Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944)**.

1.2 Ordering Information

Figure 1 - 1 Part Number, Memory Size, and Package of RL78/I1D



Part No. R5F117GCGxxxFB#U0

Packaging specification
- #10: Tray (LFQFP, LQFP, LSSOP, TSSOP)
- #30: Tray (LFQFP, LQFP, LSSOP, TSSOP), Tube (LSSOP) Note 1
- #U0, #00, #20: Tray (HWQFN, HVQFN)
- #50: Embossed Tape (LFQFP, LQFP, LSSOP, TSSOP)
- #W0, #40: Embossed Tape (HWQFN, HVQFN)

Package type:
- SM: TSSOP, 0.65 mm pitch
- SP: LSSOP, 0.65 mm pitch
- FP: LQFP, 0.80 mm pitch
- FB: LFQFP, 0.50 mm pitch
- NA: HWQFN, 0.50 mm pitch Note 2
- NA: HVQFN, 0.50 mm pitch Note 3

ROM number (Omitted for blank products)

Fields of application:
- G: Industrial applications, T_A = -40 to +105 °C

ROM capacity:
- 8: 8 KB
- A: 16 KB
- C: 32 KB

Pin count:
- 6: 20-pin
- 7: 24-pin
- A: 30-pin
- B: 32-pin
- G: 48-pin

RL78/I1D

Memory type:
- F : Flash memory

Renesas MCU

Renesas semiconductor product

Note 1. The packaging specification is only “Tube” for products in the 20-pin LSSOP.

Note 2. 24-pin products

Note 3. 32-pin products

<R>

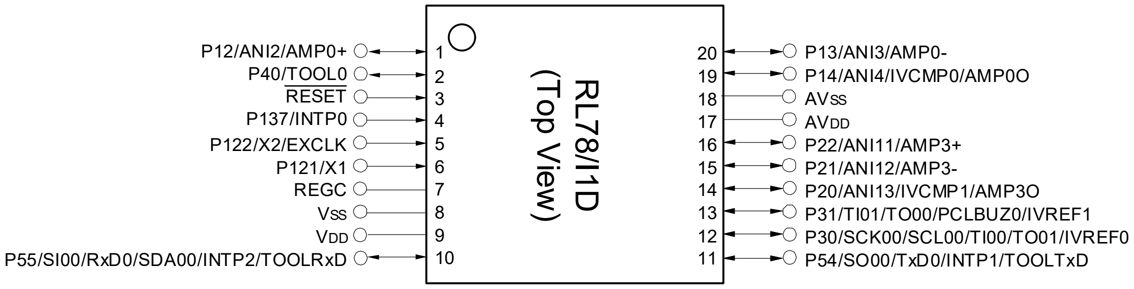
Pin count	Package	Ordering Part Number	RENESAS Code
20 pins	20-pin plastic LSSOP (4.4 × 6.5 mm, 0.65 mm pitch)	R5F11768GSP#30, R5F1176AGSP#30, R5F11768GSP#50, R5F1176AGSP#50	PLSP0020JB-A
	20-pin plastic TSSOP (4.4 × 6.5 mm, 0.65 mm pitch)	R5F11768GSM#10, R5F1176AGSM#10, R5F11768GSM#30, R5F1176AGSM#30, R5F11768GSM#50, R5F1176AGSM#50	PTSP0020JI-A
24 pins	24-pin plastic HWQFN (4 × 4 mm, 0.5 mm pitch)	R5F11778GNA#U0, R5F1177AGNA#U0, R5F11778GNA#W0, R5F1177AGNA#W0	PWQN0024KE-A
		R5F11778GNA#00, R5F1177AGNA#00, R5F11778GNA#20, R5F1177AGNA#20, R5F11778GNA#40, R5F1177AGNA#40	PWQN0024KF-A PWQN0024KH-A
30 pins	30-pin plastic LSSOP (7.62 mm (300), 0.65 mm pitch)	R5F117A8GSP#10, R5F117AAGSP#10, R5F117ACGSP#10, R5F117A8GSP#30, R5F117AAGSP#30, R5F117ACGSP#30, R5F117A8GSP#50, R5F117AAGSP#50, R5F117ACGSP#50	PLSP0030JB-B
32 pins	32-pin plastic HVQFN (5 × 5 mm, 0.5 mm pitch)	R5F117BAGNA#00, R5F117BCGNA#00, R5F117BAGNA#20, R5F117BCGNA#20, R5F117BAGNA#40, R5F117BCGNA#40	PVQN0032KE-A
	32-pin plastic LQFP (7 × 7 mm, 0.8 mm pitch)	R5F117BAGFP#10, R5F117BCGFP#10, R5F117BAGFP#30, R5F117BCGFP#30, R5F117BAGFP#50, R5F117BCGFP#50	PLQP0032GB-A
48 pins	48-pin plastic LFQFP (7 × 7 mm, 0.5 mm pitch)	R5F117GAGFB#10, R5F117GCGFB#10, R5F117GAGFB#30, R5F117GCGFB#30, R5F117GAGFB#50, R5F117GCGFB#50	PLQP0048KB-A

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

1.3 Pin Configuration (Top View)

1.3.1 20-pin products

- 20-pin plastic LSSOP (4.4 × 6.5 mm, 0.65 mm pitch)
- 20-pin plastic TSSOP (4.4 × 6.5 mm, 0.65 mm pitch)



Caution 1. Connect the REGC pin to Vss pin via a capacitor (0.47 to 1 μF).

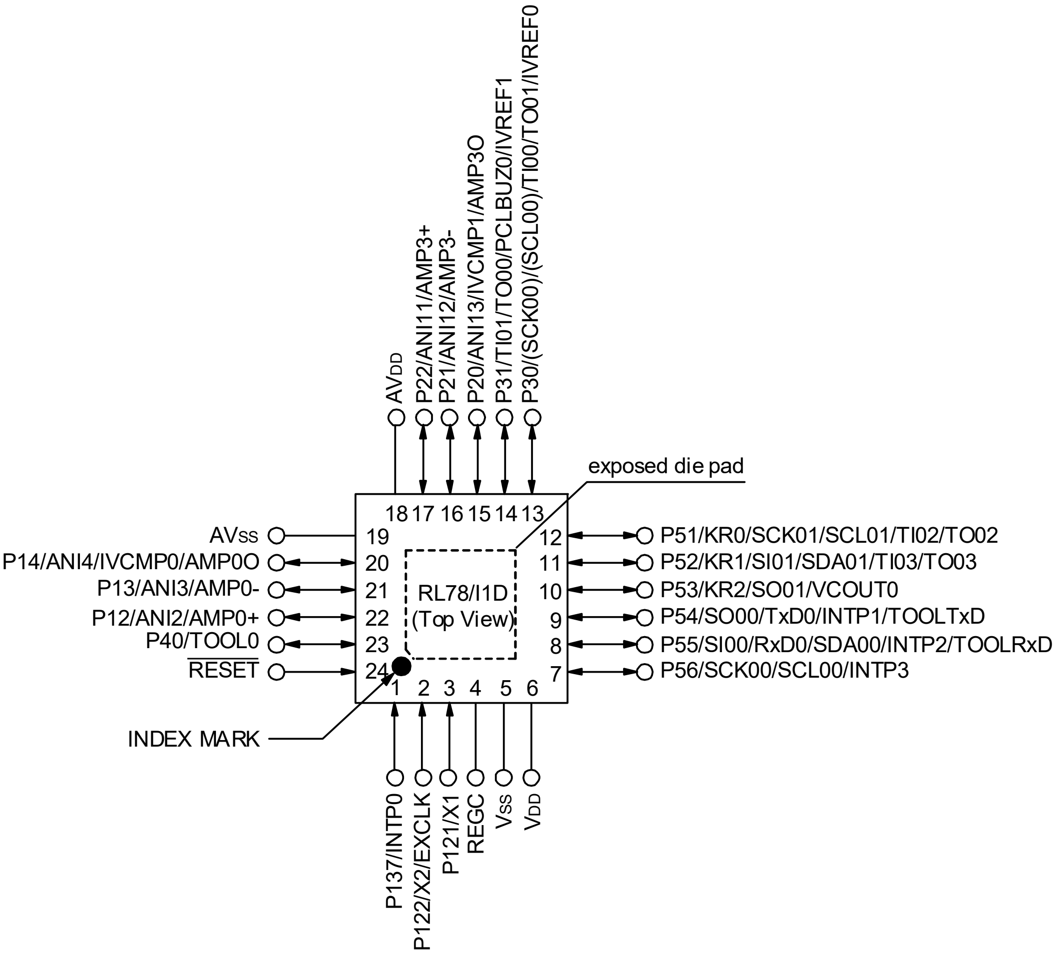
Caution 2. Make AVss pin the same potential as Vss pin.

Caution 3. Make AVDD pin the same potential as VDD pin.

Remark For pin identification, see **1.4 Pin Identification**.

1.3.2 24-pin products

- 24-pin plastic HWQFN (4 × 4 mm, 0.5 mm pitch)



Caution 1. Connect the REGC pin to VSS pin via a capacitor (0.47 to 1 μF).

Caution 2. Make AVSS pin the same potential as VSS pin.

Caution 3. Make AVDD pin the same potential as VDD pin.

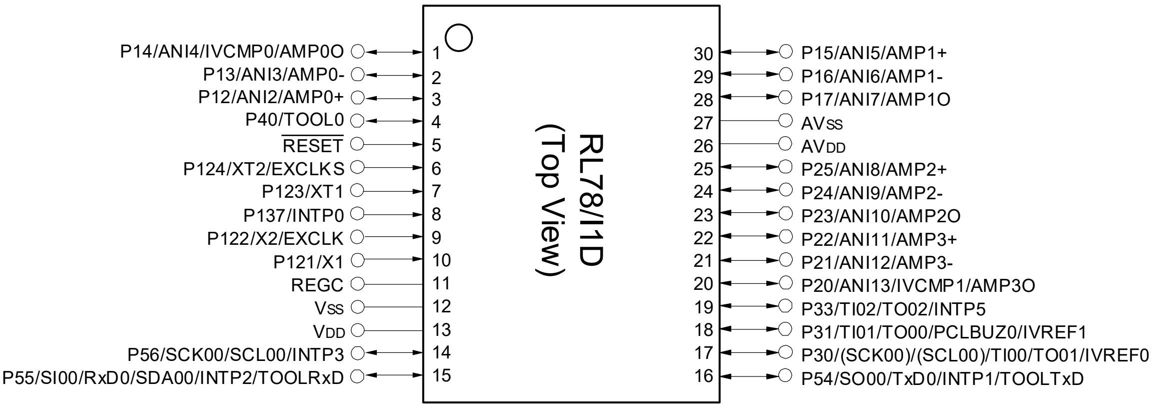
Remark 1. For pin identification, see **1.4 Pin Identification**.

Remark 2. It is recommended to connect an exposed die pad to VSS.

Remark 3. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register 0 (PIOR0).

1.3.3 30-pin products

- 30-pin plastic LSSOP (7.62 mm (300), 0.65 mm pitch)



Caution 1. Connect the REGC pin to VSS pin via a capacitor (0.47 to 1 μF).

Caution 2. Make AVSS pin the same potential as VSS pin.

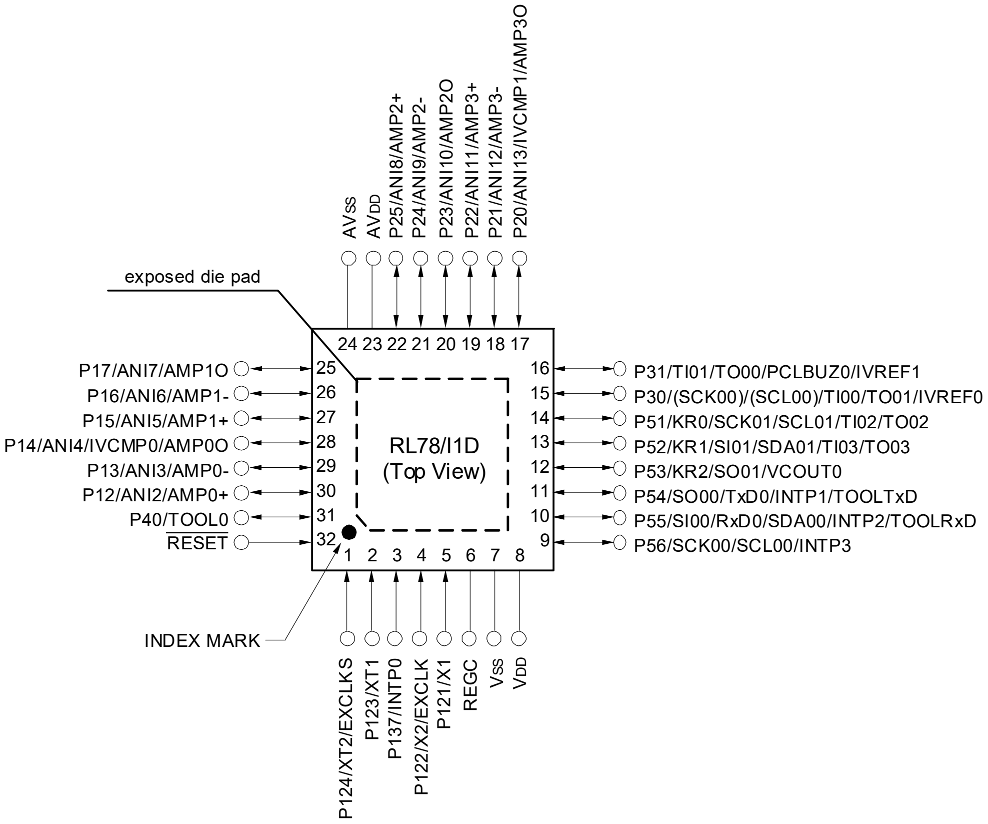
Caution 3. Make AVDD pin the same potential as VDD pin.

Remark 1. For pin identification, see **1.4 Pin Identification**.

Remark 2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register 0 (PIOR0).

1.3.4 32-pin products

- 32-pin plastic HVQFN (5 × 5 mm, 0.5 mm pitch)



Caution 1. Connect the REGC pin to Vss pin via a capacitor (0.47 to 1 μF).

Caution 2. Make AVss pin the same potential as Vss pin.

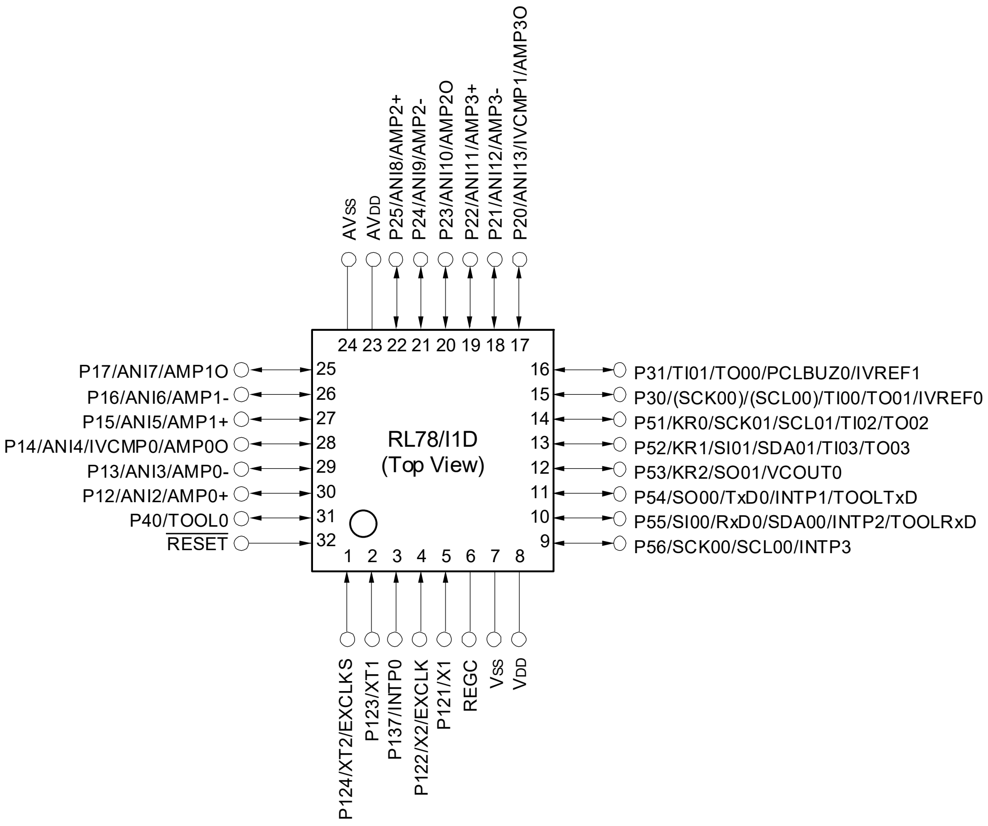
Caution 3. Make AVDD pin the same potential as VDD pin.

Remark 1. For pin identification, see **1.4 Pin Identification**.

Remark 2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register 0 (PIOR0).

Remark 3. It is recommended to connect an exposed die pad to Vss.

- 32-pin plastic LQFP (7 × 7 mm, 0.8 mm pitch)



Caution 1. Connect the REGC pin to VSS pin via a capacitor (0.47 to 1 μF).

Caution 2. Make AVSS pin the same potential as VSS pin.

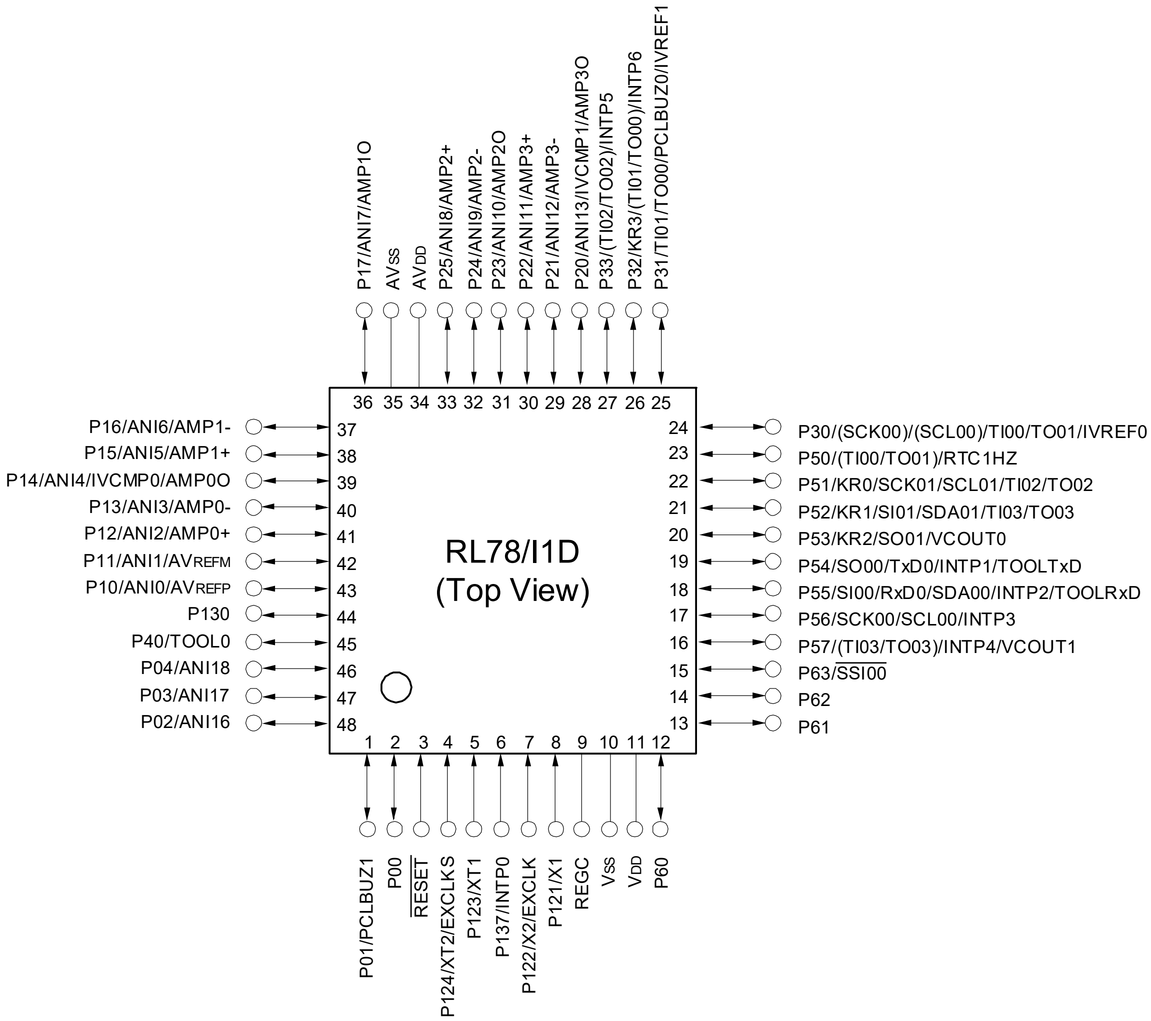
Caution 3. Make AVDD pin the same potential as VDD pin.

Remark 1. For pin identification, see **1.4 Pin Identification**.

Remark 2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register 0 (PIOR0).

1.3.5 48-pin products

- 48-pin plastic LFQFP (7 × 7 mm, 0.5 mm pitch)



Caution 1. Connect the REGC pin to Vss pin via a capacitor (0.47 to 1 μF).

Caution 2. Make AVss pin the same potential as Vss pin.

Caution 3. Make AVDD pin the same potential as VDD pin.

Remark 1. For pin identification, see **1.4 Pin Identification**.

Remark 2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register 0 (PIOR0).

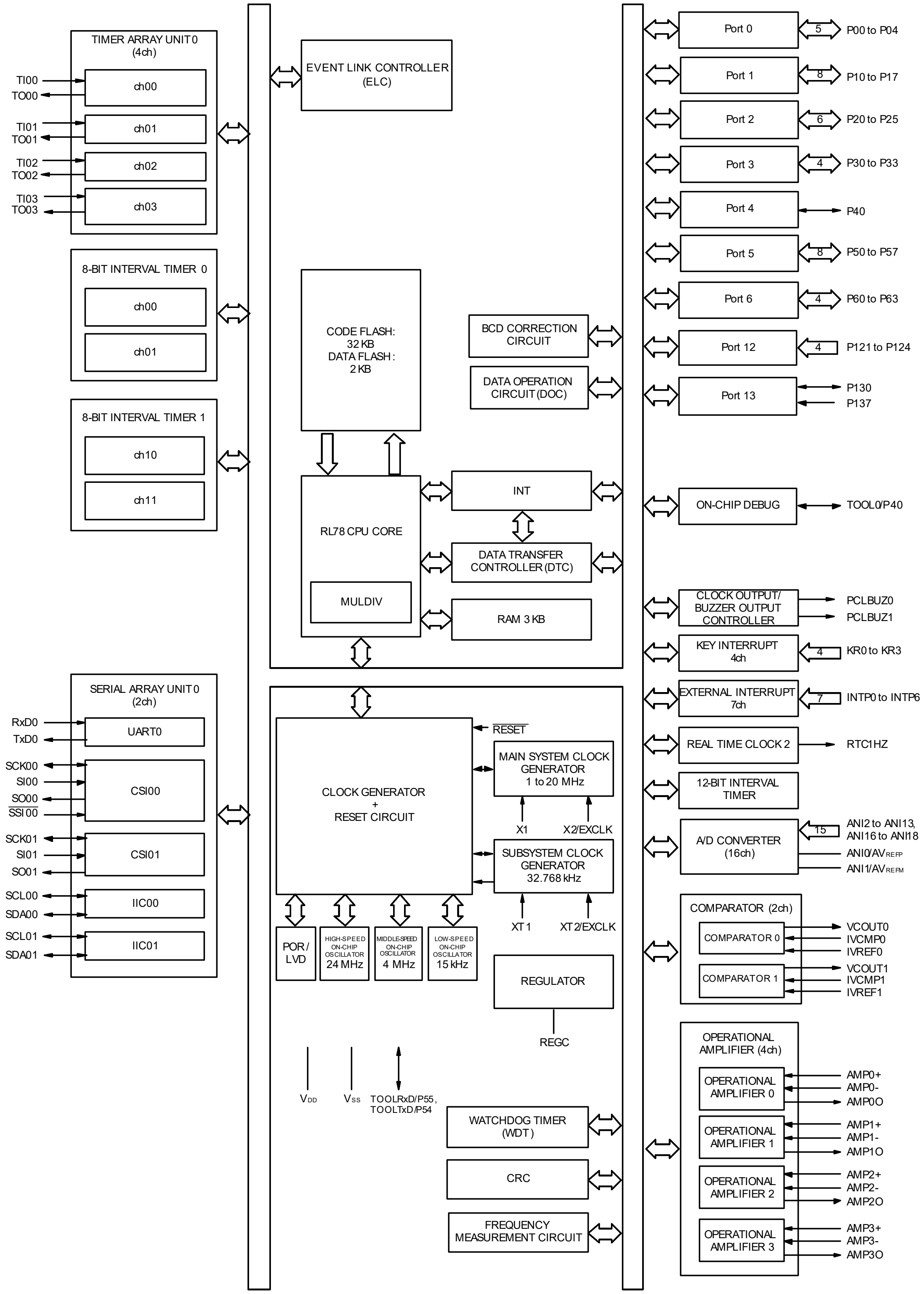
1.4 Pin Identification

ANI0 to ANI13, ANI16 to ANI18 : Analog input
AV_{DD} : Analog power supply
AV_{REFM} : A/D converter reference potential (- side) input
AV_{REFP} : A/D converter reference potential (+ side) input
AV_{SS} : Analog ground
EXCLK : External clock input (main system clock)
EXCLKS : External clock input (subsystem clock)
INTP0 to INTP6 : External interrupt input
IVCMP0, IVCMP1 : Comparator input
IVREF0, IVREF1 : Comparator reference input
KR0 to KR3 : Key return
P00 to P04 : Port 0
P10 to P17 : Port 1
P20 to P25 : Port 2
P30 to P33 : Port 3
P40 : Port 4
P50 to P57 : Port 5
P60 to P63 : Port 6
P121 to P124 : Port 12
P130, P137 : Port 13

PCLBUZ0, PCLBUZ1 : Programmable clock output/buzzer output
REGC : Regulator capacitance
$\overline{\text{RESET}}$: Reset
RTC1HZ : Real-time clock correction clock (1 Hz) output
RxD0 : Receive data
SCK00, SCK01 : Serial clock input/output
SCL00, SCL01 : Serial clock input/output
SDA00, SDA01 : Serial data input/output
SI00, SI01 : Serial data input
SO00, SO01 : Serial data output
$\overline{\text{SSI00}}$: Serial interface chip select input
TI00 to TI03 : Timer input
TO00 to TO03 : Timer output
TOOL0 : Data input/output for tool
TOOLRxD, TOOLTxD : Data input/output for external device
TxD0 : Transmit data
VCOUT0, VCOUT1 : Comparator output
AMP0+, AMP1+, AMP2+, AMP3+ : Operational amplifier (+side) input
AMP0-, AMP1-, AMP2-, AMP3- : Operational amplifier (-side) input
AMP0O, AMP1O, AMP2O, AMP3O : Operational amplifier output
V_{DD} : Power supply
V_{SS} : Ground
X1, X2 : Crystal oscillator (main system clock)
XT1, XT2 : Crystal oscillator (subsystem clock)

1.5 Block Diagram

1.5.1 48-pin products



1.6 Outline of Functions

Remark This outline describes the functions at the time when Peripheral I/O redirection register 0 (PIOR0) are set to 00H.

(1/2)

Item		20-pin	24-pin	30-pin	32-pin	48-pin
		R5F1176x (x = 8, A)	R5F1177x (x = 8, A)	R5F117Ax (x = 8, A, C)	R5F117Bx (x = A, C)	R5F117Gx (x = A, C)
Code flash memory (KB)		8 to 16 KB	8 to 16 KB	8 to 32 KB	16 to 32 KB	16 to 32 KB
Data flash memory (KB)		2 KB	2 KB	2 KB	2 KB	2 KB
RAM		0.7 to 2.0 KB	0.7 to 2.0 KB	0.7 to 3.0 KB Note	2.0 to 3.0 KB Note	2.0 to 3.0 KB Note
Address space		1 MB				
Main system clock	High-speed system clock (f_{MX})	X1 (crystal/ceramic) oscillation, external main system clock input (EXCLK) HS (High-speed main) mode:1 to 20 MHz (V_{DD} = 2.7 to 3.6 V), HS (High-speed main) mode:1 to 16 MHz (V_{DD} = 2.4 to 3.6 V), LS (Low-speed main) mode:1 to 8 MHz (V_{DD} = 1.8 to 3.6 V), LV (Low-voltage main) mode:1 to 4 MHz (V_{DD} = 1.6 to 3.6 V), LP (Low-power main) mode:1 MHz (V_{DD} = 1.8 to 3.6 V)				
	High-speed on-chip oscillator clock (f_{IH}) Max: 24 MHz	HS (High-speed main) mode: 1 to 24 MHz (V_{DD} = 2.7 to 3.6 V), HS (High-speed main) mode: 1 to 16 MHz (V_{DD} = 2.4 to 3.6 V), LS (Low-speed main) mode: 1 to 8 MHz (V_{DD} = 1.8 to 3.6 V), LV (Low-voltage main) mode: 1 to 4 MHz (V_{DD} = 1.6 to 3.6 V), LP (Low-power main) mode: 1 MHz (V_{DD} = 1.8 to 3.6 V)				
	Middle-speed on-chip oscillator clock (f_{IM}) Max: 4 MHz					
Subsystem clock	Subsystem clock oscillator (f_{SX}, f_{SXR})	—		XT1 (crystal) oscillation 32.768 kHz (TYP.): V_{DD} = 1.6 to 3.6 V		
	Low-speed on-chip oscillator clock (f_{IL})	15 kHz (TYP.): V_{DD} = 1.6 to 3.6 V				
General-purpose register		8 bits × 32 registers (8 bits × 8 registers × 4 banks)				
Minimum instruction execution time		0.04167 μs (High-speed on-chip oscillator clock: f_{IH} = 24 MHz operation)				
		0.05 μs (High-speed system clock: f_{MX} = 20 MHz operation)				
		—		30.5 μs (Subsystem clock oscillator clock: f_{SX} = 32.768 kHz operation)		
Instruction set		• Data transfer (8/16 bits) • Adder and subtractor/logical operation (8/16 bits) • Multiplication (8 bits × 8 bits, 16 bits × 16 bits), Division (16 bits ÷ 16 bits, 32 bits ÷ 32 bits) • Multiplication and Accumulation (16 bits × 16 bits + 32 bits) • Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc.				
I/O port	Total	14	18	24	26	42
	CMOS I/O	11	15	19	21	33
	CMOS input	3	3	5	5	5
	N-ch open-drain I/O (6 V tolerance)	—	—	—	—	4
Timer	16-bit timer	4 channels				
	Watchdog timer	1 channel				
	Real-time clock	1 channel				
	12-bit interval timer	1 channel				
	8/16-bit interval timer	4 channels (8 bit) / 2 channels (16 bit)				
	Timer output	2	4	3	4	4
	RTC output	—		1 channel • 1 Hz (subsystem clock generator and RTC2/other clock: f_{SX} = 32.768 kHz)		

Note The flash library uses RAM in self-programming and rewriting of the data flash memory.
The target products and start address of the RAM areas used by the flash library are shown below.

R5F117xC (x = A, B, G): Start address FF300H

For the RAM areas used by the flash library, see **Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944)**.

(2/2)

Item		20-pin	24-pin	30-pin	32-pin	48-pin
		R5F1176x (x = 8, A)	R5F1177x (x = 8, A)	R5F117Ax (x = 8, A, C)	R5F117Bx (x = A, C)	R5F117Gx (x = A, C)
Clock output/buzzer output		1	1	1	1	2
		[20-pin, 24-pin products] • 2.44 kHz, 4.88 kHz, 9.76 kHz, 1.25 MHz, 2.5 MHz, 5 MHz, 10 MHz (Main system clock: f_{MAIN} = 20 MHz operation) [30-pin, 32-pin, 48-pin products] • 2.44 kHz, 4.88 kHz, 9.76 kHz, 1.25 MHz, 2.5 MHz, 5 MHz, 10 MHz (Main system clock: f_{MAIN} = 20 MHz operation) • 256 Hz, 512 Hz, 1.024 kHz, 2.048 kHz, 4.096 kHz, 8.192 kHz, 16.384 kHz, 32.768 kHz (subsystem clock generator and RTC/other clock: f_{SXR} = 32.768 kHz operation)				
12-bit resolution A/D converter		6 channels	6 channels	12 channels	12 channels	17 channels
Comparator (Window Comparator)		2 channels				
Operational amplifier		2 channels		4 channels		
Data Operation Circuit (DOC)		Comparison, addition, and subtraction of 16-bit data				
Serial interface		[20-pin, 30-pin products] • Simplified SPI (CSI): 1 channel/UART: 1 channel/simplified I^{2}C: 1 channel [24-pin, 32-pin, 48-pin products] • Simplified SPI (CSI): 2 channels/UART: 1 channel/simplified I^{2}C: 2 channels				
Data transfer controller (DTC)		16 sources	20 sources	19 sources	20 sources	22 sources
Event link controller (ELC)		Event input: 15 Event trigger output: 5	Event input: 17 Event trigger output: 5	Event input: 17 Event trigger output: 7	Event input: 17 Event trigger output: 7	Event input: 20 Event trigger output: 7
Vectored interrupt sources	Internal	22	22	24	24	24
	External	3	5	5	5	8
Key interrupt		—	3	—	3	4
Reset		• Reset by $\overline{\text{RESET}}$ pin • Internal reset by watchdog timer • Internal reset by power-on-reset • Internal reset by voltage detector • Internal reset by illegal instruction execution Note • Internal reset by RAM parity error • Internal reset by illegal-memory access				
Power-on-reset circuit		• Power-on-reset: 1.51 ± 0.04V (T_A = -40 to +85°C) • Power-down-reset: 1.50 ± 0.04 V (T_A = -40 to +85°C)				
Voltage detector	Power on	1.67 V to 3.13 V (12 stages)				
	Power down	1.63 V to 3.06 V (12 stages)				
On-chip debug function		Provided (Enable to tracing)				
Power supply voltage		V_{DD} = 1.6 to 3.6 V				
Operating ambient temperature		T_A = -40 to +105°C				

The illegal instruction is generated when instruction code FFH is executed.
Reset by the illegal instruction execution is not issued by emulation with the in-circuit emulator or on-chip debug emulator.

2. ELECTRICAL SPECIFICATIONS

Caution 1. The RL78 microcontrollers have an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.

Caution 2. The pins mounted depend on the product. Refer to 2.1 Port Functions to 2.2.1 Functions for each product in the RL78/I1D User's Manual.

Caution 3. Please contact Renesas Electronics sales office for derating of operation under T_A = +85 to +105°C. Derating is the systematic reduction of load for the sake of improved reliability.

Caution 4. When operating temperature exceeds 85°C, only HS (high-speed main) mode can be used as the flash operation mode. Regulator mode should be used with the normal setting (MCSEL = 0).

2.1 Absolute Maximum Ratings

Absolute Maximum Ratings **(1/2)**

Parameter	Symbols	Conditions	Ratings	Unit
Supply voltage	V_{DD}, AV_{DD}	$V_{DD} = AV_{DD}$	-0.3 to + 4.6	V
	AV_{REFP}		0.3 to AV_{DD} + 0.3 Note 2	V
	AV_{SS}		-0.5 to + 0.3	V
	AV_{REFM}		-0.3 to AV_{DD} + 0.3 Note 2 and $AV_{REFM} \leq AV_{REFP}$	V
REGC pin input voltage	V_{IREGC}	REGC	-0.3 to + 2.8 and -0.3 to V_{DD} + 0.3 Note 1	V
Input voltage	V_{I1}	P00 to P04, P30 to P33, P40, P50 to P57, P121 to P124, P130, P137, EXCLK, EXCLKS, $\overline{\text{RESET}}$	-0.3 to V_{DD} + 0.3 Note 2	V
	V_{I2}	P60 to P63 (N-ch open-drain)	-0.3 to + 6.5	V
	V_{I3}	P10 to P17, P20 to P25	-0.3 to AV_{DD} + 0.3 Note 2	V
Output voltage	V_{O1}	P00 to P04, P30 to P33, P40, P50 to P57, P60 to P63, P130	-0.3 to V_{DD} + 0.3 Note 2	V
	V_{O2}	P10 to P17, P20 to P25	-0.3 to AV_{DD} + 0.3 Note 2	V
Analog input voltage	V_{AI1}	ANI16 to ANI18	-0.3 to V_{DD} + 0.3 and -0.3 to $AV_{REF}(+)$ + 0.3 Notes 2, 3	V
	V_{AI2}	ANI0 to ANI13	-0.3 to AV_{DD} + 0.3 and -0.3 to $AV_{REF}(+)$ + 0.3 Notes 2, 3	V
	V_{AI3}	Operational amplifier input pin	-0.3 to AV_{DD} + 0.3 Note 2	V

Note 1. Connect the REGC pin to V_{SS} via a capacitor (0.47 to 1 μF). This value regulates the absolute maximum rating of the REGC pin. Do not use this pin with voltage applied to it.

Note 2. Must be 4.6 V or lower.

Note 3. Do not exceed AV_{REF} (+) + 0.3 V in case of A/D conversion target pin.

Caution **Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.**

Remark 1. Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

Remark 2. AV_{REF} (+): + side reference voltage of the A/D converter.

Remark 3. V_{SS}: Reference voltage

Absolute Maximum Ratings **(2/2)**

Parameter	Symbols	Conditions		Ratings	Unit
Output current, high	I_{OH1}	Per pin	P00 to P04, P30 to P33, P40, P50 to P57, P130	-40	mA
		Total of all pins -170 mA	P00 to P04, P40, P130	-70	mA
			P30 to P33, P50 to P57	-100	mA
	I_{OH2}	Per pin	P10 to P17, P20 to P25	-0.1	mA
		Total of all pins		-1.4	mA
Output current, low	I_{OL1}	Per pin	P00 to P04, P30 to P33, P40, P50 to P57, P60 to P63, P130	40	mA
		Total of all pins 170 mA	P00 to P04, P40, P130	70	mA
			P30 to P33, P50 to P57, P60 to P63	100	mA
	I_{OL2}	Per pin	P10 to P17, P20 to P25	0.4	mA
		Total of all pins		5.6	mA
Operating ambient temperature	T_A	In normal operation mode		-40 to +105	°C
		In flash memory programming mode			
Storage temperature	T_{stg}			-65 to +150	°C

Caution **Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.**

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

2.2 Oscillator Characteristics

2.2.1 X1, XT1 characteristics

(T_A = -40 to +85°C, 1.6 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V)
(T_A = +85 to +105°C, 2.4 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V)

Resonator	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock oscillation frequency (f_X) Note	Ceramic resonator/ crystal resonator	2.7 V ≤ V_{DD} ≤ 3.6 V	1.0		20.0	MHz
		2.4 V ≤ V_{DD} < 2.7 V	1.0		16.0	
		1.8 V ≤ V_{DD} < 2.4 V	1.0		8.0	
		1.6 V ≤ V_{DD} < 1.8 V	1.0		4.0	
XT1 clock oscillation frequency (f_{XT}) Note	Crystal resonator		32	32.768	35	kHz

Note Indicates only permissible oscillator frequency ranges. Refer to **AC Characteristics** for instruction execution time. Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.

Caution Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.

Remark When using the X1 oscillator and XT1 oscillator, refer to **6.4 System Clock Oscillator** in the RL78/I1D User's Manual.

2.2.2 On-chip oscillator characteristics

(T_A = -40 to +85°C, 1.6 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V)
(T_A = +85 to +105°C, 2.4 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V)

Oscillators	Parameters	Conditions		MIN.	TYP.	MAX.	Unit
High-speed on-chip oscillator clock frequency Notes 1, 2	f_{IH}			1		24	MHz
High-speed on-chip oscillator clock frequency accuracy		-20 to +85°C	1.8 V ≤ V_{DD} ≤ 3.6 V	-1.0		+1.0	%
			1.6 V ≤ V_{DD} < 1.8 V	-5.0		+5.0	
		-40 to -20°C	1.8 V ≤ V_{DD} ≤ 3.6 V	-1.5		+1.5	%
			1.6 V ≤ V_{DD} < 1.8 V	-5.5		+5.5	
		+85 to +105°C	2.4 V ≤ V_{DD} ≤ 3.6 V	-2.0		+2.0	%
Middle-speed on-chip oscillator oscillation frequency Note 2	f_{IM}			1		4	MHz
Middle-speed on-chip oscillator oscillation frequency accuracy		1.8V ≤ V_{DD} ≤ 3.6V		-12		+12	%
Low-speed on-chip oscillator clock frequency Note 2	f_{IL}				15		kHz
Low-speed on-chip oscillator clock frequency accuracy				-15		+15	%

Note 1. High-speed on-chip oscillator frequency is selected with bits 0 to 3 of the option byte (000C2H) and bits 0 to 2 of the HOCODIV register.

Note 2. This only indicates the oscillator characteristics. Refer to **AC Characteristics** for instruction execution time.

2.3 DC Characteristics

2.3.1 Pin characteristics

(T_A = -40 to +85°C, 1.6 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V)
(T_A = +85 to +105°C, 2.4 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V) **(1/5)**

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, high Note 1	I_{OH1}	Per pin for P00 to P04, P30 to P33, P40, P50 to P57, P130	T_A = -40 to +85°C			-10.0 Note 2	mA
			T_A = +85 to +105°C			-3.0 Note 2	mA
		Total of P00 to P04, P40, P130 (When duty ≤ 70% Note 3)	2.7 V ≤ V_{DD} ≤ 3.6 V			-10.0	mA
			1.8 V ≤ V_{DD} < 2.7 V			-5.0	mA
			1.6 V ≤ V_{DD} < 1.8 V			-2.5	mA
		Total of P30 to P33, P50 to P57 (When duty ≤ 70% Note 3)	2.7 V ≤ V_{DD} ≤ 3.6 V			-19.0	mA
			1.8 V ≤ V_{DD} < 2.7 V			-10.0	mA
			1.6 V ≤ V_{DD} < 1.8 V			-5.0	mA
		Total of all pins (When duty ≤ 70% Note 3)				-29.0	mA
	I_{OH2}	Per pin for P10 to P17, P20 to P25				-0.1 Note 2	mA
		Total of all pins (When duty ≤ 70% Note 3)	1.6 V ≤ V_{DD} ≤ 3.6 V			-1.4	mA

Note 1. Value of current at which the device operation is guaranteed even if the current flows from the V_{DD} pin to an output pin.

Note 2. Do not exceed the total current value.

Note 3. Specification under conditions where the duty factor ≤ 70%.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

- Total output current of pins = (I_{OH} × 0.7)/(n × 0.01)

<Example> Where n = 80% and I_{OH} = -10.0 mA
Total output current of pins = (-10.0 × 0.7)/(80 × 0.01) ≈ -8.7 mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor.
A current higher than the absolute maximum rating must not flow into one pin.

Caution **P30 and P51 to P56 do not output high level in N-ch open-drain mode.**

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(T_A = -40 to +85°C, 1.6 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V)
(T_A = +85 to +105°C, 2.4 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V) (2/5)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, low Note 1	I_{OL1}	Per pin for P00 to P04, P30 to P33, P40, P50 to P57, P130	T_A = -40 to +85°C			20.0 Note 2	mA
			T_A = +85 to +105°C			8.5 Note 2	mA
		Per pin for P60 to P63				15.0 Note 2	mA
		Total of P00 to P04, P40, P130 (When duty ≤ 70% Note 3)	2.7 V ≤ V_{DD} ≤ 3.6 V			15.0	mA
			1.8 V ≤ V_{DD} < 2.7 V			9.0	mA
			1.6 V ≤ V_{DD} < 1.8 V			4.5	mA
		Total of P30 to P33, P50 to P57, P60 to P63 (When duty ≤ 70% Note 3)	2.7 V ≤ V_{DD} ≤ 3.6 V			35.0	mA
			1.8 V ≤ V_{DD} < 2.7 V			20.0	mA
			1.6 V ≤ V_{DD} < 1.8 V			10.0	mA
		Total of all pins (When duty ≤ 70% Note 3)				50.0	mA
	I_{OL2}	Per pin for P10 to P17, P20 to P25				0.4 Note 2	mA
		Total of all pins (When duty ≤ 70% Note 3)	1.6 V ≤ V_{DD} ≤ 3.6 V			5.6	mA

Note 1. Value of current at which the device operation is guaranteed even if the current flows from an output pin to the V_{SS} pin.

Note 2. Do not exceed the total current value.

Note 3. Specification under conditions where the duty factor ≤ 70%.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

- Total output current of pins = (I_{OL} × 0.7)/(n × 0.01)

  <Example> Where n = 80% and I_{OL} = 10.0 mA

  Total output current of pins = (10.0 × 0.7)/(80 × 0.01) ≈ 8.7 mA

  However, the current that is allowed to flow into one pin does not vary depending on the duty factor.

  A current higher than the absolute maximum rating must not flow into one pin.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(T_A = -40 to +85°C, 1.6 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V)

(T_A = +85 to +105°C, 2.4 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V) **(3/5)**

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Input voltage, high	V_{IH1}	P00 to P04, P30 to P33, P40, P50 to P57, P130	Normal input buffer	0.8 V_{DD}		V_{DD}	V
	V_{IH2}	P30, P32, P33, P51, P52, P54 to P57	TTL input buffer 3.3 V ≤ V_{DD} ≤ 3.6 V	2.0		V_{DD}	V
			TTL input buffer 1.6 V ≤ V_{DD} < 3.3 V	1.5		V_{DD}	V
	V_{IH3}	P10 to P17, P20 to P25		0.7 AV_{DD}		AV_{DD}	V
	V_{IH4}	P60 to P63		0.7 V_{DD}		6.0	V
	V_{IH5}	P121 to P124, P137, EXCLK, EXCLKS, $\overline{\text{RESET}}$		0.8 V_{DD}		V_{DD}	V
Input voltage, low	V_{IL1}	P00 to P04, P30 to P33, P40, P50 to P57, P130	Normal input buffer	0		0.2 V_{DD}	V
	V_{IL2}	P30, P32, P33, P51, P52, P54 to P57	TTL input buffer 3.3 V ≤ V_{DD} ≤ 3.6 V	0		0.5	V
			TTL input buffer 1.6 V ≤ V_{DD} < 3.3 V	0		0.32	V
	V_{IL3}	P10 to P17, P20 to P25		0		0.3 AV_{DD}	V
	V_{IL4}	P60 to P63		0		0.3 V_{DD}	V
	V_{IL5}	P121 to P124, P137, EXCLK, EXCLKS, $\overline{\text{RESET}}$		0		0.2 V_{DD}	V

Caution The maximum value of V_{IH} of pins P30 and P51 to P56 is V_{DD}, even in the N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(TA = -40 to +85°C, 1.6 V ≤ AVDD = VDD ≤ 3.6 V, VSS = AVSS = 0 V)

(TA = +85 to +105°C, 2.4 V ≤ AVDD = VDD ≤ 3.6 V, VSS = AVSS = 0 V) **(4/5)**

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output voltage, high	VOH1	P00 to P04, P30 to P33, P40, P50 to P57, P130	2.7 V ≤ VDD ≤ 3.6 V, IOH = -2.0 mA	VDD - 0.6			V
			1.8 V ≤ VDD ≤ 3.6 V Note 3, IOH = -1.5 mA	VDD - 0.5			V
			1.6 V ≤ VDD ≤ 3.6 V Note 1, IOH = -1.0 mA	VDD - 0.5			V
	VOH2	P10 to P17, P20 to P25	1.6 V ≤ AVDD ≤ 3.6 V Note 2, IOH = -100 μA	AVDD - 0.5			V
Output voltage, low	VOL1	P00 to P04, P30 to P33, P40, P50 to P57, P130	2.7 V ≤ VDD ≤ 3.6 V, IOL = 3.0 mA			0.6	V
			2.7 V ≤ VDD ≤ 3.6 V, IOL = 1.5 mA			0.4	V
			1.8 V ≤ VDD ≤ 3.6 V Note 3, IOL = 0.6 mA			0.4	V
			1.6 V ≤ AVDD ≤ 3.6 V Note 1, IOL = 0.3 mA			0.4	V
	VOL2	P10 to P17, P20 to P25	1.6 V ≤ AVDD ≤ 3.6 V Note 2, IOL = 400 μA			0.4	V
	VOL3	P60 to P63	2.7 V ≤ VDD ≤ 3.6 V, IOL = 3.0 mA			0.4	V
			1.8 V ≤ VDD ≤ 3.6 V Note 3, IOL = 2.0 mA			0.4	V
			1.6 V ≤ AVDD ≤ 3.6 V Note 1, IOL = 1.0 mA			0.4	V

Note 1. Only TA = -40 to +85°C is guaranteed.

Note 2. The condition that 2.4 V ≤ AVDD ≤ 3.6 V is guaranteed when +85°C < TA ≤ +105°C.

Note 3. The condition that 2.4 V ≤ VDD ≤ 3.6 V is guaranteed when +85°C < TA ≤ +105°C.

Caution **P30 and P51 to P56 do not output high level in N-ch open-drain mode.**

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(T_A = -40 to +85°C, 1.6 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V)
(T_A = +85 to +105°C, 2.4 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V) **(5/5)**

Items	Symbol	Conditions			MIN.	TYP.	MAX.	Unit
Input leakage current, high	I_{LIH1}	P00 to P04, P30 to P33, P40, P50 to P57, P60 to P63, P130, P137	$V_I = V_{DD}$				1	μA
	I_{LIH2}	$\overline{\text{RESET}}$	$V_I = V_{DD}$				1	μA
	I_{LIH3}	P121 to P124 (X1, X2, EXCLK, XT1, XT2, EXCLKS)	$V_I = V_{DD}$	In input port or external clock input			1	μA
				In resonator connection			10	μA
	I_{LIH4}	P10 to P17, P20 to P25	$V_I = AV_{DD}$				1	μA
Input leakage current, low	I_{LIL1}	P00 to P04, P30 to P33, P40, P50 to P57, P60 to P63, P130, P137	$V_I = V_{SS}$				-1	μA
	I_{LIL2}	$\overline{\text{RESET}}$	$V_I = V_{SS}$				-1	μA
	I_{LIL3}	P121 to P124 (X1, X2, EXCLK, XT1, XT2, EXCLKS)	$V_I = V_{SS}$	In input port or external clock input			-1	μA
				In resonator connection			-10	μA
	I_{LIL4}	P10 to P17, P20 to P25	$V_I = AV_{SS}$				-1	μA
On-chip pull-up resistance	R_U	P00 to P04, P30 to P33, P40, P50 to P57, P130	$V_I = V_{SS}$, In input port		10	20	100	kΩ

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

2.3.2 Supply current characteristics

(T_A = -40 to +85°C, 1.6 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V)
(T_A = +85 to +105°C, 2.4 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V) (1/4)

Parameter	Symbol	Conditions						MIN.	TYP.	MAX.	Unit
Supply current Note 1	I_{DD1}	Operating mode	HS (high-speed main) mode	f_{IH} = 24 MHz Note 3, T_A = -40 to +105°C	Basic operation	V_{DD} = 3.0 V			1.4		mA
			HS (high-speed main) mode	f_{IH} = 24 MHz Note 3, T_A = -40 to +85°C	Normal operation	V_{DD} = 3.0 V			3.2	6.3	mA
				f_{IH} = 24 MHz Note 3, T_A = +85 to +105°C	Normal operation	V_{DD} = 3.0 V				6.7	
				f_{IH} = 16 MHz Note 3, T_A = -40 to +85°C	Normal operation	V_{DD} = 3.0 V			2.4	4.6	
				f_{IH} = 16 MHz Note 3, T_A = +85 to +105°C	Normal operation	V_{DD} = 3.0 V				4.9	
			LS (low-speed main) mode (MCSEL = 0)	f_{IH} = 8 MHz Note 3, T_A = -40 to +85°C	Normal operation	V_{DD} = 3.0 V			1.1	2.0	mA
						V_{DD} = 2.0 V			1.1	2.0	
			LS (low-speed main) mode (MCSEL = 1)	f_{IH} = 4 MHz Note 3, T_A = -40 to +85°C	Normal operation	V_{DD} = 3.0 V			0.72	1.30	mA
						V_{DD} = 2.0 V			0.72	1.30	
				f_{IM} = 4 MHz Note 7, T_A = -40 to +85°C	Normal operation	V_{DD} = 3.0 V			0.58	1.10	
						V_{DD} = 2.0 V			0.58	1.10	
			LV (low-voltage main) mode	f_{IH} = 3 MHz Note 3, T_A = -40 to +85°C	Normal operation	V_{DD} = 3.0 V			1.2	1.8	mA
						V_{DD} = 2.0 V			1.2	1.8	
			LP (low-power main) mode Note 5 (MCSEL = 1)	f_{IH} = 1 MHz Note 3, T_A = -40 to +85°C	Normal operation	V_{DD} = 3.0 V			290	480	μA
						V_{DD} = 2.0 V			290	480	
				f_{IM} = 1 MHz Note 5, T_A = -40 to +85°C	Normal operation	V_{DD} = 3.0 V			124	230	
						V_{DD} = 2.0 V			124	230	
			HS (high-speed main) mode	f_{MX} = 20 MHz Note 2, T_A = -40 to +85°C	Normal operation	V_{DD} = 3.0 V	Square wave input		2.7	5.3	mA
							Resonator connection		2.8	5.5	
				f_{MX} = 20 MHz Note 2, T_A = +85 to +105°C	Normal operation	V_{DD} = 3.0 V	Square wave input			5.7	
							Resonator connection			5.8	
				f_{MX} = 10 MHz Note 2, T_A = -40 to +85°C	Normal operation	V_{DD} = 3.0 V	Square wave input		1.8	3.1	
							Resonator connection		1.9	3.2	
				f_{MX} = 10 MHz Note 2, T_A = +85 to +105°C	Normal operation	V_{DD} = 3.0 V	Square wave input			3.4	
							Resonator connection			3.5	
			LS (low-speed main) mode (MCSEL = 0)	f_{MX} = 8 MHz Note 2, T_A = -40 to +85°C	Normal operation	V_{DD} = 3.0 V	Square wave input		0.9	1.9	mA
							Resonator connection		1.0	2.0	
				f_{MX} = 8 MHz Note 2, T_A = -40 to +85°C	Normal operation	V_{DD} = 2.0 V	Square wave input		0.9	1.9	
							Resonator connection		1.0	2.0	
			LS (low-speed main) mode (MCSEL = 1)	f_{MX} = 4 MHz Note 2, T_A = -40 to +85°C	Normal operation	V_{DD} = 3.0 V	Square wave input		0.6	1.1	mA
							Resonator connection		0.6	1.2	
				f_{MX} = 4 MHz Note 2, T_A = -40 to +85°C	Normal operation	V_{DD} = 2.0 V	Square wave input		0.6	1.1	
							Resonator connection		0.6	1.2	
			LP (low-power main) mode (MCSEL = 1)	f_{MX} = 1 MHz Note 2, T_A = -40 to +85°C	Normal operation	V_{DD} = 3.0 V	Square wave input		100	190	μA
							Resonator connection		136	250	
				f_{MX} = 1 MHz Note 2, T_A = -40 to +85°C	Normal operation	V_{DD} = 2.0 V	Square wave input		100	190	
							Resonator connection		136	250	

(**Notes** and **Remarks** are listed on the next page.)

(T_A = -40 to +85°C, 1.6 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V)
(T_A = +85 to +105°C, 2.4 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V) **(2/4)**

Parameter	Symbol	Conditions					MIN.	TYP.	MAX.	Unit
Supply current Note 1	I_{DD1}	Operating mode	Subsystem clock operation	f_{SX} = 32.768 kHz, T_A = -40°C Note 4	Normal operation	Square wave input		3.2	6.1	μA
						Resonator connection		3.3	6.1	
				f_{SX} = 32.768 kHz, T_A = +25°C Note 4	Normal operation	Square wave input		3.4	6.1	
						Resonator connection		3.6	6.1	
				f_{SX} = 32.768 kHz, T_A = +50°C Note 4	Normal operation	Square wave input		3.5	6.7	
						Resonator connection		3.7	6.7	
				f_{SX} = 32.768 kHz, T_A = +70°C Note 4	Normal operation	Square wave input		3.7	7.5	
						Resonator connection		3.9	7.5	
				f_{SX} = 32.768 kHz, T_A = +85°C Note 4	Normal operation	Square wave input		4.0	8.9	
						Resonator connection		4.2	8.9	
				f_{SX} = 32.768 kHz, T_A = +105°C Note 4	Normal operation	Square wave input		4.5	21.0	
						Resonator connection		4.7	21.1	
				f_{IL} = 15 kHz, T_A = -40°C Note 6	Normal operation			1.8	5.9	
				f_{IL} = 15 kHz, T_A = +25°C Note 6	Normal operation			1.9	5.9	
				f_{IL} = 15 kHz, T_A = +85°C Note 6	Normal operation			2.3	8.7	
				f_{IL} = 15 kHz, T_A = +105°C Note 6	Normal operation			3.0	20.9	

<R> **Note 1.** Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD} or V_{SS}. The following points apply in the HS (high-speed main), LS (low-speed main), LV (low-voltage main), and LP (low-power main) modes.

- The currents in the “TYP.” column do not include the operating currents of the peripheral modules.
- The currents in the “MAX.” column include the operating currents of the peripheral modules, except for those flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors, and those flowing while the data flash memory is being rewritten.

In the subsystem clock operation, the currents in both the “TYP.” and “MAX.” columns do not include the operating currents of the peripheral modules. However, in HALT mode, including the current flowing into the real-time clock 2.

Note 2. When the high-speed on-chip oscillator clock, middle-speed on-chip oscillator clock, low-speed on-chip oscillator clock, and sub clock are stopped.

Note 3. When the high-speed system clock, middle-speed on-chip oscillator clock, low-speed on-chip oscillator clock, and sub clock are stopped.

<R> **Note 4.** When the high-speed system clock, high-speed on-chip oscillator clock, middle-speed on-chip oscillator clock, low-speed on-chip oscillator clock, and sub clock are stopped. When ultra-low-power consumption oscillation is set (AMPHS1, AMPHS0) = (1, 0).

<R> **Note 5.** When the high-speed system clock, high-speed on-chip oscillator clock, sub clock, and low-speed on-chip oscillator clock are stopped.

Note 6. When the high-speed system clock, high-speed on-chip oscillator clock, middle-speed on-chip oscillator clock, and sub clock are stopped.

Note 7. When the high-speed system clock, high-speed on-chip oscillator clock, low-speed on-chip oscillator clock, and sub clock are stopped.

Remark 1. f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
Remark 2. f_{IH}: High-speed on-chip oscillator clock frequency (24 MHz max.)
Remark 3. f_{IM}: Middle-speed on-chip oscillator clock frequency (4 MHz max.)
Remark 4. f_{IL}: Low-speed on-chip oscillator clock frequency
Remark 5. f_{SX}: Sub clock frequency (XT1 clock oscillation frequency)
Remark 6. f_{SUB}: Subsystem clock frequency (XT1 clock oscillation frequency or low-speed on-chip oscillator clock frequency)
Remark 7. Except subsystem clock operation, temperature condition of the TYP. value is T_A = 25°C.

(T_A = -40 to +85°C, 1.6 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V)

(T_A = +85 to +105°C, 2.4 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V) **(3/4)**

Parameter	Symbol	Conditions					MIN.	TYP.	MAX.	Unit
Supply current Note 1	I_{DD2} Note 2	HALT mode	HS (high-speed main) mode	f_{IH} = 24 MHz Note 4, T_A = -40 to +85°C	V_{DD} = 3.0 V			0.37	1.83	mA
				f_{IH} = 24 MHz Note 4, T_A = +85 to +105°C	V_{DD} = 3.0 V				2.85	
				f_{IH} = 16 MHz Note 4, T_A = -40 to +85°C	V_{DD} = 3.0 V			0.36	1.38	
				f_{IH} = 16 MHz Note 4, T_A = +85 to +105°C	V_{DD} = 3.0 V				2.08	
			LS (low-speed main) mode (MCSEL = 0)	f_{IH} = 8 MHz Note 4, T_A = -40 to +85°C	V_{DD} = 3.0 V			250	710	μA
					V_{DD} = 2.0 V			250	710	
			LS (low-speed main) mode (MCSEL = 1)	f_{IH} = 4 MHz Note 4, T_A = -40 to +85°C	V_{DD} = 3.0 V			204	400	μA
					V_{DD} = 2.0 V			204	400	
				f_{IM} = 4 MHz Note 7, T_A = -40 to +85°C	V_{DD} = 3.0 V			40	250	
					V_{DD} = 2.0 V			40	250	
			LV (low-voltage main) mode	f_{IH} = 3 MHz Note 4, T_A = -40 to +85°C	V_{DD} = 3.0 V			425	800	μA
					V_{DD} = 2.0 V			425	800	
			LP (low-power main) mode (MCSEL = 1)	f_{IH} = 1 MHz Note 4, T_A = -40 to +85°C	V_{DD} = 3.0 V			192	400	μA
					V_{DD} = 2.0 V			192	400	
				f_{IM} = 1 MHz Note 7, T_A = -40 to +85°C	V_{DD} = 3.0 V			27	100	
					V_{DD} = 2.0 V			27	100	
			HS (high-speed main) mode	f_{MX} = 20 MHz Note 3, T_A = -40 to +85°C	V_{DD} = 3.0 V	Square wave input		0.20	1.55	mA
						Resonator connection		0.40	1.74	
				f_{MX} = 20 MHz Note 3, T_A = +85 to +105°C	V_{DD} = 3.0 V	Square wave input			2.45	
						Resonator connection			2.57	
				f_{MX} = 10 MHz Note 3, T_A = -40 to +85°C	V_{DD} = 3.0 V	Square wave input		0.15	0.86	
						Resonator connection		0.30	0.93	
				f_{MX} = 10 MHz Note 3, T_A = +85 to +105°C	V_{DD} = 3.0 V	Square wave input			1.28	
						Resonator connection			1.36	
			LS (low-speed main) mode (MCSEL = 0)	f_{MX} = 8 MHz Note 3, T_A = -40 to +85°C	V_{DD} = 3.0 V	Square wave input		68	550	μA
						Resonator connection		120	590	
				f_{MX} = 8 MHz Note 3, T_A = -40 to +85°C	V_{DD} = 2.0 V	Square wave input		68	550	
						Resonator connection		120	590	
			LS (low-speed main) mode (MCSEL = 1)	f_{MX} = 4 MHz Note 3, T_A = -40 to +85°C	V_{DD} = 3.0 V	Square wave input		23	128	μA
						Resonator connection		65	200	
				f_{MX} = 1 MHz Note 3, T_A = -40 to +85°C	V_{DD} = 2.0 V	Square wave input		23	128	
						Resonator connection		65	200	
			LP (low-power main) mode (MCSEL = 1)	f_{MX} = 4 MHz Note 3, T_A = -40 to +85°C	V_{DD} = 3.0 V	Square wave input		10	64	μA
						Resonator connection		48	150	
				f_{MX} = 1 MHz Note 3, T_A = -40 to +85°C	V_{DD} = 2.0 V	Square wave input		10	64	
						Resonator connection		48	150	
			Subsystem clock operation	f_{SX} = 32.768 kHz, T_A = -40°C Note 5		Square wave input		0.24	0.57	μA
						Resonator connection		0.42	0.76	
				f_{SX} = 32.768 kHz, T_A = +25°C Note 5		Square wave input		0.30	0.57	
						Resonator connection		0.54	0.76	
				f_{SX} = 32.768 kHz, T_A = +50°C Note 5		Square wave input		0.35	1.17	
						Resonator connection		0.60	1.36	
				f_{SX} = 32.768 kHz, T_A = +70°C Note 5		Square wave input		0.42	1.97	
						Resonator connection		0.70	2.16	
				f_{SX} = 32.768 kHz, T_A = +85°C Note 5		Square wave input		0.80	3.37	
						Resonator connection		0.95	3.56	
				f_{SX} = 32.768 kHz, T_A = +105°C Note 5		Square wave input		1.80	17.10	
						Resonator connection		2.20	17.50	
				f_{IL} = 15 kHz, T_A = -40°C Note 6				0.40	1.22	μA
				f_{IL} = 15 kHz, T_A = +25°C Note 6				0.47	1.22	
				f_{IL} = 15 kHz, T_A = +85°C Note 6				0.80	3.30	
				f_{IL} = 15 kHz, T_A = +105°C Note 6				2.00	17.30	

(**Notes** and **Remarks** are listed on the next page.)

<R> **Note 1.** Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD} or V_{SS}. The following points apply in the HS (high-speed main), LS (low-speed main), LV (low-voltage main), and LP (low-power main) modes.

- The currents in the “TYP.” column do not include the operating currents of the peripheral modules.
- The currents in the “MAX.” column include the operating currents of the peripheral modules, except for those flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors, and those flowing while the data flash memory is being rewritten.

In the subsystem clock operation, the currents in both the “TYP.” and “MAX.” columns do not include the operating currents of the peripheral modules. However, in HALT mode, including the current flowing into the real-time clock 2.

Note 2. When the HALT instruction is executed in the flash memory.

Note 3. When the high-speed on-chip oscillator clock, middle-speed on-chip oscillator clock, low-speed on-chip oscillator clock, and sub clock are stopped.

Note 4. When the high-speed system clock, middle-speed on-chip oscillator clock, low-speed on-chip oscillator clock, and sub clock are stopped.

<R> **Note 5.** When the high-speed system clock, middle-speed on-chip oscillator clock, low-speed on-chip oscillator clock, and high-speed on-chip oscillator clock are stopped. When RTCLPC = 1 and ultra-low-power consumption oscillation is set (AMPHS1, AMPHS0) = (1, 0).

Note 6. When the high-speed on-chip oscillator clock, middle-speed on-chip oscillator clock, high-speed system clock, and sub clock are stopped.

Note 7. When the high-speed system clock, high-speed on-chip oscillator clock, low-speed on-chip oscillator clock, and sub clock are stopped.

Remark 1. f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
Remark 2. f_{IH}: High-speed on-chip oscillator clock frequency (24 MHz max.)
Remark 3. f_{IM}: Middle-speed on-chip oscillator clock frequency (4 MHz max.)
Remark 4. f_{IL}: Low-speed on-chip oscillator clock frequency
Remark 5. f_{SX}: Sub clock frequency (XT1 clock oscillation frequency)
Remark 6. f_{SUB}: Subsystem clock frequency (XT1 clock oscillation frequency or low-speed on-chip oscillator clock frequency)
Remark 7. Except subsystem clock operation, temperature condition of the TYP. value is T_A = 25°C.

(T_A = -40 to +85°C, 1.6 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V)

(T_A = +85 to +105°C, 2.4 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V) **(4/4)**

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
<R> Supply current Note 1	I_{DD3}	STOP mode Note 2	T_A = -40°C		0.16	0.51	μA
			T_A = +25°C		0.22	0.51	
			T_A = +50°C		0.27	1.10	
			T_A = +70°C		0.37	1.90	
			T_A = +85°C		0.60	3.30	
			T_A = +105°C		1.50	17.00	

<R> **Note 1.** Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD} or V_{SS}. In the STOP mode, the currents in both the “TYP.” and “MAX.” columns do not include the operating currents of the peripheral modules.

<R> **Note 2.** For the setting of the current values when operating the subsystem clock in STOP mode, see the current values when operating the subsystem clock in HALT mode.

Peripheral Functions (Common to all products)

(T_A = -40 to +85°C, 1.6 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V)

(T_A = +85 to +105°C, 2.4 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V) **(1/2)**

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Low-speed on-chip oscillator operating current	I_{FIL} Note 1				0.20		μA
RTC2 operating current	I_{RTC} Notes 1, 2, 3	f_{SX} = 32.768 kHz			0.02		μA
12-bit interval timer operating current	I_{TMKA} Notes 1, 2, 4	f_{SX} = 32.768 kHz			0.04		μA
8-bit interval timer operating current	I_{TMT} Notes 1, 9	f_{SX} = 32.768 kHz f_{MAIN} stopped (per unit)	8-bit counter mode × 2-channel operation		0.12		μA
			16-bit counter mode operation		0.10		μA
Watchdog timer operating current	I_{WDT} Notes 1, 2, 5	f_{IL} = 15 kHz			0.22		μA
A/D converter operating current	I_{ADC} Notes 6, 10	During maximum-speed conversion	AV_{DD} = 3.0 V		420	720	μA
$AV_{REF(+)}$ current	I_{AVREF} Note 11	AV_{REFP} = 3.0 V, ADREFP1 = 0, ADREFP0 = 1			14.0	25.0	μA
Internal reference voltage (1.45 V) current	I_{ADREF} Notes 1, 12				85.0		μA
Temperature sensor operating current	I_{TMPS} Note 1				85.0		μA
Comparator operating current	I_{CMP} Notes 8, 10	AV_{DD} = 3.6 V, Regulator output voltage = 2.1 V	Comparator high-speed mode Window mode		12.5		μA
			Comparator low-speed mode Window mode		3.0		
			Comparator high-speed mode Standard mode		6.5		
			Comparator low-speed mode Standard mode		1.7		
		AV_{DD} = 3.6 V, Regulator output voltage = 1.8 V	Comparator high-speed mode Window mode		8.0		
			Comparator low-speed mode Window mode		2.2		
			Comparator high-speed mode Standard mode		4.0		
			Comparator low-speed mode Standard mode		1.3		
Operational amplifier operating current	I_{AMP} Notes 10, 13	Low-power consumption mode	One operational amplifier unit operates Note 14		2.5	4.0	μA
			Two operational amplifier units operate Note 14		4.5	8.0	
			Three operational amplifier units operate Note 14		6.5	11.0	
			Four operational amplifier units operate Note 14		8.5	14.0	
		High-speed mode	One operational amplifier unit operates Note 14		140	220	
			Two operational amplifier units operate Note 14		280	410	
			Three operational amplifier units operate Note 14		420	600	
			Four operational amplifier units operate Note 14		560	780	
LVD operating current	I_{LVD} Notes 1, 7				0.10		μA

(**Notes** and **Remarks** are listed on the next page.)

Note 1. Current flowing to V_{DD}.

Note 2. When the high-speed on-chip oscillator clock, middle-speed on-chip oscillator clock, and high-speed system clock are stopped.

Note 3. Current flowing only to the real-time clock 2 (RTC2) (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either I_{DD1} or I_{DD2}, and I_{RTC}, when the real-time clock 2 operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, I_{FIL} should be added. I_{DD2} subsystem clock operation includes the operational current of the real-time clock 2.

Note 4. Current flowing only to the 12-bit interval timer (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either I_{DD1} or I_{DD2}, and I_{IT}, when the 12-bit interval timer operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, I_{FIL} should be added.

Note 5. Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator).
The supply current of the RL78 microcontrollers is the sum of I_{DD1}, I_{DD2} or I_{DD3} and I_{WDT} when the watchdog timer is in operation.

Note 6. Current flowing only to the A/D converter. The supply current of the RL78 microcontrollers is the sum of I_{DD1} or I_{DD2} and I_{ADC} when the A/D converter operates in an operation mode or the HALT mode.

Note 7. Current flowing only to the LVD circuit. The supply current of the RL78 microcontrollers is the sum of I_{DD1}, I_{DD2} or I_{DD3} and I_{LVD} when the LVD circuit is in operation.

Note 8. Current flowing only to the comparator circuit. The supply current of the RL78 microcontrollers is the sum of I_{DD1}, I_{DD2}, or I_{DD3} and I_{CMP} when the comparator circuit is in operation.

Note 9. Current flowing only to the 8-bit interval timer (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either I_{DD1} or I_{DD2}, and I_{IT}, when the 8-bit interval timer operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, I_{FIL} should be added.

Note 10. Current flowing to AV_{DD}.

Note 11. Current flowing into AV_{REFP}.

Note 12. Current consumed by generating the internal reference voltage (1.45 V).

Note 13. Current flowing only to the operational amplifier. The current value of the RL78 microcontrollers is the sum of I_{DD1}, I_{DD2}, or I_{DD3} and I_{AMP} when the operational amplifier is operating in operating mode, HALT mode, or STOP mode.

Note 14. The values include the operating current of the operational amplifier reference current circuit.

Remark 1. f_{IL}: Low-speed on-chip oscillator clock frequency
Remark 2. f_{SUB}: Subsystem clock frequency (XT1 clock oscillation frequency)
Remark 3. f_{CLK}: CPU/peripheral hardware clock frequency
Remark 4. Temperature condition of the TYP. value is T_A = 25°C.

(T_A = -40 to +85°C, 1.6 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V)
(T_A = +85 to +105°C, 2.4 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V) **(2/2)**

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Self-programming operating current	I_{FSP} Notes 1, 3				2.0	12.20	mA
BGO current	I_{BGO} Notes 1, 2				2.0	12.20	mA
SNOOZE operating current	I_{SNOZ} Note 1	ADC operation AV_{REFP} = V_{DD} = 3.0 V T_A = -40 to +85°C	The mode is performed Note 5		0.50	0.60	mA
			The A/D conversion operations are performed Note 1		0.60	0.75	mA
			The A/D conversion operations are performed Note 4		420	720	μA
		ADC operation AV_{REFP} = V_{DD} = 3.0 V T_A = +85 to +105°C	The mode is performed Note 5		0.50	1.10	mA
			The A/D conversion operations are performed Note 1		0.60	1.34	mA
			The A/D conversion operations are performed Note 4		420	720	μA
		Simplified SPI (CSI)/UART operation	T_A = -40 to +85°C		0.70	0.84	mA
			T_A = +85 to +105°C		0.70	1.54	mA

Note 1. Current flowing to V_{DD}.
Note 2. Current flowing during programming of the data flash.
Note 3. Current flowing during self-programming.
Note 4. Current flowing to AV_{DD}.
Note 5. For shift time to the SNOOZE mode, see **23.3.3 SNOOZE mode** in the RL78/I1D User's Manual.

Remark 1. f_{IL}: Low-speed on-chip oscillator clock frequency
Remark 2. f_{SUB}: Subsystem clock frequency (XT1 clock oscillation frequency)
Remark 3. f_{CLK}: CPU/peripheral hardware clock frequency
Remark 4. Temperature condition of the TYP. value is T_A = 25°C.

2.4 AC Characteristics

(T_A = -40 to +85°C, 1.6 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V)

(T_A = +85 to +105°C, 2.4 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V) **(1/2)**

Items	Symbol	Conditions			MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum instruction execution time)	T_{CY}	Main system clock (f_{MAIN}) operation	HS (high-speed main) mode	2.7 V ≤ V_{DD} ≤ 3.6 V	0.04167		1	μs
				2.4 V ≤ V_{DD} < 2.7 V	0.0625		1	μs
			LS (low-speed main) mode	1.8 V ≤ V_{DD} ≤ 3.6 V PMMC. MCSEL = 0	0.125		1	μs
				1.8 V ≤ V_{DD} ≤ 3.6 V PMMC. MCSEL = 1	0.25		1	
			LP (low-power main) mode	1.8 V ≤ V_{DD} ≤ 3.6 V		1		μs
			LV (low-voltage main) mode	1.8 V ≤ V_{DD} ≤ 3.6 V	0.25		1	μs
				1.6 V ≤ V_{DD} < 1.8 V	0.34		1	
		Subsystem clock (f_{SUB}) operation	f_{SX}	1.8 V ≤ V_{DD} ≤ 3.6 V	28.5	30.5	31.3	μs
			f_{IL}	1.8 V ≤ V_{DD} ≤ 3.6 V		66.7		
		In the self-programming mode	HS (high-speed main) mode	2.7 V ≤ V_{DD} ≤ 3.6 V	0.04167		1	μs
				2.4 V ≤ V_{DD} < 2.7 V	0.0625		1	μs
			LS (low-speed main) mode	1.8 V ≤ V_{DD} ≤ 3.6 V	0.125		1	μs
			LV (low-voltage main) mode	1.8 V ≤ V_{DD} ≤ 3.6 V	0.25		1	μs
External system clock frequency	f_{EX}	2.7 V ≤ V_{DD} ≤ 3.6 V			1.0		20.0	MHz
		2.4 V ≤ V_{DD} <2.7 V			1.0		16.0	MHz
		1.8 V ≤ V_{DD} <2.4 V			1		8	MHz
		1.6 V ≤ V_{DD} <1.8 V			1		4	MHz
	f_{EXS}				32		35	kHz
External system clock input high-level width, low-level width	t_{EXH}, t_{EXL}	2.7 V ≤ V_{DD} ≤ 3.6 V			24			ns
		2.4 V ≤ V_{DD} <2.7 V			30			ns
		1.8 V ≤ V_{DD} <2.4 V			60			ns
		1.6 V ≤ V_{DD} <1.8 V			120			ns
	t_{EXHS}, t_{EXLS}				13.7			μs
TI00 to TI03 input high-level width, low-level width	t_{TIH}, t_{TIL}				$1/f_{MCK}$ + 10			ns

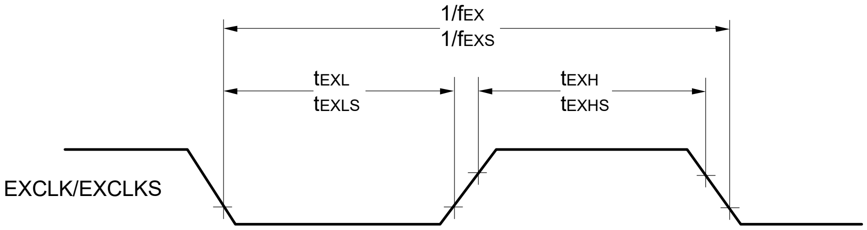
Remark f_{MCK}: Timer array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of timer mode register mn (TMRmn). m: Unit number (m = 0), n: Channel number (n = 0 to 3))

(T_A = -40 to +85°C, 1.6 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V)
(T_A = +85 to +105°C, 2.4 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V) **(2/2)**

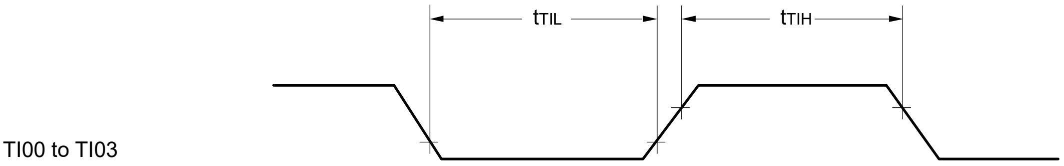
Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
TO00 to TO03 output frequency	f_{TO}	HS (high-speed main) mode	2.7 V ≤ V_{DD} ≤ 3.6 V			8	MHz
			2.4 V ≤ V_{DD} < 2.7 V			4	
		LS (low-speed main) mode	1.8 V ≤ V_{DD} ≤ 3.6 V			4	
		LP (low-power main) mode	1.8 V ≤ V_{DD} ≤ 3.6 V			0.5	
		LV (low-voltage main) mode	1.6 V ≤ V_{DD} ≤ 3.6 V			2	
PCLBUZ0, PCLBUZ1 output frequency	f_{PCL}	HS (high-speed main) mode	2.7 V ≤ V_{DD} ≤ 3.6 V			8	MHz
			2.4 V ≤ V_{DD} < 2.7 V			4	
		LS (low-speed main) mode	1.8 V ≤ V_{DD} ≤ 3.6 V			4	
		LP (low-power main) mode	1.8 V ≤ V_{DD} ≤ 3.6 V			1	
		LV (low-voltage main) mode	1.8 V ≤ V_{DD} ≤ 3.6 V			4	
			1.6 V ≤ V_{DD} < 1.8 V			2	
Interrupt input high-level width, low-level width	t_{INTH}, t_{INTL}	INTP0 to INTP6	1.6 V ≤ V_{DD} ≤ 3.6 V	1			μs
Key interrupt input low-level width	t_{KR}	KR0 to KR3	1.8 V ≤ V_{DD} ≤ 3.6 V	250			ns
			1.6 V ≤ V_{DD} < 1.8 V	1			μs
$\overline{\text{RESET}}$ low-level width	t_{RSL}			10			μs

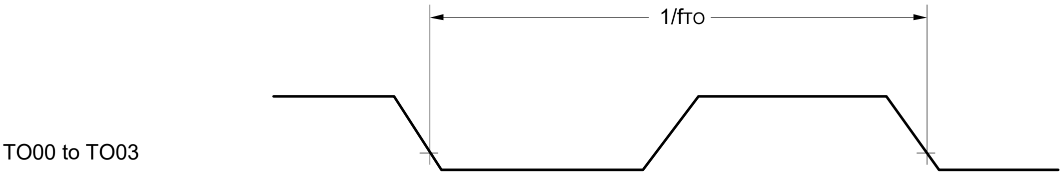
AC Timing Test Points

External System Clock Timing

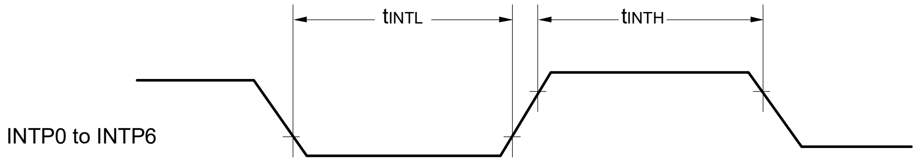


TI/TO Timing

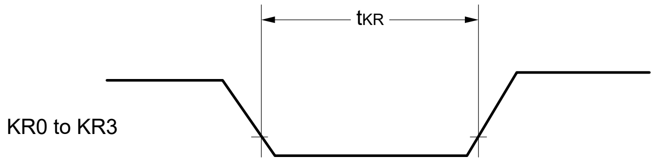




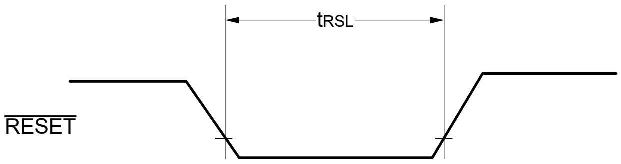
Interrupt Request Input Timing



Key Interrupt Input Timing



$\overline{\text{RESET}}$ Input Timing



2.5 Peripheral Functions Characteristics

AC Timing Test Points

2.5.1 Serial array unit

(1) During communication at same potential (UART mode)

(T_A = -40 to +85°C, 1.6 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LP (Low-power main) mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate Note 1		2.4 V ≤ V_{DD} ≤ 3.6 V			f_{MCK}/6		f_{MCK}/6		f_{MCK}/6		f_{MCK}/6	bps
			Theoretical value of the maximum transfer rate f_{MCK} = f_{CLK} Note 2		4.0		1.3		0.1		0.6	Mbps
		1.8 V ≤ V_{DD} ≤ 3.6 V		—			f_{MCK}/6		f_{MCK}/6		f_{MCK}/6	bps
			Theoretical value of the maximum transfer rate f_{MCK} = f_{CLK} Note 2	—			1.3		0.1		0.6	Mbps
		1.7 V ≤ V_{DD} ≤ 3.6 V		—		—		—			f_{MCK}/6	bps
			Theoretical value of the maximum transfer rate f_{MCK} = f_{CLK} Note 2	—		—		—			0.6	Mbps
		1.6 V ≤ V_{DD} ≤ 3.6 V		—		—		—			f_{MCK}/6	bps
			Theoretical value of the maximum transfer rate f_{MCK} = f_{CLK} Note 2	—		—		—			0.6	Mbps

Note 1. Transfer rate in the SNOOZE mode is 4800 bps only.

Note 2. The maximum operating frequencies of the CPU/peripheral hardware clock (f_{CLK}) are:

HS (high-speed main) mode:	24 MHz (2.7 V ≤ V_{DD} ≤ 3.6 V)
	16 MHz (2.4 V ≤ V_{DD} ≤ 3.6 V)
LS (low-speed main) mode:	8 MHz (1.8 V ≤ V_{DD} ≤ 3.6 V)
LP (low-power main) mode:	1 MHz (1.8 V ≤ V_{DD} ≤ 3.6 V)
LV (low-voltage main) mode:	4 MHz (1.6 V ≤ V_{DD} ≤ 3.6 V)

Caution **Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).**

(T_A = +85 to +105°C, 2.4 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		Unit
				MIN.	MAX.	
Transfer rate Note 1		2.4 V ≤ V_{DD} ≤ 3.6 V			f_{MCK}/12	bps
			Theoretical value of the maximum transfer rate f_{MCK} = f_{CLK} Note 2		2.0	Mbps

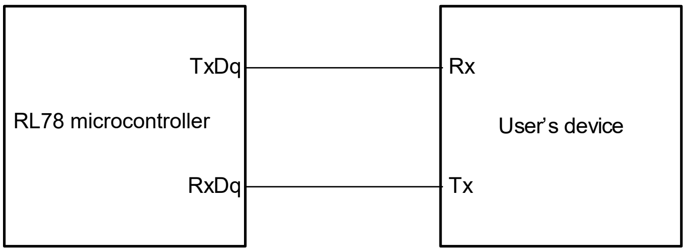
Note 1. Transfer rate in the SNOOZE mode is 4800 bps only.

Note 2. The maximum operating frequencies of the CPU/peripheral hardware clock (f_{CLK}) are:

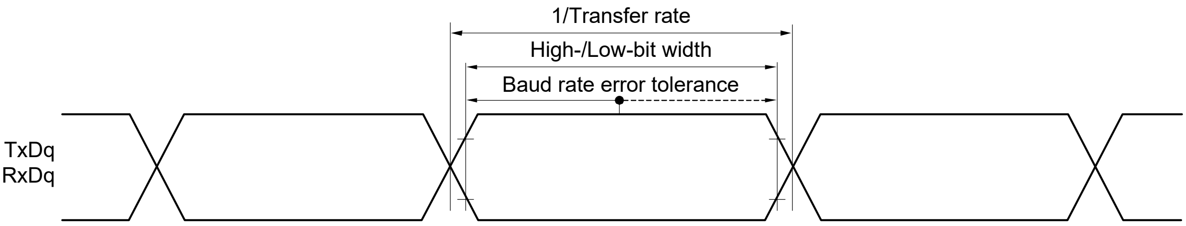
HS (high-speed main) mode:	24 MHz (2.7 V ≤ V_{DD} ≤ 3.6 V)
	16 MHz (2.4 V ≤ V_{DD} ≤ 3.6 V)

Caution **Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).**

UART mode connection diagram (during communication at same potential)



UART mode bit width (during communication at same potential) (reference)



Remark 1. q: UART number (q = 0), g: PIM and POM number (g = 5)

Remark 2. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01))

(2) During communication at same potential (simplified SPI (CSI) mode) (master mode, SCKp... internal clock output, corresponding CSI00 only)

(T_A = -40 to +85°C, 2.7 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LP (Low-power main) mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	t_{KCY1}	t_{KCY1} ≥ f_{CLK}/2	83.3		250		2000		500		ns
SCKp high-/low-level width	t_{KL1}		t_{KCY1}/2 - 10		t_{KCY1}/2 - 50		t_{KCY1}/2 - 50		t_{KCY1}/2 - 50		ns
SIp setup time (to SCKp↑) Note 1	t_{SIK1}		33		110		110		110		ns
SIp hold time (from SCKp↑) Note 2	t_{KSI1}		10		10		10		10		ns
Delay time from SCKp↓ to SOp output Note 3	t_{KSO1}	C = 20 pF Note 4		10		20		20		20	ns

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes “to SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes “from SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes “from SCKp↑” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 4. C is the load capacitance of the SCKp and SOp output lines.

Caution **Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).**

Remark 1. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM numbers (g = 5)

Remark 2. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
n: Channel number (mn = 00))

(3) During communication at same potential (simplified SPI (CSI) mode) (master mode, SCKp... internal clock output)

(T_A = -40 to +85°C, 1.6 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LP (Low-power main) mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	t_{KCY1}	t_{KCY1} ≥ f_{CLK}/4	2.7 V ≤ V_{DD} ≤ 3.6 V	167		500		4000		1000		ns
			2.4 V ≤ V_{DD} ≤ 3.6 V	250								
			1.8 V ≤ V_{DD} ≤ 3.6 V	—								
			1.7 V ≤ V_{DD} ≤ 3.6 V	—		—		—				
			1.6 V ≤ V_{DD} ≤ 3.6 V	—		—		—				
SCKp high-/low-level width	t_{KH1}, t_{KL1}	2.7 V ≤ V_{DD} ≤ 3.6 V		t_{KCY1}/2 - 18		t_{KCY1}/2 - 50		t_{KCY1}/2 - 50		t_{KCY1}/2 - 50		ns
		2.4 V ≤ V_{DD} ≤ 3.6 V		t_{KCY1}/2 - 38								
		1.8 V ≤ V_{DD} ≤ 3.6 V		—								
		1.7 V ≤ V_{DD} ≤ 3.6 V		—		—		—		t_{KCY1}/2 - 100		
		1.6 V ≤ V_{DD} ≤ 3.6 V		—		—		—				
SIp setup time (to SCKp↑) Note 1	t_{SIK1}	2.7 V ≤ V_{DD} ≤ 3.6 V		58		110		110		110		ns
		2.4 V ≤ V_{DD} ≤ 3.6 V		75								
		1.8 V ≤ V_{DD} ≤ 3.6 V		—								
		1.7 V ≤ V_{DD} ≤ 3.6 V		—		—		—		220		
		1.6 V ≤ V_{DD} ≤ 3.6 V		—		—		—				
SIp hold time (from SCKp↑) Note 2	t_{KSI1}	2.4 V ≤ V_{DD} ≤ 3.6 V		19		19		19		19		ns
		1.8 V ≤ V_{DD} ≤ 3.6 V		—								
		1.6 V ≤ V_{DD} ≤ 3.6 V		—		—		—				
Delay time from SCKp↓ to SOp output Note 3	t_{KSO1}	C = 30 pF Note 4	2.4 V ≤ V_{DD} ≤ 3.6 V		33.4		33.4		33.4		33.4	ns
			1.8 V ≤ V_{DD} ≤ 3.6 V		—							
			1.6 V ≤ V_{DD} ≤ 3.6 V		—		—		—			

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 4. C is the load capacitance of the SCKp and SOp output lines.

Caution **Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).**

Remark 1. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM numbers (g = 5)

Remark 2. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
n: Channel number (mn = 00, 01))

(3) During communication at same potential (simplified SPI (CSI) mode) (master mode, SCKp... internal clock output)

(T_A = +85 to +105°C, 2.7 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		Unit
				MIN.	MAX.	
SCKp cycle time	t_{KCY1}	$t_{KCY1} \geq f_{CLK}/4$	2.7 V ≤ V_{DD} ≤ 3.6 V	250		ns
			2.4 V ≤ V_{DD} ≤ 3.6 V	500		ns
SCKp high-/low-level width	t_{KH1}, t_{KL1}	2.7 V ≤ V_{DD} ≤ 3.6 V		$t_{KCY1}/2 - 36$		ns
		2.4 V ≤ V_{DD} ≤ 3.6 V		$t_{KCY1}/2 - 76$		ns
SIp setup time (to SCKp↑) Note 1	t_{SIK1}	2.7 V ≤ V_{DD} ≤ 3.6 V		66		ns
		2.4 V ≤ V_{DD} ≤ 3.6 V		133		ns
SIp hold time (from SCKp↑) Note 2	t_{KSI1}			38		ns
Delay time from SCKp↓ to SOp output Note 3	t_{KSO1}	C = 30 pF Note 4			50	ns

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes “to SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes “from SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes “from SCKp↑” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 4. C is the load capacitance of the SCKp and SOp output lines.

Caution **Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).**

Remark 1. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM numbers (g = 5)

Remark 2. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
n: Channel number (mn = 00, 01))

(4) During communication at same potential (simplified SPI (CSI) mode) (slave mode, SCKp... external clock input)

(T_A = -40 to +85°C, 1.6 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V) **(1/2)**

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LP (Low-power main) mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time Note 5	t_{KCY2}	2.7 V ≤ V_{DD} ≤ 3.6 V	f_{MCK} > 16 MHz	8/f_{MCK}		—	—	—	—	—	—	ns
			f_{MCK} ≤ 16 MHz	6/f_{MCK}		6/f_{MCK}		6/f_{MCK}		6/f_{MCK}		
		2.4 V ≤ V_{DD} ≤ 3.6 V		6/f_{MCK} and 500		6/f_{MCK}		6/f_{MCK}		6/f_{MCK}		
		1.8 V ≤ V_{DD} ≤ 3.6 V		—		6/f_{MCK}		6/f_{MCK}		6/f_{MCK}		
		1.7 V ≤ V_{DD} ≤ 3.6 V		—		—		—				
		1.6 V ≤ V_{DD} ≤ 3.6 V		—		—		—				
SCKp high-/low-level width	t_{KH2}, t_{KL2}	2.7 V ≤ V_{DD} ≤ 3.6 V		t_{KCY2}/2 - 8		t_{KCY2}/2 - 8		t_{KCY2}/2 - 8		t_{KCY2}/2 - 8		ns
		2.4 V ≤ V_{DD} ≤ 3.6 V		t_{KCY2}/2 - 18		t_{KCY2}/2 - 18		t_{KCY2}/2 - 18		t_{KCY2}/2 - 18		
		1.8 V ≤ V_{DD} ≤ 3.6 V		—								
		1.7 V ≤ V_{DD} ≤ 3.6 V		—		—		—		t_{KCY2}/2 - 66		
		1.6 V ≤ V_{DD} ≤ 3.6 V		—		—		—				
SIp setup time (to SCKp↑) Note 1	t_{SIK2}	2.7 V ≤ V_{DD} ≤ 3.6 V		1/f_{MCK} + 20		1/f_{MCK} + 30		1/f_{MCK} + 30		1/f_{MCK} + 30		ns
		2.4 V ≤ V_{DD} ≤ 3.6 V		1/f_{MCK} + 30								
		1.8 V ≤ V_{DD} ≤ 3.6 V		—								
		1.7 V ≤ V_{DD} ≤ 3.6 V		—		—		—		1/f_{MCK} + 40		
		1.6 V ≤ V_{DD} ≤ 3.6 V		—		—		—				
SIp hold time (from SCKp↑) Note 2	t_{KSI2}	2.4 V ≤ V_{DD} ≤ 3.6 V		1/f_{MCK} + 31		1/f_{MCK} + 31		1/f_{MCK} + 31		1/f_{MCK} + 31		ns
		1.8 V ≤ V_{DD} ≤ 3.6 V		—								
		1.7 V ≤ V_{DD} ≤ 3.6 V		—		—		—		1/f_{MCK} + 250		
		1.6 V ≤ V_{DD} ≤ 3.6 V		—		—		—				
Delay time from SCKp↓ to SOp output Note 3	t_{KSO2}	C = 30 pF Note 4	2.7 V ≤ V_{DD} ≤ 3.6 V		2/f_{MCK} + 44		2/f_{MCK} + 110		2/f_{MCK} + 110		2/f_{MCK} + 110	ns
			2.4 V ≤ V_{DD} ≤ 3.6 V		2/f_{MCK} + 75							
			1.8 V ≤ V_{DD} ≤ 3.6 V		—							
			1.7 V ≤ V_{DD} ≤ 3.6 V		—		—		—		2/f_{MCK} + 220	
			1.6 V ≤ V_{DD} ≤ 3.6 V		—		—		—			

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes “to SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes “from SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes “from SCKp↑” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 4. C is the load capacitance of the SOp output lines.

Note 5. The maximum transfer rate when using the SNOOZE mode is 1 Mbps.

Caution **Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).**

Remark 1. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM numbers (g = 5)

Remark 2. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
n: Channel number (mn = 00, 01))

(4) During communication at same potential (simplified SPI (CSI) mode) (slave mode, SCKp... external clock input)

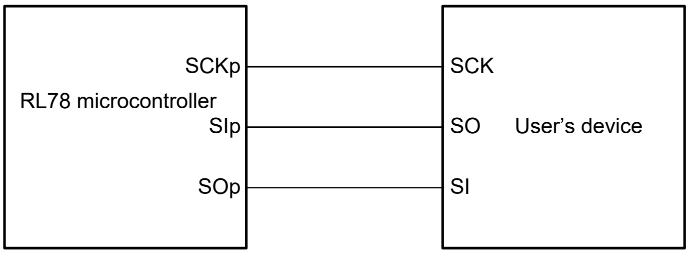
(T_A = -40 to +85°C, 1.6 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V) (2/2)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LP (Low-power main) mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
$\overline{\text{SSI00}}$ setup time	t_{SSIK}	DAPmn = 0	2.7 V ≤ V_{DD} ≤ 3.6 V	120		120		120		120		ns
			2.4 V ≤ V_{DD} < 2.7 V	200		200		200		200		
			1.8 V ≤ V_{DD} < 2.4 V	—								
			1.6 V ≤ V_{DD} < 1.8 V	—		—		—		400		
		DAPmn = 1	2.7 V ≤ V_{DD} ≤ 3.6 V	$1/f_{MCK}$ + 120		$1/f_{MCK}$ + 120		$1/f_{MCK}$ + 120		$1/f_{MCK}$ + 120		ns
			2.4 V ≤ V_{DD} < 2.7 V	$1/f_{MCK}$ + 200		$1/f_{MCK}$ + 200		$1/f_{MCK}$ + 200		$1/f_{MCK}$ + 200		
			1.8 V ≤ V_{DD} < 2.4 V	—								
			1.6 V ≤ V_{DD} < 1.8 V	—		—		—		$1/f_{MCK}$ + 400		
$\overline{\text{SSI00}}$ hold time	t_{KSSI}	DAPmn = 0	2.7 V ≤ V_{DD} ≤ 3.6 V	$1/f_{MCK}$ + 120		$1/f_{MCK}$ + 120		$1/f_{MCK}$ + 120		$1/f_{MCK}$ + 120		ns
			2.4 V ≤ V_{DD} < 2.7 V	$1/f_{MCK}$ + 200		$1/f_{MCK}$ + 200		$1/f_{MCK}$ + 200		$1/f_{MCK}$ + 200		
			1.8 V ≤ V_{DD} < 2.4 V	—								
			1.6 V ≤ V_{DD} < 1.8 V	—		—		—		$1/f_{MCK}$ + 400		
		DAPmn = 1	2.7 V ≤ V_{DD} ≤ 3.6 V	120		120		120		120		ns
			2.4 V ≤ V_{DD} < 2.7 V	200		200		200		200		
			1.8 V ≤ V_{DD} < 2.4 V	—								
			1.6 V ≤ V_{DD} < 1.8 V	—		—		—		400		

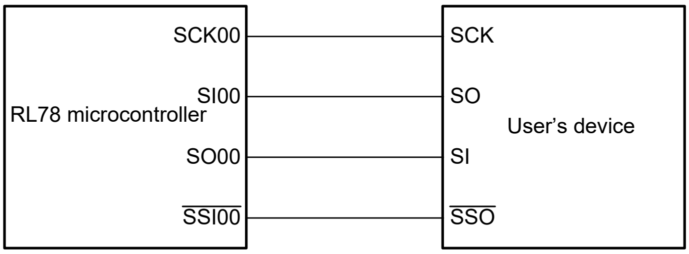
Caution **Select the normal input buffer for the SIp pin and SCKp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).**

Remark p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM numbers (g = 5)

Simplified SPI (CSI) mode connection diagram (during communication at same potential)



Simplified SPI (CSI) mode connection diagram (during communication at same potential)
(Slave Transmission of slave select input function (CSI00))



Remark 1. p: CSI number (p = 00, 01)
Remark 2. m: Unit number, n: Channel number (mn = 00, 01)

(4) During communication at same potential (simplified SPI (CSI) mode) (slave mode, SCKp... external clock input)

(T_A = +85 to +105°C, 2.4 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V) **(1/2)**

Parameter	Symbol	Conditions		HS (high-speed main) Mode		Unit
				MIN.	MAX.	
SCKp cycle time Note 5	t_{KCY2}	2.7 V ≤ V_{DD} < 3.6 V	f_{MCK} > 16 MHz	16/f_{MCK}		ns
			f_{MCK} ≤ 16 MHz	12/f_{MCK}		ns
		2.4 V ≤ V_{DD} < 2.7 V		12/f_{MCK} and 1000		ns
SCKp high-/low-level width	t_{KH2}, t_{KL2}	2.7 V ≤ V_{DD} ≤ 3.6 V		t_{KCY2}/2 - 16		ns
		2.4 V ≤ V_{DD} < 2.7 V		t_{KCY2}/2 - 36		ns
SIp setup time (to SCKp↑) Note 1	t_{SIK2}	2.7 V ≤ V_{DD} ≤ 3.6 V		1/f_{MCK} + 40		ns
		2.4 V ≤ V_{DD} < 2.7 V		1/f_{MCK} + 60		ns
SIp hold time (from SCKp↑) Note 2	t_{KSI2}			1/f_{MCK} + 62		ns
Delay time from SCKp↓ to SOp output Note 3	t_{KSO2}	C = 30 pF Note 4	2.7 V ≤ V_{DD} ≤ 3.6 V		2/f_{MCK} + 66	ns
			2.4 V ≤ V_{DD} < 2.7 V		2/f_{MCK} + 113	ns

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes “to SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes “from SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes “from SCKp↑” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 4. C is the load capacitance of the SOp output lines.

Note 5. The maximum transfer rate when using the SNOOZE mode is 1 Mbps.

Caution **Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).**

Remark 1. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM numbers (g = 5)

Remark 2. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
n: Channel number (mn = 00, 01))

(4) During communication at same potential (simplified SPI (CSI) mode) (slave mode, SCKp... external clock input)

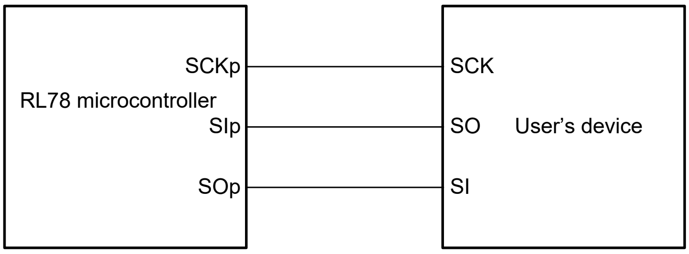
(T_A = +85 to +105°C, 2.4 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V) **(2/2)**

Parameter	Symbol	Conditions		HS (high-speed main) Mode		Unit
				MIN.	MAX.	
$\overline{\text{SSI00}}$ setup time	t_{SSIK}	DAPmn = 0	2.7 V ≤ V_{DD} ≤ 3.6 V	240		ns
			2.4 V ≤ V_{DD} < 2.7 V	400		ns
		DAPmn = 1	2.7 V ≤ V_{DD} ≤ 3.6 V	$1/f_{MCK}$ + 240		ns
			2.4 V ≤ V_{DD} < 2.7 V	$1/f_{MCK}$ + 400		ns
$\overline{\text{SSI00}}$ hold time	t_{KSSI}	DAPmn = 0	2.7 V ≤ V_{DD} ≤ 3.6 V	$1/f_{MCK}$ + 240		ns
			2.4 V ≤ V_{DD} < 2.7 V	$1/f_{MCK}$ + 400		ns
		DAPmn = 1	2.7 V ≤ V_{DD} ≤ 3.6 V	240		ns
			2.4 V ≤ V_{DD} < 2.7 V	400		ns

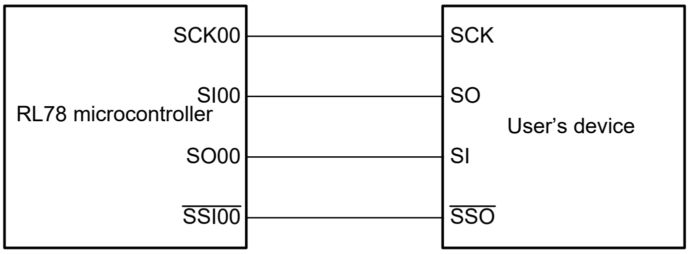
Caution **Select the normal input buffer for the SIp pin and SCKp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).**

Remark p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM numbers (g = 5)

Simplified SPI (CSI) mode connection diagram (during communication at same potential)

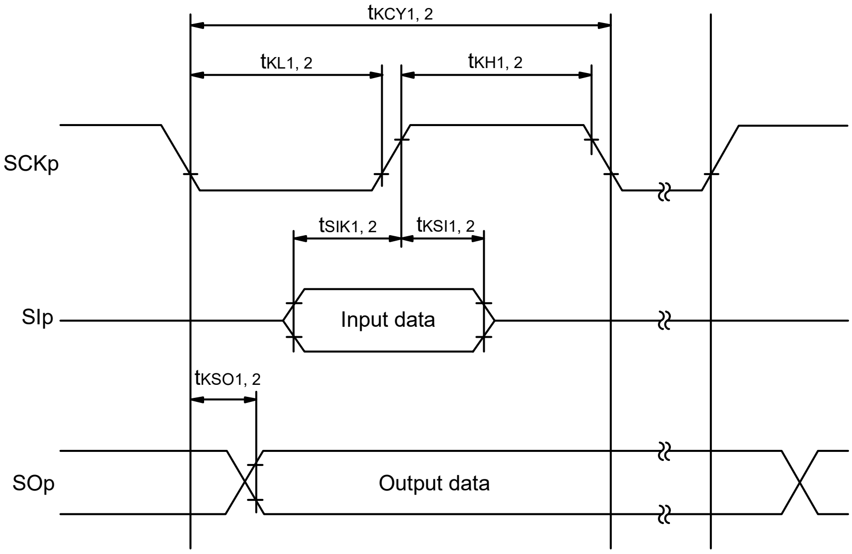


Simplified SPI (CSI) mode connection diagram (during communication at same potential)
(Slave Transmission of slave select input function (CSI00))

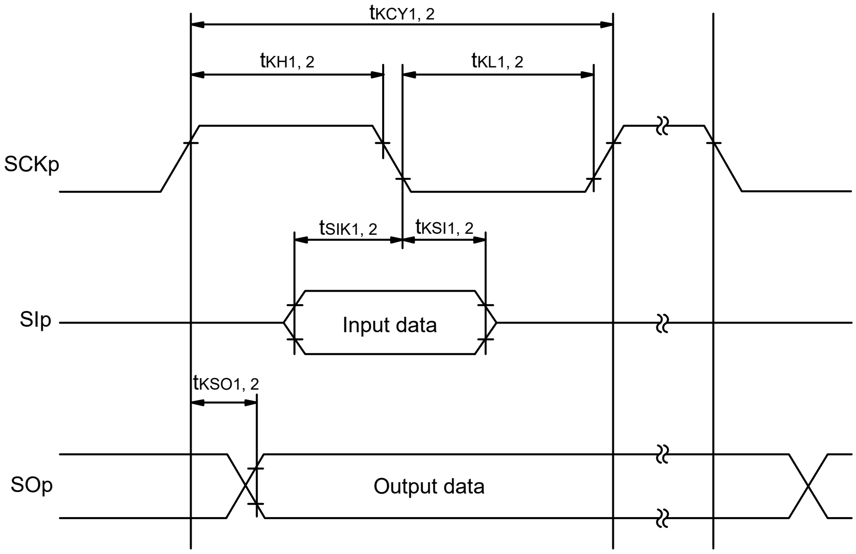


Remark 1. p: CSI number (p = 00, 01)
Remark 2. m: Unit number, n: Channel number (mn = 00, 01)

Simplified SPI (CSI) mode serial transfer timing (during communication at same potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



Simplified SPI (CSI) mode serial transfer timing (during communication at same potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remark 1. p: CSI number (p = 00, 01)
Remark 2. m: Unit number, n: Channel number (mn = 00, 01)

(5) During communication at same potential (simplified I²C mode)

(T_A = -40 to +85°C, 1.6 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LP (Low-power main) mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLr clock frequency	f_{SCL}	2.7 V ≤ V_{DD} ≤ 3.6 V, C_b = 50 pF, R_b = 2.7 kΩ		1000 Note 1		400 Note 1		250 Note 1		400 Note 1	kHz
		1.8 V ≤ V_{DD} ≤ 3.6 V, C_b = 100 pF, R_b = 3 kΩ		—							
		1.8 V ≤ V_{DD} < 2.7 V, C_b = 100 pF, R_b = 5 kΩ		—		300 Note 1		250 Note 1		300 Note 1	
		1.7 V ≤ V_{DD} < 1.8 V, C_b = 100 pF, R_b = 5 kΩ		—		—		—		250 Note 1	
		1.6 V ≤ V_{DD} < 1.8 V, C_b = 100 pF, R_b = 5 kΩ		—		—		—			
Hold time when SCLr = "L"	t_{LOW}	2.7 V ≤ V_{DD} ≤ 3.6 V, C_b = 50 pF, R_b = 2.7 kΩ	475		1150		1150		1150		ns
		1.8 V ≤ V_{DD} ≤ 3.6 V, C_b = 100 pF, R_b = 3 kΩ	—								
		1.8 V ≤ V_{DD} < 2.7 V, C_b = 100 pF, R_b = 5 kΩ	—		1550		1550		1550		
		1.7 V ≤ V_{DD} < 1.8 V, C_b = 100 pF, R_b = 5 kΩ	—		—		—		1850		
		1.6 V ≤ V_{DD} < 1.8 V, C_b = 100 pF, R_b = 5 kΩ	—		—		—				
Hold time when SCLr = "H"	t_{HIGH}	2.7 V ≤ V_{DD} ≤ 3.6 V, C_b = 50 pF, R_b = 2.7 kΩ	475		1150		1150		1150		ns
		1.8 V ≤ V_{DD} ≤ 3.6 V, C_b = 100 pF, R_b = 3 kΩ	—								
		1.8 V ≤ V_{DD} < 2.7 V, C_b = 100 pF, R_b = 5 kΩ	—		1550		1550		1550		
		1.7 V ≤ V_{DD} < 1.8 V, C_b = 100 pF, R_b = 5 kΩ	—		—		—		1850		
		1.6 V ≤ V_{DD} < 1.8 V, C_b = 100 pF, R_b = 5 kΩ	—		—		—				
Data setup time (reception)	$t_{SU:DAT}$	2.7 V ≤ V_{DD} ≤ 3.6 V, C_b = 50 pF, R_b = 2.7 kΩ	$1/f_{MCK}$ + 85 Note 2		$1/f_{MCK}$ + 145 Note 2		$1/f_{MCK}$ + 145 Note 2		$1/f_{MCK}$ + 145 Note 2		ns
		1.8 V ≤ V_{DD} ≤ 3.6 V, C_b = 100 pF, R_b = 3 kΩ	—								
		1.8 V ≤ V_{DD} < 2.7 V, C_b = 100 pF, R_b = 5 kΩ	—		$1/f_{MCK}$ + 230 Note 2		$1/f_{MCK}$ + 230 Note 2		$1/f_{MCK}$ + 230 Note 2		
		1.7 V ≤ V_{DD} < 1.8 V, C_b = 100 pF, R_b = 5 kΩ	—		—		—		$1/f_{MCK}$ + 290 Note 2		
		1.6 V ≤ V_{DD} < 1.8 V, C_b = 100 pF, R_b = 5 kΩ	—		—		—				
Data hold time (transmission)	$t_{HD:DAT}$	2.7 V ≤ V_{DD} ≤ 3.6 V, C_b = 50 pF, R_b = 2.7 kΩ	0	305	0	305	0	305	0	305	ns
		1.8 V ≤ V_{DD} ≤ 3.6 V, C_b = 100 pF, R_b = 3 kΩ	—	—		355		355		355	
		1.8 V ≤ V_{DD} < 2.7 V, C_b = 100 pF, R_b = 5 kΩ	—	—							
		1.7 V ≤ V_{DD} < 1.8 V, C_b = 100 pF, R_b = 5 kΩ	—	—	—	—	—	—		405	
		1.6 V ≤ V_{DD} < 1.8 V, C_b = 100 pF, R_b = 5 kΩ	—	—	—	—	—	—			

(**Notes** and **Caution** are listed on the next page.)

Note 1. The value must also be equal to or less than f_{MCK}/4.

Note 2. Set the f_{MCK} value to keep the hold time of SCLr = “L” and SCLr = “H”.

Caution **Select the normal input buffer and the N-ch open drain output (V_{DD} tolerance) mode for the SDAr pin and the normal output mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register h (POMh).**

(5) During communication at same potential (simplified I^{2}C mode)

(T_A = +85 to +105°C, 2.4 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V)

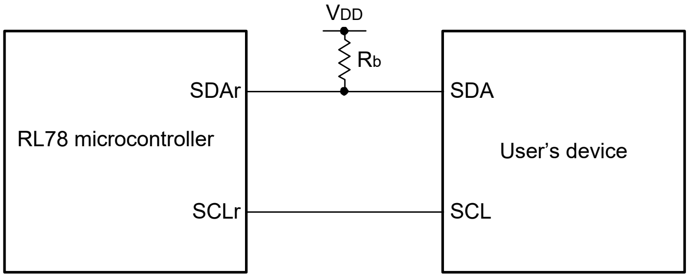
Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
SCLr clock frequency	f_{SCL}	2.7 V ≤ V_{DD} ≤ 3.6 V, C_b = 50 pF, R_b = 2.7 kΩ		400 Note 1	kHz
		2.4 V ≤ V_{DD} ≤ 3.6 V, C_b = 100 pF, R_b = 3 kΩ		100 Note 1	kHz
Hold time when SCLr = “L”	t_{LOW}	2.7 V ≤ V_{DD} ≤ 3.6 V, C_b = 50 pF, R_b = 2.7 kΩ	1200		ns
		2.4 V ≤ V_{DD} ≤ 3.6 V, C_b = 100 pF, R_b = 3 kΩ	4600		ns
Hold time when SCLr = “H”	t_{HIGH}	2.7 V ≤ V_{DD} ≤ 3.6 V, C_b = 50 pF, R_b = 2.7 kΩ	1200		ns
		2.4 V ≤ V_{DD} ≤ 3.6 V, C_b = 100 pF, R_b = 3 kΩ	4600		ns
Data setup time (reception)	$t_{SU:DAT}$	2.7 V ≤ V_{DD} ≤ 3.6 V, C_b = 50 pF, R_b = 2.7 kΩ	1/f_{MCK} + 220 Note 2		ns
		2.4 V ≤ V_{DD} ≤ 3.6 V, C_b = 100 pF, R_b = 3 kΩ	1/f_{MCK} + 580 Note 2		ns
Data hold time (transmission)	$t_{HD:DAT}$	2.7 V ≤ V_{DD} ≤ 3.6 V, C_b = 50 pF, R_b = 2.7 kΩ	0	770	ns
		2.4 V ≤ V_{DD} ≤ 3.6 V, C_b = 100 pF, R_b = 3 kΩ	0	1420	ns

Note 1. The value must also be equal to or less than f_{MCK}/4.

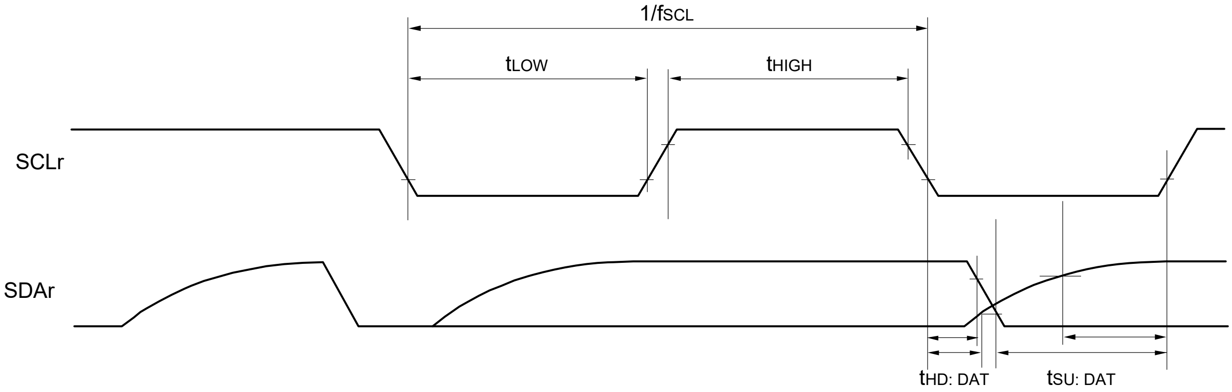
Note 2. Set the f_{MCK} value to keep the hold time of SCLr = “L” and SCLr = “H”.

Caution **Select the normal input buffer and the N-ch open drain output (V_{DD} tolerance) mode for the SDAr pin and the normal output mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register h (POMh).**

Simplified I²C mode connection diagram (during communication at same potential)



Simplified I²C mode serial transfer timing (during communication at same potential)



Remark 1. R_b[Ω]: Communication line (SDAr) pull-up resistance, C_b[F]: Communication line (SDAr, SCLr) load capacitance

Remark 2. r: IIC number (r = 00, 01), g: PIM number (g = 5), h: POM number (h = 5)

Remark 3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0),
n: Channel number (n = 0, 1), mn = 00, 01)

(6) Communication at different potential (1.8 V, 2.5 V) (UART mode) (dedicated baud rate generator output)

(T_A = -40 to +85°C, 1.8 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V) (1/2)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LP (Low-power main) mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate Notes 1, 2		reception	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V		$f_{MCK}/6$ Note 1		$f_{MCK}/6$ Note 1		$f_{MCK}/6$ Note 1		$f_{MCK}/6$ Note 1	bps
			Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}$ Note 3		4.0		1.3		0.1		0.6	Mbps
			1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V		$f_{MCK}/6$ Notes 1, 2		$f_{MCK}/6$ Notes 1, 2		$f_{MCK}/6$ Notes 1, 2		$f_{MCK}/6$ Notes 1, 2	bps
			Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}$ Note 3		4.0		1.3		0.1		0.6	Mbps

Note 1. Transfer rate in the SNOOZE mode is 4,800 bps only.

Note 2. Use it with V_{DD} ≥ Vb.

Note 3. The maximum operating frequencies of the CPU/peripheral hardware clock (f_{CLK}) are:

HS (high-speed main) mode:	24 MHz (2.7 V ≤ V_{DD} ≤ 3.6 V)
	16 MHz (2.4 V ≤ V_{DD} ≤ 3.6 V)
LS (low-speed main) mode:	8 MHz (1.8 V ≤ V_{DD} ≤ 3.6 V)
LP (low-power main) mode:	1 MHz (1.8 V ≤ V_{DD} ≤ 3.6 V)
LV (low-voltage main) mode:	4 MHz (1.6 V ≤ V_{DD} ≤ 3.6 V)

Caution **Select the TTL input buffer for the RxDq pin and the N-ch open drain output (V_{DD} tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.**

Remark 1. V_b[V]: Communication line voltage

Remark 2. q: UART number (q = 0), g: PIM and POM number (g = 5)

Remark 3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01)

(6) Communication at different potential (1.8 V, 2.5 V) (UART mode) (dedicated baud rate generator output)

(T_A = -40 to +85°C, 1.8 V ≤ $AV_{DD} = V_{DD}$ ≤ 3.6 V, $V_{SS} = AV_{SS}$ = 0 V) (2/2)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LP (Low-power main) mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate [Note 2]		Transmission	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V		Note 1		Note 1		Note 1		Note 1	bps
			Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 2.7 kΩ, V_b = 2.3 V		1.2 Note 2		1.2 Note 2		1.2 Note 2		1.2 Note 2	Mbps
			1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V		Notes 3, 4		Notes 3, 4		Notes 3, 4		Notes 3, 4	bps
			Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 5.5 kΩ, V_b = 1.6 V		0.43 Note 5		0.43 Note 5		0.43 Note 5		0.43 Note 5	Mbps

Note 1. The smaller maximum transfer rate derived by using $f_{MCK}/6$ or the following expression is the valid maximum transfer rate.
Expression for calculating the transfer rate when 2.7 V ≤ V_{DD} ≤ 3.6 V and 2.3 V ≤ V_b ≤ 2.7 V

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\} \times 3} \text{ [bps]}$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \text{ [\%]}$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

Note 2. This value as an example is calculated when the conditions described in the "Conditions" column are met.
Refer to Note 1 above to calculate the maximum transfer rate under conditions of the customer.

Note 3. Use it with $V_{DD} \geq V_b$.

Note 4. The smaller maximum transfer rate derived by using $f_{MCK}/6$ or the following expression is the valid maximum transfer rate.
Expression for calculating the transfer rate when 1.8 V ≤ V_{DD} < 3.3 V and 1.6 V ≤ V_b ≤ 2.0 V

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\} \times 3} \text{ [bps]}$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \text{ [\%]}$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

Note 5. This value as an example is calculated when the conditions described in the "Conditions" column are met.
Refer to Note 4 above to calculate the maximum transfer rate under conditions of the customer.

Caution **Select the TTL input buffer for the RxDq pin and the N-ch open drain output (V_{DD} tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.**

(6) Communication at different potential (1.8 V, 2.5 V) (UART mode) (dedicated baud rate generator output)

(T_A = +85 to +105°C, 2.4 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V) **(1/2)**

Parameter	Symbol	Conditions			HS (high-speed main) Mode		Unit
					MIN.	MAX.	
Transfer rate Notes 1, 2		Reception	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V			$f_{MCK}/12$ Note 1	bps
				Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}$ Note 3		2.0	Mbps
			2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V			$f_{MCK}/12$ Notes 1, 2	bps
				Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}$ Note 3		0.66	Mbps

Note 1. Transfer rate in the SNOOZE mode is 4,800 bps only.

Note 2. Use it with V_{DD} ≥ Vb.

Note 3. The maximum operating frequencies of the CPU/peripheral hardware clock (f_{CLK}) are:

HS (high-speed main) mode: 24 MHz (2.7 V ≤ V_{DD} ≤ 3.6 V)
16 MHz (2.4 V ≤ V_{DD} ≤ 3.6 V)

Caution **Select the TTL input buffer for the RxDq pin and the N-ch open drain output (V_{DD} tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.**

Remark 1. V_b[V]: Communication line voltage

Remark 2. q: UART number (q = 0), g: PIM and POM numbers (g = 5)

Remark 3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01)

(6) Communication at different potential (1.8 V, 2.5 V) (UART mode) (dedicated baud rate generator output)

(T_A = +85 to +105°C, 2.4 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V) **(2/2)**

Parameter	Symbol	Conditions			HS (high-speed main) Mode		Unit
					MIN.	MAX.	
Transfer rate Note 2		Transmission	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V			Note 1	bps
				Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 2.7 kΩ, V_b = 2.3 V		1.2 Note 2	Mbps
			2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V			Notes 3, 4	bps
				Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 5.5 kΩ, V_b = 1.6 V		0.43 Note 5	Mbps

Note 1. The smaller maximum transfer rate derived by using $f_{MCK}/6$ or the following expression is the valid maximum transfer rate.
Expression for calculating the transfer rate when 2.7 V ≤ V_{DD} ≤ 3.6 V and 2.3 V ≤ V_b ≤ 2.7 V

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln\left(1 - \frac{2.0}{V_b}\right)\} \times 3} \text{ [bps]}$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln\left(1 - \frac{2.0}{V_b}\right)\}}{\left(\frac{1}{\text{Transfer rate}}\right) \times \text{Number of transferred bits}} \times 100\ [\%]$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

Note 2. This value as an example is calculated when the conditions described in the “Conditions” column are met.
Refer to Note 1 above to calculate the maximum transfer rate under conditions of the customer.

Note 3. Use it with $V_{DD} \geq V_b$.

Note 4. The smaller maximum transfer rate derived by using $f_{MCK}/6$ or the following expression is the valid maximum transfer rate.
Expression for calculating the transfer rate when 2.4 V ≤ V_{DD} < 3.3 V and 1.6 V ≤ V_b ≤ 2.0 V

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln\left(1 - \frac{1.5}{V_b}\right)\} \times 3} \text{ [bps]}$$

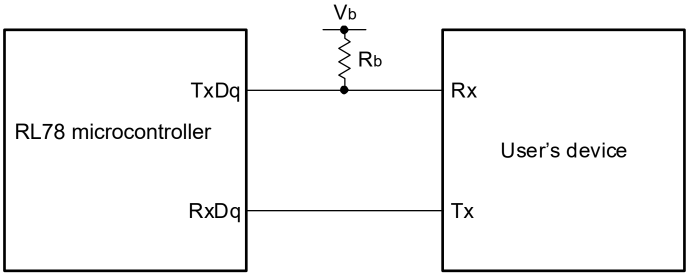
$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln\left(1 - \frac{1.5}{V_b}\right)\}}{\left(\frac{1}{\text{Transfer rate}}\right) \times \text{Number of transferred bits}} \times 100\ [\%]$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

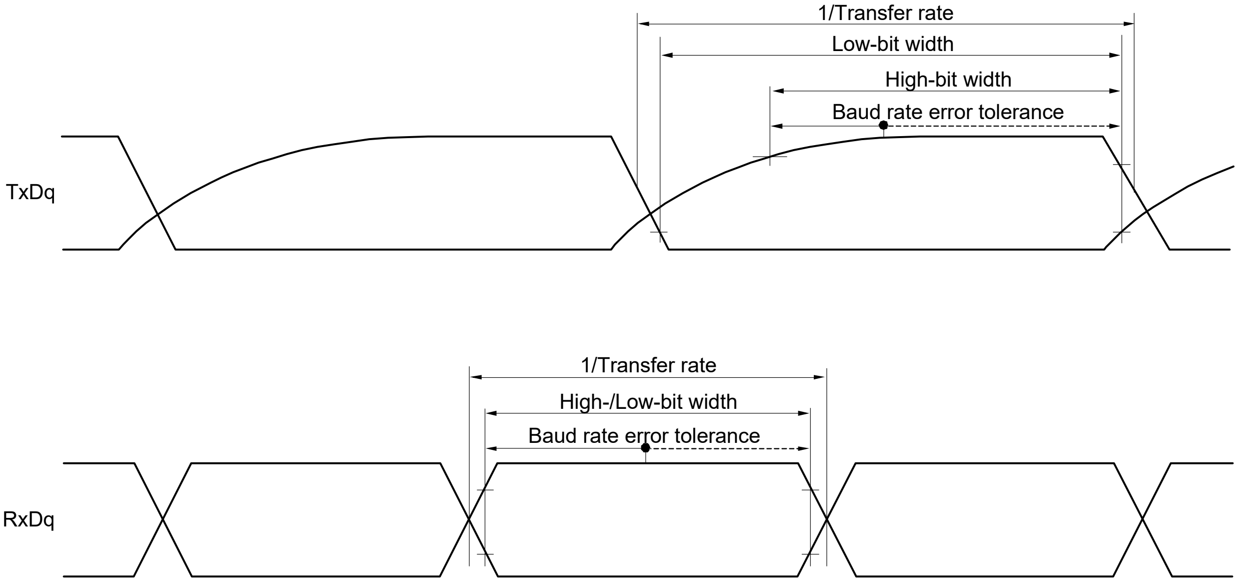
Note 5. This value as an example is calculated when the conditions described in the “Conditions” column are met.
Refer to Note 4 above to calculate the maximum transfer rate under conditions of the customer.

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (V_{DD} tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

UART mode connection diagram (during communication at different potential)



UART mode bit width (during communication at different potential) (reference)



Remark 1. $R_b[\Omega]$: Communication line (TxDq) pull-up resistance, $C_b[F]$: Communication line (TxDq) load capacitance, $V_b[V]$: Communication line voltage

Remark 2. q: UART number (q = 0), g: PIM and POM number (g = 5)

Remark 3. f_{MCK}: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01))

(7) Communication at different potential (2.5 V) (simplified SPI (CSI) mode) (master mode, SCKp... internal clock output, corresponding CSI00 only)

(T_A = -40 to +85°C, 2.7 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LP (Low-power main) mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	t_{KCY1}	t_{KCY1} ≥ f_{CLK}/2 2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ	300		1500		1500		1500		ns
SCKp high-level width	t_{KH1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ	t_{KCY1}/2 - 120		t_{KCY1}/2 - 120		t_{KCY1}/2 - 120		t_{KCY1}/2 - 120		ns
SCKp low-level width	t_{KL1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 1.4 kΩ	t_{KCY1}/2 - 10		t_{KCY1}/2 - 50		t_{KCY1}/2 - 50		t_{KCY1}/2 - 50		ns
SIp setup time (to SCKp↑) Note 1	t_{SIK1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ	121		479		479		479		ns
SIp hold time (from SCKp↑) Note 1	t_{KSI1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ	10		10		10		10		ns
Delay time from SCKp↓ to SOp output Note 1	t_{KSO1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		130		130		130		130	ns
SIp setup time (to SCKp↓) Note 2	t_{SIK1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ	33		110		110		110		ns
SIp hold time (from SCKp↓) Note 2	t_{KSI1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ	10		10		10		10		ns
Delay time from SCKp↑ to SOp output Note 2	t_{KSO1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		10		10		10		10	ns

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.
Note 2. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

Remark 1. R_b[Ω]: Communication line (SCKp, SOp) pull-up resistance, C_b[F]: Communication line (SCKp, SOp) load capacitance, V_b[V]: Communication line voltage

Remark 2. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM number (g = 5)

Remark 3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
n: Channel number (mn = 00))

(8) Communication at different potential (1.8 V, 2.5 V) (simplified SPI (CSI) mode) (master mode, SCKp... internal clock output)

(T_A = -40 to +85°C, 1.8 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V) **(1/2)**

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LP (Low-power main) mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	t_{KCY1}	$t_{KCY1} \geq f_{CLK}/4$	2.7V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	500		1150		1150		1150		ns
			1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note, C_b = 30 pF, R_b = 5.5 kΩ	1150		1150		1150		1150		ns
SCKp high-level width	t_{KH1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		$t_{KCY1}/2$ - 170		$t_{KCY1}/2$ - 170		$t_{KCY1}/2$ - 170		$t_{KCY1}/2$ - 170		ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note, C_b = 30 pF, R_b = 5.5 kΩ		$t_{KCY1}/2$ - 458		$t_{KCY1}/2$ - 458		$t_{KCY1}/2$ - 458		$t_{KCY1}/2$ - 458		ns
SCKp low-level width	t_{KL1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		$t_{KCY1}/2$ - 18		$t_{KCY1}/2$ - 50		$t_{KCY1}/2$ - 50		$t_{KCY1}/2$ - 50		ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note, C_b = 30 pF, R_b = 5.5 kΩ		$t_{KCY1}/2$ - 50		$t_{KCY1}/2$ - 50		$t_{KCY1}/2$ - 50		$t_{KCY1}/2$ - 50		ns

Note Use it with V_{DD} ≥ V_b.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

(**Remarks** are listed on the page after the next page.)

(8) Communication at different potential (1.8 V, 2.5 V) (simplified SPI (CSI) mode) (master mode, SCKp... internal clock output)

(T_A = -40 to +85°C, 1.8 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V) **(2/2)**

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LP (Low-power main) mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SIp setup time (to SCKp↑) Note 1	t_{SIK1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	177		479		479		479		ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 3, C_b = 30 pF, R_b = 5.5 kΩ	479		479		479		479		ns
SIp hold time (from SCKp↑) Note 1	t_{KSI1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	19		19		19		19		ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 3, C_b = 30 pF, R_b = 5.5 kΩ	19		19		19		19		ns
Delay time from SCKp↓ to SOp output Note 1	t_{KSO1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		195		195		195		195	ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 3, C_b = 30 pF, R_b = 5.5 kΩ		483		483		483		483	ns
SIp setup time (to SCKp↓) Note 2	t_{SIK1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	44		110		110		110		ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 3, C_b = 30 pF, R_b = 5.5 kΩ	110		110		110		110		ns
SIp hold time (from SCKp↓) Note 2	t_{KSI1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	19		19		19		19		ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 3, C_b = 30 pF, R_b = 5.5 kΩ	19		19		19		19		ns
Delay time from SCKp↑ to SOp output Note 2	t_{KSO1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		25		25		25		25	ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 3, C_b = 30 pF, R_b = 5.5 kΩ		25		25		25		25	ns

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

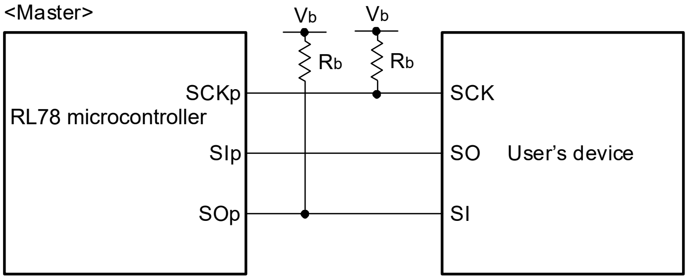
Note 2. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 3. Use it with V_{DD} ≥ V_b.

Caution **Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.**

(**Remarks** are listed on the next page.)

Simplified SPI (CSI) mode connection diagram (during communication at different potential)

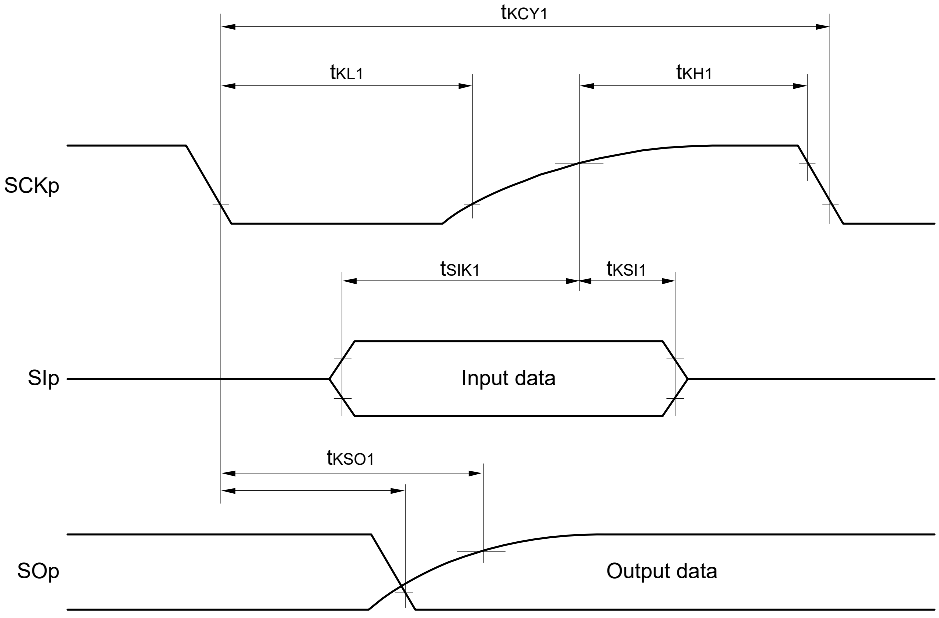


Remark 1. R_b[Ω]: Communication line (SCKp, SOp) pull-up resistance, C_b[F]: Communication line (SCKp, SOp) load capacitance, V_b[V]: Communication line voltage

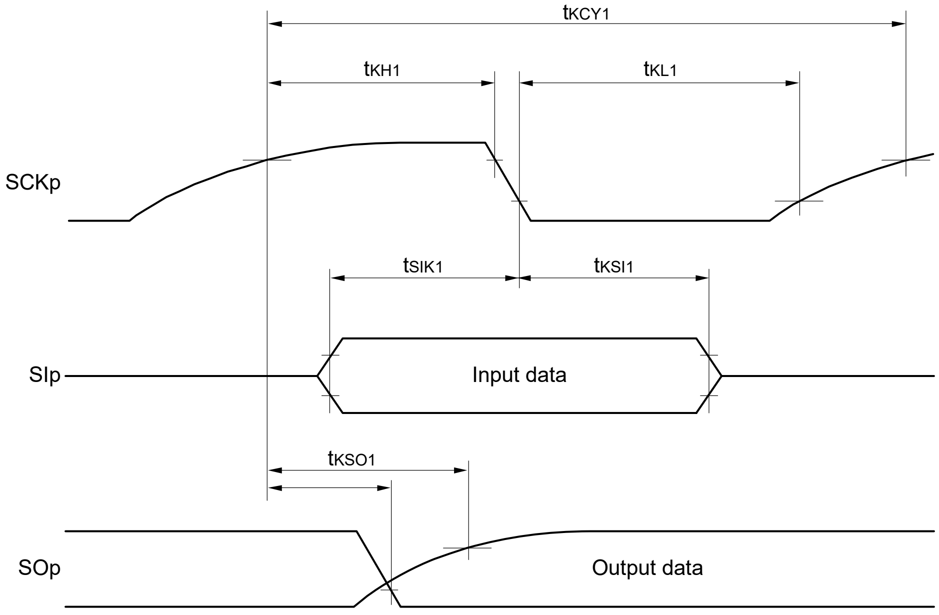
Remark 2. p: CSI number (p = 00, 01), m: Unit number (m = 0), n: Channel number (n = 0, 1), g: PIM and POM numbers (g = 5)

Remark 3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
n: Channel number (mn = 00, 01))

Simplified SPI (CSI) mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



Simplified SPI (CSI) mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remark p: CSI number (p = 00, 01), m: Unit number (m = 0), n: Channel number (n = 0, 1), g: PIM and POM numbers (g = 5)

(8) Communication at different potential (1.8 V, 2.5 V) (simplified SPI (CSI) mode) (master mode, SCKp... internal clock output)

(T_A = +85 to 105°C, 2.4 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V) **(1/2)**

Parameter	Symbol	Conditions		HS (high-speed main) Mode		Unit
				MIN.	MAX.	
SCKp cycle time	t_{KCY1}	$t_{KCY1} \geq f_{CLK}/4$	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	1000		ns
			2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V, C_b = 30 pF, R_b = 5.5 kΩ	2300		ns
SCKp high-level width	t_{KH1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		$t_{KCY1}/2 - 340$		ns
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V, C_b = 30 pF, R_b = 5.5 kΩ		$t_{KCY1}/2 - 916$		ns
SCKp low-level width	t_{KL1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		$t_{KCY1}/2 - 36$		ns
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V, C_b = 30 pF, R_b = 5.5 kΩ		$t_{KCY1}/2 - 100$		ns

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

(**Remarks** are listed on the page after the next page.)

(8) Communication at different potential (1.8 V, 2.5 V) (simplified SPI (CSI) mode) (master mode, SCKp... internal clock output)

(T_A = +85 to 105°C, 2.4 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V) (2/2)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
SIp setup time (to SCKp↑) Note 1	t_{SIK1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	354		ns
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 3, C_b = 30 pF, R_b = 5.5 kΩ	958		ns
SIp hold time (from SCKp↑) Note 1	t_{KSI1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	38		ns
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 3, C_b = 30 pF, R_b = 5.5 kΩ	38		ns
Delay time from SCKp↓ to SOp output Note 1	t_{KSO1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		390	ns
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 3, C_b = 30 pF, R_b = 5.5 kΩ		966	ns
SIp setup time (to SCKp↓) Note 2	t_{SIK1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	88		ns
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 3, C_b = 30 pF, R_b = 5.5 kΩ	220		ns
SIp hold time (from SCKp↓) Note 2	t_{KSI1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	38		ns
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 3, C_b = 30 pF, R_b = 5.5 kΩ	38		ns
Delay time from SCKp↑ to SOp output Note 2	t_{KSO1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		50	ns
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 3, C_b = 30 pF, R_b = 5.5 kΩ		50	ns

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

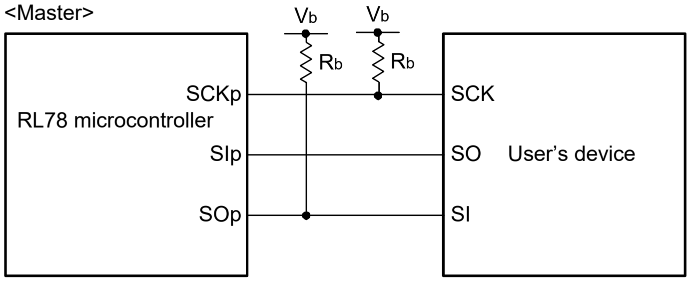
Note 2. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 3. Use it with V_{DD} ≥ V_b.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

(**Remarks** are listed on the next page.)

Simplified SPI (CSI) mode connection diagram (during communication at different potential)

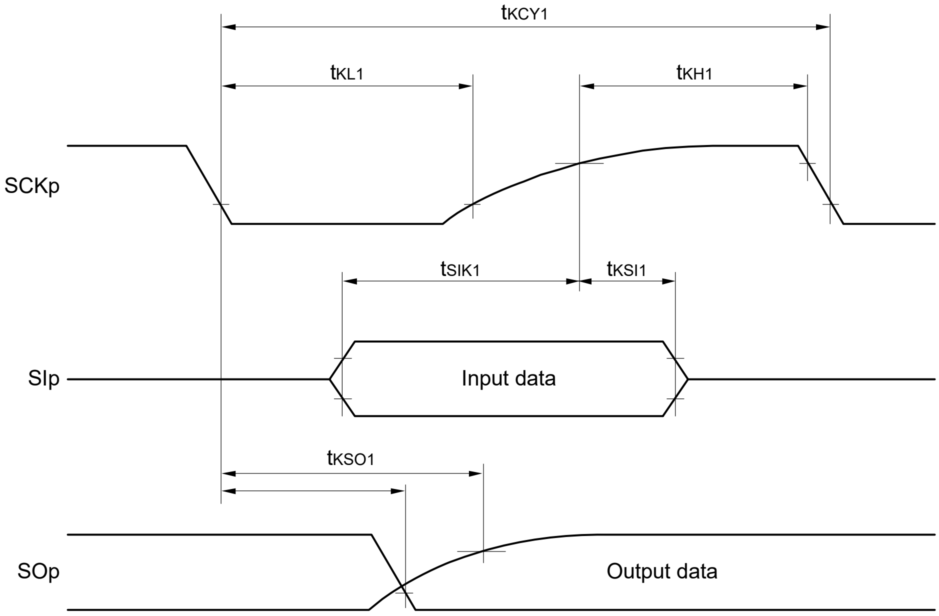


Remark 1. $R_b[\Omega]$: Communication line (SCKp, SOp) pull-up resistance, $C_b[F]$: Communication line (SCKp, SOp) load capacitance, $V_b[V]$: Communication line voltage

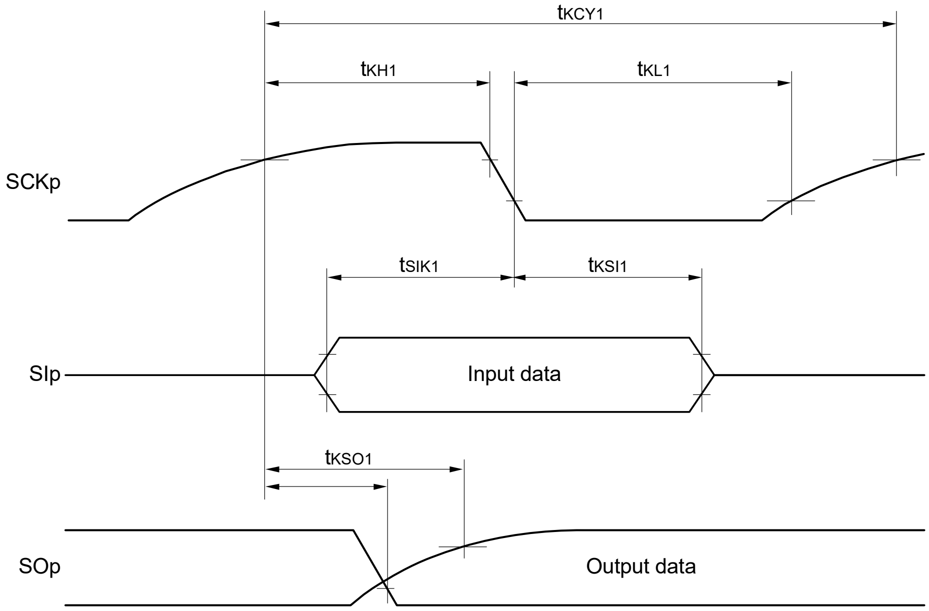
Remark 2. p: CSI number (p = 00, 01), m: Unit number (m = 0), n: Channel number (n = 0, 1), g: PIM and POM numbers (g = 5)

Remark 3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
n: Channel number (mn = 00, 01))

Simplified SPI (CSI) mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



Simplified SPI (CSI) mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remark p: CSI number (p = 00, 01), m: Unit number (m = 0), n: Channel number (n = 0, 1), g: PIM and POM numbers (g = 5)

(9) Communication at different potential (1.8 V, 2.5 V) (simplified SPI (CSI) mode) (slave mode, SCKp... external clock input)

(T_A = -40 to 85°C, 1.8 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LP (Low-power main) mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time Note 1	t_{KCY2}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V	20 MHz < f_{MCK} ≤ 24 MHz	16/f_{MCK}		—		—		—		ns
			16 MHz < f_{MCK} ≤ 20 MHz	14/f_{MCK}		—		—		—		ns
			8 MHz < f_{MCK} ≤ 16 MHz	12/f_{MCK}		—		—		—		ns
			4 MHz < f_{MCK} ≤ 8 MHz	8/f_{MCK}		16/f_{MCK}		—		—		ns
			f_{MCK} ≤ 4 MHz	6/f_{MCK}		10/f_{MCK}		10/f_{MCK}		10/f_{MCK}		ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2	20 MHz < f_{MCK} ≤ 24 MHz	36/f_{MCK}		—		—		—		ns
			16 MHz < f_{MCK} ≤ 20 MHz	32/f_{MCK}		—		—		—		ns
			8 MHz < f_{MCK} ≤ 16 MHz	26/f_{MCK}		—		—		—		ns
			4 MHz < f_{MCK} ≤ 8 MHz	16/f_{MCK}		16/f_{MCK}		—		—		ns
			f_{MCK} ≤ 4 MHz	10/f_{MCK}		10/f_{MCK}		10/f_{MCK}		10/f_{MCK}		ns
SCKp high-/low-level width	t_{KH2}, t_{KL2}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V		t_{KCY2}/2 - 18		t_{KCY2}/2 - 50		t_{KCY2}/2 - 50		t_{KCY2}/2 - 50		ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2		t_{KCY2}/2 - 50		t_{KCY2}/2 - 50		t_{KCY2}/2 - 50		t_{KCY2}/2 - 50		ns
SIp setup time (to SCKp↑) Note 3	t_{SIK2}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V		1/f_{MCK} + 20		1/f_{MCK} + 30		1/f_{MCK} + 30		1/f_{MCK} + 30		ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2		1/f_{MCK} + 30		1/f_{MCK} + 30		1/f_{MCK} + 30		1/f_{MCK} + 30		ns
SIp hold time (from SCKp↑) Note 4	t_{KSI2}			1/f_{MCK} + 31		1/f_{MCK} + 31		1/f_{MCK} + 31		1/f_{MCK} + 31		ns
Delay time from SCKp↓ to SOp output Note 5	t_{KSO2}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ			2/f_{MCK} + 214		2/f_{MCK} + 573		2/f_{MCK} + 573		2/f_{MCK} + 573	ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2, C_b = 30 pF, R_b = 5.5 kΩ			2/f_{MCK} + 573		2/f_{MCK} + 573		2/f_{MCK} + 573		2/f_{MCK} + 573	ns

(**Notes** and **Caution** are listed on the next page. **Remarks** are listed on the page after the next page.)

Note 1. Transfer rate in the SNOOZE mode: MAX. 1 Mbps

Note 2. Use it with $V_{DD} \geq V_b$.

Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes “to SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

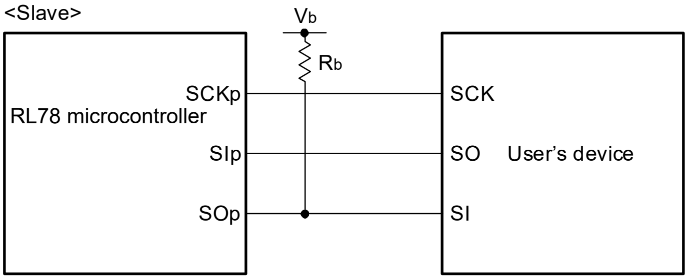
Note 4. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes “from SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 5. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes “from SCKp↑” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Caution **Select the TTL input buffer for the SIp pin and SCKp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.**

(**Remarks** are listed on the next page.)

Simplified SPI (CSI) mode connection diagram (during communication at different potential)

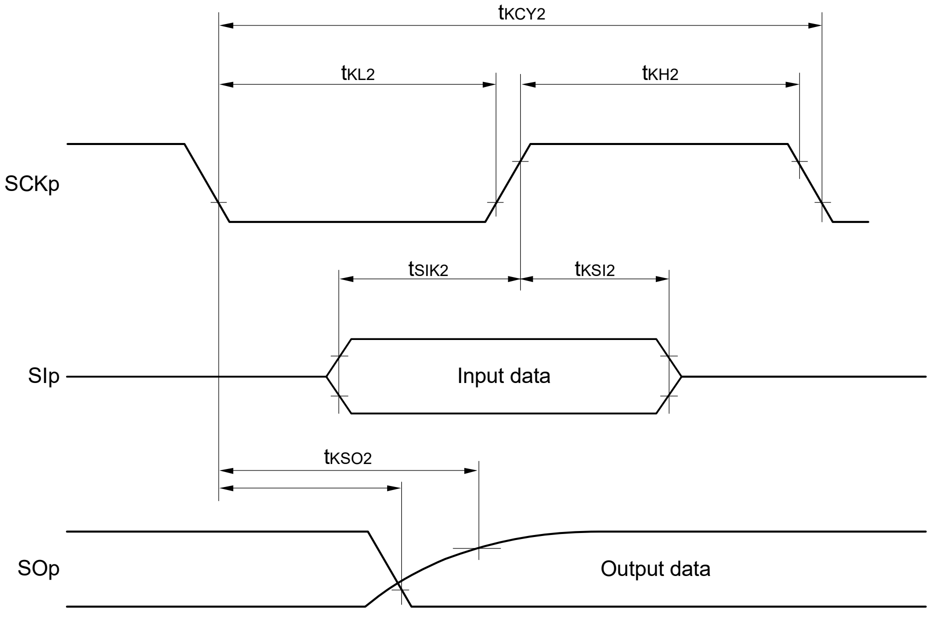


Remark 1. R_b[Ω]: Communication line (SOp) pull-up resistance, C_b[F]: Communication line (SOp) load capacitance, V_b[V]: Communication line voltage

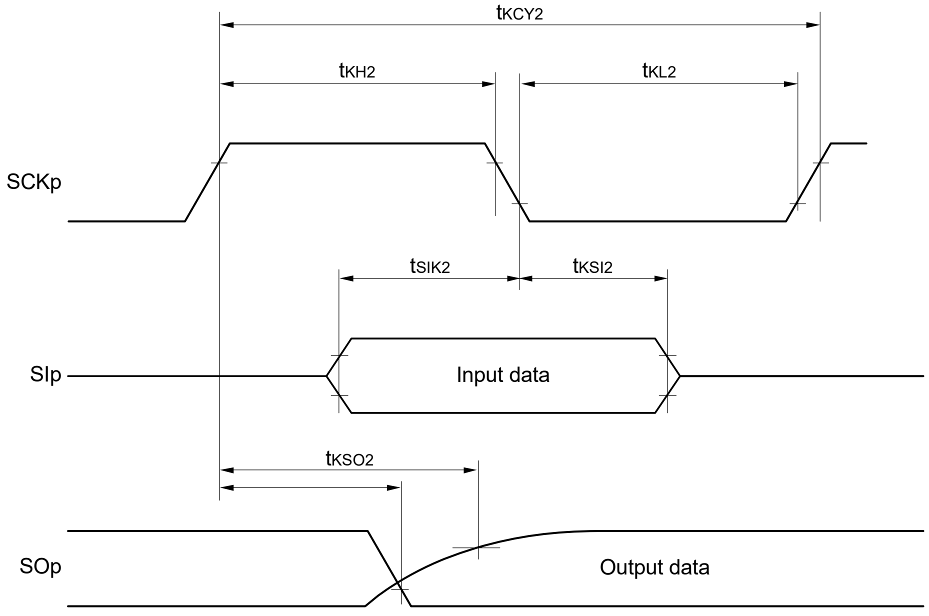
Remark 2. p: CSI number (p = 00, 01), m: Unit number (m = 0), n: Channel number (n = 0, 1), g: PIM and POM numbers (g = 5)

Remark 3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
n: Channel number (mn = 00, 01))

Simplified SPI (CSI) mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



Simplified SPI (CSI) mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remark p: CSI number (p = 00, 01), m: Unit number (m = 0), n: Channel number (n = 0, 1), g: PIM and POM numbers (g = 5)

(9) Communication at different potential (1.8 V, 2.5 V) (simplified SPI (CSI) mode) (slave mode, SCKp... external clock input)

(T_A = +85 to 105°C, 2.4 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		Unit
				MIN.	MAX.	
SCKp cycle time Note 1	t_{KCY2}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V	20 MHz < f_{MCK} ≤ 24 MHz	32/f_{MCK}		ns
			16 MHz < f_{MCK} ≤ 20 MHz	28/f_{MCK}		ns
			8 MHz < f_{MCK} ≤ 16 MHz	24/f_{MCK}		ns
			4 MHz < f_{MCK} ≤ 8 MHz	16/f_{MCK}		ns
			f_{MCK} ≤ 4 MHz	12/f_{MCK}		ns
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2	20 MHz < f_{MCK} ≤ 24 MHz	72/f_{MCK}		ns
			16 MHz < f_{MCK} ≤ 20 MHz	64/f_{MCK}		ns
			8 MHz < f_{MCK} ≤ 16 MHz	52/f_{MCK}		ns
			4 MHz < f_{MCK} ≤ 8 MHz	32/f_{MCK}		ns
			f_{MCK} ≤ 4 MHz	20/f_{MCK}		ns
SCKp high-/low-level width	t_{KH2}, t_{KL2}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V		t_{KCY2}/2 - 36		ns
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2		t_{KCY2}/2 - 100		ns
SIp setup time (to SCKp↑) Note 3	t_{SIK2}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V		1/f_{MCK} + 40		ns
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2		1/f_{MCK} + 60		ns
SIp hold time (from SCKp↑) Note 4	t_{KSI2}			1/f_{MCK} + 62		ns
Delay time from SCKp↓ to SOp output Note 5	t_{KSO2}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V C_b = 30 pF, R_b = 2.7 kΩ			2/f_{MCK} + 428	ns
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2 C_b = 30 pF, R_b = 5.5 kΩ			2/f_{MCK} + 1146	ns

(**Notes** and **Caution** are listed on the next page. **Remarks** are listed on the page after the next page.)

Note 1. Transfer rate in the SNOOZE mode: MAX. 1 Mbps

Note 2. Use it with $V_{DD} \geq V_b$.

Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes “to SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

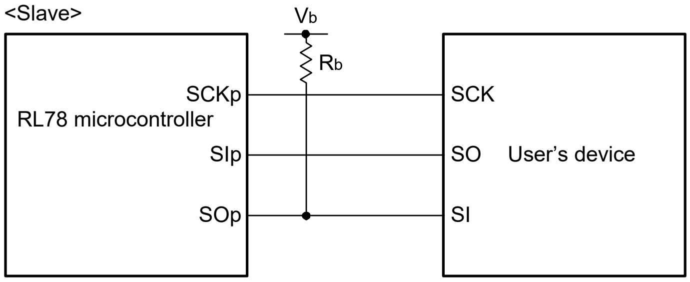
Note 4. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes “from SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 5. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes “from SCKp↑” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Caution **Select the TTL input buffer for the SIp pin and SCKp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.**

(**Remarks** are listed on the next page.)

Simplified SPI (CSI) mode connection diagram (during communication at different potential)

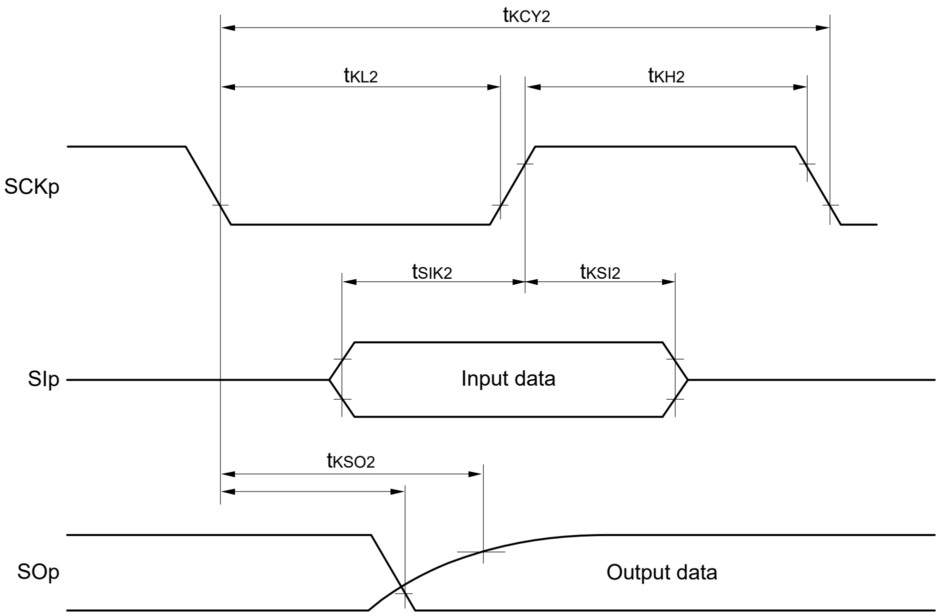


Remark 1. R_b[Ω]: Communication line (SOp) pull-up resistance, C_b[F]: Communication line (SOp) load capacitance, V_b[V]: Communication line voltage

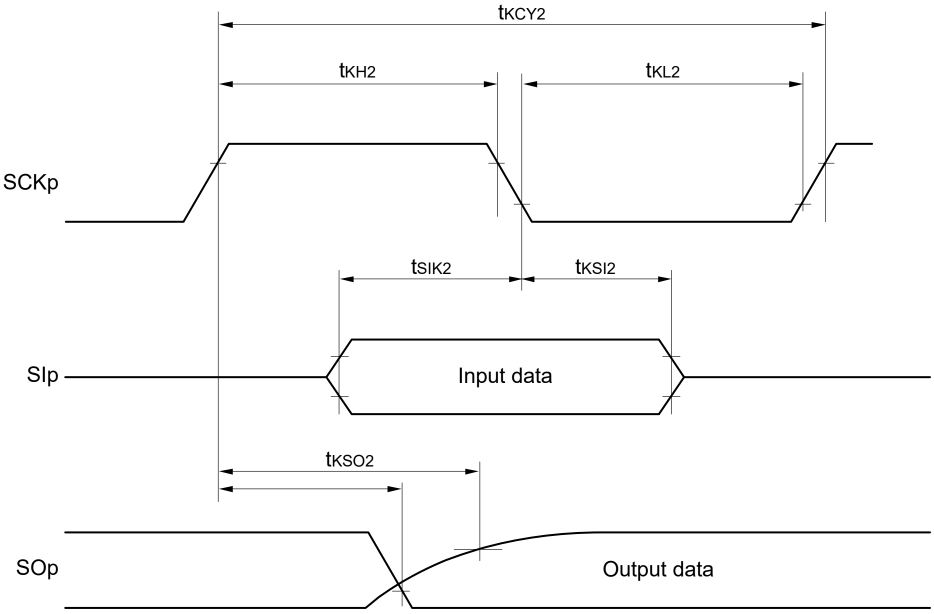
Remark 2. p: CSI number (p = 00, 01), m: Unit number (m = 0), n: Channel number (n = 0, 1), g: PIM and POM numbers (g = 5)

Remark 3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01))

Simplified SPI (CSI) mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



Simplified SPI (CSI) mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remark p: CSI number (p = 00, 01), m: Unit number (m = 0), n: Channel number (n = 0, 1), g: PIM and POM numbers (g = 5)

(10) Communication at different potential (1.8 V, 2.5 V) (simplified I²C mode)

(T_A = -40 to 85°C, 1.8 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LP (Low-power main) mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLr clock frequency	f_{SCL}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 50 pF, R_b = 2.7 kΩ		1000 Note 1		300 Note 1		250 Note 1		300 Note 1	kHz
		2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 100 pF, R_b = 2.7 kΩ		400 Note 1		300 Note 1		250 Note 1		300 Note 1	kHz
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2, C_b = 100 pF, R_b = 5.5 kΩ		300 Note 1		300 Note 1		250 Note 1		300 Note 1	kHz
Hold time when SCLr = "L"	t_{LOW}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 50 pF, R_b = 2.7 kΩ	475		1550		1550		1550		ns
		2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 100 pF, R_b = 2.7 kΩ	1150		1550		1550		1550		ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2, C_b = 100 pF, R_b = 5.5 kΩ	1550		1550		1550		1550		ns
Hold time when SCLr = "H"	t_{HIGH}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 50 pF, R_b = 2.7 kΩ	200		610		610		610		ns
		2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 100 pF, R_b = 2.7 kΩ	600		610		610		610		ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2, C_b = 100 pF, R_b = 5.5 kΩ	610		610		610		610		ns
Data setup time (reception)	$t_{SU:DAT}$	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 50 pF, R_b = 2.7 kΩ	1/f_{MCK} + 135 Note 3		1/f_{MCK} + 190 Note 2		1/f_{MCK} + 190 Note 3		1/f_{MCK} + 190 Note 3		ns
		2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 100 pF, R_b = 2.7 kΩ	1/f_{MCK} + 190 Note 3		1/f_{MCK} + 190 Note 3		1/f_{MCK} + 190 Note 3		1/f_{MCK} + 190 Note 3		ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2, C_b = 100 pF, R_b = 5.5 kΩ	1/f_{MCK} + 190 Note 3		1/f_{MCK} + 190 Note 3		1/f_{MCK} + 190 Note 3		1/f_{MCK} + 190 Note 3		ns
Data hold time (transmission)	$t_{HD:DAT}$	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 50 pF, R_b = 2.7 kΩ	0	305	0	305	0	305	0	305	ns
		2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 100 pF, R_b = 2.7 kΩ	0	355	0	355	0	355	0	355	ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2, C_b = 100 pF, R_b = 5.5 kΩ	0	405	0	405	0	405	0	405	ns

Note 1. The value must also be equal to or less than f_{MCK}/4.

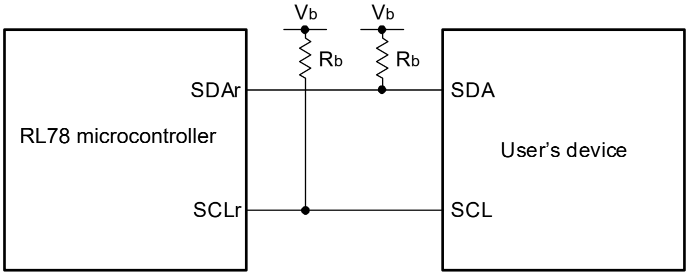
Note 2. Use it with V_{DD} ≥ V_b.

Note 3. Set the f_{MCK} value to keep the hold time of SCLr = "L" and SCLr = "H".

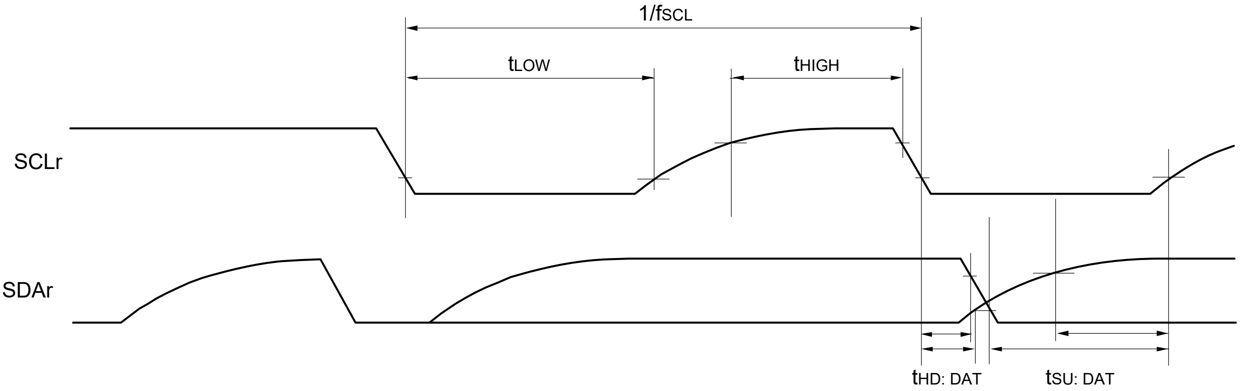
Caution **Select the TTL input buffer and the N-ch open drain output (V_{DD} tolerance) mode for the SDAr pin and the N-ch open drain output (V_{DD} tolerance) mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.**

(**Remarks** are listed on the next page.)

Simplified I²C mode connection diagram (during communication at different potential)



Simplified I²C mode serial transfer timing (during communication at different potential)



Remark 1. R_b[Ω]: Communication line (SDAr, SCLr) pull-up resistance, C_b[F]: Communication line (SDAr, SCLr) load capacitance, V_b[V]: Communication line voltage

Remark 2. r: IIC number (r = 00, 01), g: PIM, POM number (g = 5)

Remark 3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0),
n: Channel number (n = 0, 1), mn = 00, 01)

(10) Communication at different potential (1.8 V, 2.5 V) (simplified I^{2}C mode)

(T_A = +85 to 105°C, 2.4 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
SCLr clock frequency	f_{SCL}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 50 pF, R_b = 2.7 kΩ		400 $^{\text{Note 1}}$	kHz
		2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 100 pF, R_b = 2.7 kΩ		100 $^{\text{Note 1}}$	kHz
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V $^{\text{Note 2}}$, C_b = 100 pF, R_b = 5.5 kΩ		100 $^{\text{Note 1}}$	kHz
Hold time when SCLr = "L"	t_{LOW}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 50 pF, R_b = 2.7 kΩ	1200		ns
		2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 100 pF, R_b = 2.7 kΩ	4600		ns
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V $^{\text{Note 2}}$, C_b = 100 pF, R_b = 5.5 kΩ	4650		ns
Hold time when SCLr = "H"	t_{HIGH}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 50 pF, R_b = 2.7 kΩ	500		ns
		2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 100 pF, R_b = 2.7 kΩ	2400		ns
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V $^{\text{Note 2}}$, C_b = 100 pF, R_b = 5.5 kΩ	1830		ns
Data setup time (reception)	$t_{SU:DAT}$	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 50 pF, R_b = 2.7 kΩ	$1/f_{MCK}$ + 340 $^{\text{Note 3}}$		ns
		2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 100 pF, R_b = 2.7 kΩ	$1/f_{MCK}$ + 760 $^{\text{Note 3}}$		ns
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V $^{\text{Note 2}}$, C_b = 100 pF, R_b = 5.5 kΩ	$1/f_{MCK}$ + 570 $^{\text{Note 3}}$		ns
Data hold time (transmission)	$t_{HD:DAT}$	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 50 pF, R_b = 2.7 kΩ	0	770	ns
		2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 100 pF, R_b = 2.7 kΩ	0	1420	ns
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V $^{\text{Note 2}}$, C_b = 100 pF, R_b = 5.5 kΩ	0	1215	ns

Note 1. The value must also be equal to or less than $f_{MCK}/4$.

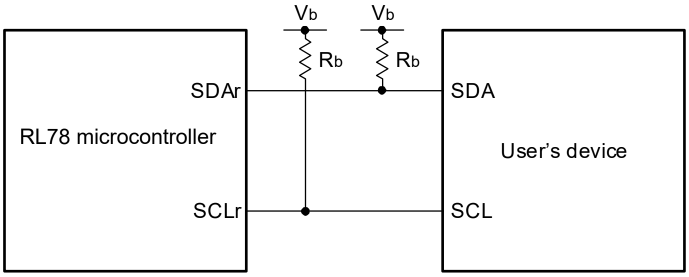
Note 2. Use it with V_{DD} ≥ V_b.

Note 3. Set the f_{MCK} value to keep the hold time of SCLr = "L" and SCLr = "H".

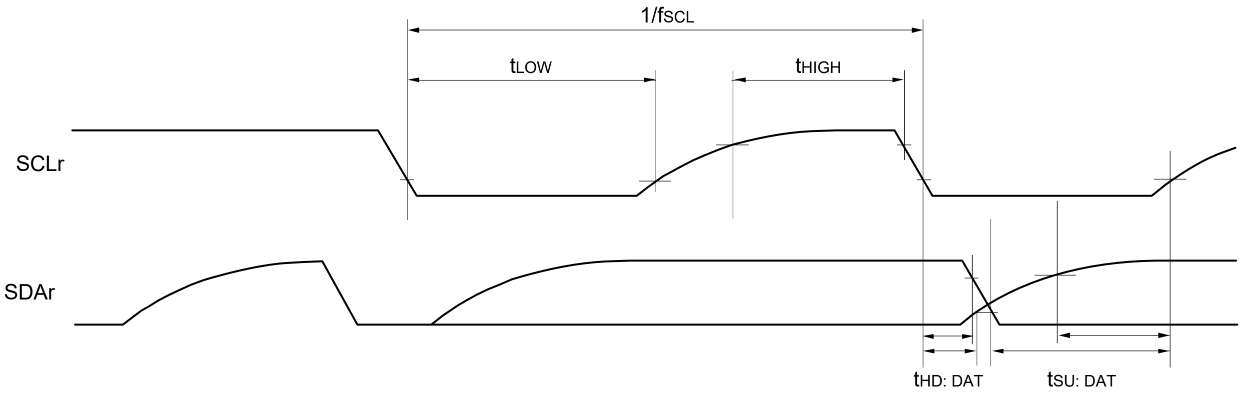
Caution **Select the TTL input buffer and the N-ch open drain output (V_{DD} tolerance) mode for the SDAr pin and the N-ch open drain output (V_{DD} tolerance) mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.**

(**Remarks** are listed on the next page.)

Simplified I^{2}C mode connection diagram (during communication at different potential)



Simplified I^{2}C mode serial transfer timing (during communication at different potential)



Remark 1. R_b[Ω]: Communication line (SDAr, SCLr) pull-up resistance, C_b[F]: Communication line (SDAr, SCLr) load capacitance, V_b[V]: Communication line voltage

Remark 2. r: IIC number (r = 00, 01), g: PIM and POM numbers (g = 5)

Remark 3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0),
n: Channel number (n = 0, 1), mn = 00, 01)

2.6 Analog Characteristics

2.6.1 A/D converter characteristics

Classification of A/D converter characteristics

Reference Voltage Input Channel	Reference voltage (+) = AVREFP Reference voltage (-) = AVREFM	Reference voltage (+) = AVDD Reference voltage (-) = AVSS	Reference voltage (+) = Internal reference voltage Reference voltage (-) = AVSS
High-accuracy channel; ANI0 to ANI13 (input buffer power supply: AVDD)	Refer to **2.6.1 (1)**. Refer to **2.6.1 (7)**.	Refer to **2.6.1 (2)**. Refer to **2.6.1 (7)**.	Refer to **2.6.1 (5)**. Refer to **2.6.1 (10)**.
Standard channel; ANI16 to ANI18 (input buffer power supply: VDD)	Refer to **2.6.1 (3)**. Refer to **2.6.1 (8)**.	Refer to **2.6.1 (4)**. Refer to **2.6.1 (9)**.	
Internal reference voltage, Temperature sensor output voltage	Refer to **2.6.1 (3)**. Refer to **2.6.1 (8)**.	Refer to **2.6.1 (4)**. Refer to **2.6.1 (9)**.	—

(1) When reference voltage (+) = AVREFP/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), conversion target: ANI2 to ANI13

(TA = -40 to +85°C, 1.6 V ≤ AVREFP ≤ AVDD = VDD ≤ 3.6 V, VSS = 0 V, AVSS = 0 V, Reference voltage (+) = AVREFP, Reference voltage (-) = AVREFM = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES		2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V	8		12	bit
			1.8 V ≤ AVREFP ≤ AVDD ≤ 3.6 V	8		10 Note 1	
			1.6 V ≤ AVREFP ≤ AVDD ≤ 3.6 V	8 Note 2			
Overall error Note 3	AINL	12-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±6.0	LSB
		10-bit resolution	1.8 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±5.0	
		8-bit resolution	1.6 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±2.5	
Conversion time	tCONV	ADTYP = 0, 12-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V	3.375			μs
		ADTYP = 0, 10-bit resolution Note 1	1.8 V ≤ AVREFP ≤ AVDD ≤ 3.6 V	6.75			
		ADTYP = 0, 8-bit resolution Note 2	1.6 V ≤ AVREFP ≤ AVDD ≤ 3.6 V	13.5			
		ADTYP = 1, 8-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V	2.5625			
			1.8 V ≤ AVREFP ≤ AVDD ≤ 3.6 V	5.125			
			1.6 V ≤ AVREFP ≤ AVDD ≤ 3.6 V	10.25			
Zero-scale error Note 3	EZS	12-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±4.5	LSB
		10-bit resolution	1.8 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±4.5	
		8-bit resolution	1.6 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±2.0	
Full-scale error Note 3	EFS	12-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±4.5	LSB
		10-bit resolution	1.8 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±4.5	
		8-bit resolution	1.6 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±2.0	
Integral linearity error Note 3	ILE	12-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±2.0	LSB
		10-bit resolution	1.8 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±1.5	
		8-bit resolution	1.6 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±1.0	
Differential linearity error Note 3	DLE	12-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±1.5	LSB
		10-bit resolution	1.8 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±1.5	
		8-bit resolution	1.6 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±1.0	
Analog input voltage	VAIN			0		AVREFP	V

Note 1. Cannot be used for lower 2 bit of ADCR register

Note 2. Cannot be used for lower 4 bit of ADCR register

Note 3. Excludes quantization error (±1/2 LSB).

Caution Always use AVDD pin with the same potential as the VDD pin.

(2) When reference voltage (+) = AVDD (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = AVSS (ADREFM = 0), conversion target: ANI0 to ANI13

(TA = -40 to +85°C, 1.6 V ≤ AVDD = VDD ≤ 3.6 V, VSS = 0 V, AVSS = 0 V, Reference voltage (+) = AVDD, Reference voltage (-) = AVSS = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES		2.4 V ≤ AVDD ≤ 3.6 V	8		12	bit
			1.8 V ≤ AVDD ≤ 3.6 V	8		10 Note 1	
			1.6 V ≤ AVDD ≤ 3.6 V	8 Note 2			
Overall error Note 3	AINL	12-bit resolution	2.4 V ≤ AVDD ≤ 3.6 V			±7.5	LSB
		10-bit resolution	1.8 V ≤ AVDD ≤ 3.6 V			±5.5	
		8-bit resolution	1.6 V ≤ AVDD ≤ 3.6 V			±3.0	
Conversion time	tCONV	ADTYP = 0, 12-bit resolution	2.4 V ≤ AVDD ≤ 3.6 V	3.375			μs
		ADTYP = 0, 10-bit resolution Note 1	1.8 V ≤ AVDD ≤ 3.6 V	6.75			
		ADTYP = 0, 8-bit resolution Note 2	1.6 V ≤ AVDD ≤ 3.6 V	13.5			
		ADTYP = 1, 8-bit resolution	2.4 V ≤ AVDD ≤ 3.6 V	2.5625			
			1.8 V ≤ AVDD ≤ 3.6 V	5.125			
			1.6 V ≤ AVDD ≤ 3.6 V	10.25			
Zero-scale error Note 3	EZS	12-bit resolution	2.4 V ≤ AVDD ≤ 3.6 V			±6.0	LSB
		10-bit resolution	1.8 V ≤ AVDD ≤ 3.6 V			±5.0	
		8-bit resolution	1.6 V ≤ AVDD ≤ 3.6 V			±2.5	
Full-scale error Note 3	EFS	12-bit resolution	2.4 V ≤ AVDD ≤ 3.6 V			±6.0	LSB
		10-bit resolution	1.8 V ≤ AVDD ≤ 3.6 V			±5.0	
		8-bit resolution	1.6 V ≤ AVDD ≤ 3.6 V			±2.5	
Integral linearity error Note 3	ILE	12-bit resolution	2.4 V ≤ AVDD ≤ 3.6 V			±3.0	LSB
		10-bit resolution	1.8 V ≤ AVDD ≤ 3.6 V			±2.0	
		8-bit resolution	1.6 V ≤ AVDD ≤ 3.6 V			±1.5	
Differential linearity error Note 3	DLE	12-bit resolution	2.4 V ≤ AVDD ≤ 3.6 V			±2.0	LSB
		10-bit resolution	1.8 V ≤ AVDD ≤ 3.6 V			±2.0	
		8-bit resolution	1.6 V ≤ AVDD ≤ 3.6 V			±1.5	
Analog input voltage	VAIN	ANI0 to ANI6		0		AVDD	V

Note 1. Cannot be used for lower 2 bit of ADCR register

Note 2. Cannot be used for lower 4 bit of ADCR register

Note 3. Excludes quantization error (±1/2 LSB).

Caution Always use AVDD pin with the same potential as the VDD pin.

(3) When reference voltage (+) = AVREFP/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), conversion target: ANI16 to ANI18, internal reference voltage, temperature sensor output voltage

(TA = -40 to +85°C, 1.6 V ≤ VDD ≤ 3.6 V, 1.6 V ≤ AVREFP ≤ AVDD = VDD ≤ 3.6 V, VSS = 0 V, AVSS = 0 V, Reference voltage (+) = AVREFP, Reference voltage (-) = AVREFM = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES		2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V	8		12	bit
			1.8 V ≤ AVREFP ≤ AVDD ≤ 3.6 V	8		10 Note 1	
			1.6 V ≤ AVREFP ≤ AVDD ≤ 3.6 V	8 Note 2			
Overall error Note 3	AINL	12-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±7.0	LSB
		10-bit resolution	1.8 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±5.5	
		8-bit resolution	1.6 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±3.0	
Conversion time	tCONV	ADTYP = 0, 12-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V	4.125			μs
		ADTYP = 0, 10-bit resolution Note 1	1.8 V ≤ AVREFP ≤ AVDD ≤ 3.6 V	9.5			
		ADTYP = 0, 8-bit resolution Note 2	1.6 V ≤ AVREFP ≤ AVDD ≤ 3.6 V	57.5			
		ADTYP = 1, 8-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V	3.3125			
			1.8 V ≤ AVREFP ≤ AVDD ≤ 3.6 V	7.875			
			1.6 V ≤ AVREFP ≤ AVDD ≤ 3.6 V	54.25			
Zero-scale error Note 3	EZS	12-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±5.0	LSB
		10-bit resolution	1.8 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±5.0	
		8-bit resolution	1.6 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±2.5	
Full-scale error Note 3	EFS	12-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±5.0	LSB
		10-bit resolution	1.8 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±5.0	
		8-bit resolution	1.6 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±2.5	
Integral linearity error Note 3	ILE	12-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±3.0	LSB
		10-bit resolution	1.8 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±2.0	
		8-bit resolution	1.6 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±1.5	
Differential linearity error Note 3	DLE	12-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±2.0	LSB
		10-bit resolution	1.8 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±2.0	
		8-bit resolution	1.6 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±1.5	
Analog input voltage	VAIN			0		AVREFP	V
		Internal reference voltage (1.8 V ≤ VDD ≤ 3.6 V)		VBGR Note 4			
		Temperature sensor output voltage (1.8 V ≤ VDD ≤ 3.6 V)		VTMP25 Note 4			

Note 1. Cannot be used for lower 2 bits of ADCR register

Note 2. Cannot be used for lower 4 bits of ADCR register

Note 3. Excludes quantization error (±1/2 LSB).

Note 4. Refer to **2.6.2 Temperature sensor, internal reference voltage output characteristics**.

Caution Always use AVDD pin with the same potential as the VDD pin.

(4) When reference voltage (+) = AVDD (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = AVSS (ADREFM = 0), conversion target: ANI16 to ANI18, internal reference voltage, temperature sensor output voltage

(TA = -40 to +85°C, 1.6 V ≤ AVDD = VDD ≤ 3.6 V, VSS = 0 V, AVSS = 0 V, Reference voltage (+) = AVDD, Reference voltage (-) = AVSS = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES		2.4 V ≤ AVDD ≤ 3.6 V	8		12	bit
			1.8 V ≤ AVDD ≤ 3.6 V	8		10 Note 1	
			1.6 V ≤ AVDD ≤ 3.6 V	8 Note 2			
Overall error Note 3	AINL	12-bit resolution	2.4 V ≤ AVDD ≤ 3.6 V			±8.5	LSB
		10-bit resolution	1.8 V ≤ AVDD ≤ 3.6 V			±6.0	
		8-bit resolution	1.6 V ≤ AVDD ≤ 3.6 V			±3.5	
Conversion time	tCONV	ADTYP = 0, 12-bit resolution	2.4 V ≤ AVDD ≤ 3.6 V	4.125			μs
		ADTYP = 0, 10-bit resolution Note 1	1.8 V ≤ AVDD ≤ 3.6 V	9.5			
		ADTYP = 0, 8-bit resolution Note 2	1.6 V ≤ AVDD ≤ 3.6 V	57.5			
		ADTYP = 1, 8-bit resolution	2.4 V ≤ AVDD ≤ 3.6 V	3.3125			
			1.8 V ≤ AVDD ≤ 3.6 V	7.875			
			1.6 V ≤ AVDD ≤ 3.6 V	54.25			
Zero-scale error Note 3	EZS	12-bit resolution	2.4 V ≤ AVDD ≤ 3.6 V			±8.0	LSB
		10-bit resolution	1.8 V ≤ AVDD ≤ 3.6 V			±5.5	
		8-bit resolution	1.6 V ≤ AVDD ≤ 3.6 V			±3.0	
Full-scale error Note 3	EFS	12-bit resolution	2.4 V ≤ AVDD ≤ 3.6 V			±8.0	LSB
		10-bit resolution	1.8 V ≤ AVDD ≤ 3.6 V			±5.5	
		8-bit resolution	1.6 V ≤ AVDD ≤ 3.6 V			±3.0	
Integral linearity error Note 3	ILE	12-bit resolution	2.4 V ≤ AVDD ≤ 3.6 V			±3.5	LSB
		10-bit resolution	1.8 V ≤ AVDD ≤ 3.6 V			±2.5	
		8-bit resolution	1.6 V ≤ AVDD ≤ 3.6 V			±1.5	
Differential linearity error Note 3	DLE	12-bit resolution	2.4 V ≤ AVDD ≤ 3.6 V			±2.5	LSB
		10-bit resolution	1.8 V ≤ AVDD ≤ 3.6 V			±2.5	
		8-bit resolution	1.6 V ≤ AVDD ≤ 3.6 V			±2.0	
Analog input voltage	VAIN			0		AVDD	V
		Internal reference voltage (1.8 V ≤ VDD ≤ 3.6 V)		VBGR Note 4			
		Temperature sensor output voltage (1.8 V ≤ VDD ≤ 3.6 V)		VTMP25 Note 4			

Note 1. Cannot be used for lower 2 bits of ADCR register

Note 2. Cannot be used for lower 4 bits of ADCR register

Note 3. Excludes quantization error (±1/2 LSB).

Note 4. Refer to **2.6.2 Temperature sensor, internal reference voltage output characteristics**.

Caution Always use AVDD pin with the same potential as the VDD pin.

(5) When reference voltage (+) = Internal reference voltage (1.45 V) (ADREFP1 = 1, ADREFP0 = 0), reference voltage (-) = AVSS (ADREFM = 0), conversion target: ANI0 to ANI13, ANI16 to ANI18

(TA = -40 to +85°C, 1.8 V ≤ AVDD = VDD ≤ 3.6 V, VSS = 0 V, AVSS = 0 V, Reference voltage (+) = internal reference voltage, Reference voltage (-) = AVSS = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	RES		8			bit
Conversion time	tCONV	8-bit resolution	16			μs
Zero-scale error Note	EZS	8-bit resolution			±4.0	LSB
Integral linearity error Note	ILE	8-bit resolution			±2.0	LSB
Differential linearity error Note	DLE	8-bit resolution			±2.5	LSB
Analog input voltage	VAIN		0		VBGR	V

Note Excludes quantization error (±1/2 LSB).

Caution Always use AVDD pin with the same potential as the VDD pin.

(6) When reference voltage (+) = AVREFP/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), conversion target: ANI2 to ANI13

(TA = +85 to +105°C, 2.4 V ≤ AVREFP ≤ AVDD = VDD ≤ 3.6 V, VSS = 0 V, AVSS = 0 V, Reference voltage (+) = AVREFP, Reference voltage (-) = AVREFM = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES		2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V	8		12	bit
Overall error Note	AINL	12-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±6.0	LSB
Conversion time	tCONV	ADTYP = 0, 12-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V	3.375			μs
Zero-scale error Note	EZS	12-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±4.5	LSB
Full-scale error Note	EFS	12-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±4.5	LSB
Integral linearity error Note	ILE	12-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±2.0	LSB
Differential linearity error Note	DLE	12-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±1.5	LSB
Analog input voltage	VAIN			0		AVREFP	V

Note Excludes quantization error (±1/2 LSB).

Caution Always use AVDD pin with the same potential as the VDD pin.

(7) When reference voltage (+) = AV_{DD} (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = AV_{SS} (ADREFM = 0), conversion target: ANI0 to ANI13

(T_A = +85 to +105°C, 2.4 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = 0 V, AV_{SS} = 0 V, Reference voltage (+) = AV_{DD}, Reference voltage (-) = AV_{SS} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	R_{ES}		2.4 V ≤ AV_{DD} ≤ 3.6 V	8		12	bit
Overall error [Note]	AINL	12-bit resolution	2.4 V ≤ AV_{DD} ≤ 3.6 V			±7.5	LSB
Conversion time	t_{CONV}	ADTYP = 0, 12-bit resolution	2.4 V ≤ AV_{DD} ≤ 3.6 V	3.375			μs
Zero-scale error [Note]	E_{ZS}	12-bit resolution	2.4 V ≤ AV_{DD} ≤ 3.6 V			±6.0	LSB
Full-scale error [Note]	E_{FS}	12-bit resolution	2.4 V ≤ AV_{DD} ≤ 3.6 V			±6.0	LSB
Integral linearity error [Note]	ILE	12-bit resolution	2.4 V ≤ AV_{DD} ≤ 3.6 V			±3.0	LSB
Differential linearity error [Note]	DLE	12-bit resolution	2.4 V ≤ AV_{DD} ≤ 3.6 V			±2.0	LSB
Analog input voltage	V_{AIN}			0		AV_{DD}	V

Note Excludes quantization error (±1/2 LSB).

Caution **Always use AV_{DD} pin with the same potential as the V_{DD} pin.**

(8) When reference voltage (+) = AVREFP/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), conversion target ANI16 to ANI18, internal reference voltage, temperature sensor output voltage

(TA = +85 to +105°C, 2.4 V ≤ AVREFP ≤ AVDD = VDD ≤ 3.6 V, VSS = 0 V, AVSS = 0 V, Reference voltage (+) = AVREFP, Reference voltage (-) = AVREFM = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES		2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V	8		12	bit
Overall error Note 1	AINL	12-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±7.0	LSB
Conversion time	tCONV	ADTYP = 0, 12-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V	4.125			μs
Zero-scale error Note 1	EZS	12-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±5.0	LSB
Full-scale error Note 1	EFS	12-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±5.0	LSB
Integral linearity error Note 1	ILE	12-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±3.0	LSB
Differential linearity error Note 1	DLE	12-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±2.0	LSB
Analog input voltage	VAIN			0		AVREFP	V
		Internal reference voltage (2.4 V ≤ VDD ≤ 3.6 V)		VBGR Note 2			
		Temperature sensor output voltage (2.4 V ≤ VDD ≤ 3.6 V)		VTMP25 Note 2			

Note 1. Excludes quantization error (±1/2 LSB).

Note 2. Refer to **2.6.2 Temperature sensor, internal reference voltage output characteristics**.

Caution **Always use AVDD pin with the same potential as the VDD pin.**

(9) When reference voltage (+) = AVDD (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = AVSS (ADREFM = 0), conversion target: ANI16 to ANI18, internal reference voltage, temperature sensor output voltage

(TA = +85 to +105°C, 2.4 V ≤ AVDD = VDD ≤ 3.6 V, VSS = 0 V, AVSS = 0 V, Reference voltage (+) = AVDD, Reference voltage (-) = AVSS = 0)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES		2.4 V ≤ AVDD ≤ 3.6 V	8		12	bit
Overall error Note 1	AINL	12-bit resolution	2.4 V ≤ AVDD ≤ 3.6 V			±8.5	LSB
Conversion time	tCONV	ADTYP = 0, 12-bit resolution	2.4 V ≤ AVDD ≤ 3.6 V	4.125			μs
Zero-scale error Note 1	EZS	12-bit resolution	2.4 V ≤ AVDD ≤ 3.6 V			±8.0	LSB
Full-scale error Note 1	EFS	12-bit resolution	2.4 V ≤ AVDD ≤ 3.6 V			±8.0	LSB
Integral linearity error Note 1	ILE	12-bit resolution	2.4 V ≤ AVDD ≤ 3.6 V			±3.5	LSB
Differential linearity error Note 1	DLE	12-bit resolution	2.4 V ≤ AVDD ≤ 3.6 V			±2.5	LSB
Analog input voltage	VAIN			0		AVDD	V
		Internal reference voltage (2.4 V ≤ VDD ≤ 3.6 V)		VBGR Note 2			
		Temperature sensor output voltage (2.4 V ≤ VDD ≤ 3.6 V)		VTMP25 Note 2			

Note 1. Excludes quantization error (±1/2 LSB).

Note 2. Refer to **2.6.2 Temperature sensor, internal reference voltage output characteristics**.

Caution Always use AVDD pin with the same potential as the VDD pin.

(10) When reference voltage (+) = Internal reference voltage (1.45 V) (ADREFP1 = 1, ADREFP0 = 0), reference voltage (-) = AVSS (ADREFM = 0), conversion target: ANI0 to ANI13, ANI16 to ANI18

(T_A = +85 to +105°C, 2.4 V ≤ V_{DD}, 2.4 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = 0 V, AV_{SS} = 0 V, Reference voltage (+) = internal reference voltage, Reference voltage (-) = AV_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	R_{ES}			8		bit
Conversion time	t_{CONV}	8-bit resolution	16.0			μs
Zero-scale error Note	E_{ZS}	8-bit resolution			±4.0	LSB
Integral linearity error Note	ILE	8-bit resolution			±2.0	LSB
Differential linearity error Note	DLE	8-bit resolution			±2.5	LSB
Analog input voltage	V_{AIN}		0		V_{BGR}	V

Note Excludes quantization error (±1/2 LSB).

Caution Always use AV_{DD} pin with the same potential as the V_{DD} pin.

2.6.2 Temperature sensor, internal reference voltage output characteristics

(T_A = -40 to 85°C, 1.8 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V)
(T_A = +85 to 105°C, 2.4 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	V_{TMPS25}	Setting ADS register = 80H, T_A = +25°C		1.05		V
Internal reference voltage	V_{BGR}	Setting ADS register = 81H	1.38	1.45	1.50	V
Temperature coefficient	F_{VTMPS}	Temperature sensor output voltage that depends on the temperature		-3.6		mV/°C
Operation stabilization wait time	t_{AMP}	2.4 V ≤ V_{DD} ≤ 3.6 V	5			μs
		1.8 V ≤ V_{DD} < 2.4 V	10			

2.6.3 Comparator

(T_A = -40 to +85°C, 1.6 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V)
(T_A = +85 to +105°C, 2.4 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Input voltage range	Ivref0	IVREF0 pin		0		V_{DD} - 1.4 Note	V
	Ivref1	IVREF1 pin		1.4 Note		V_{DD}	V
	Ivcmp	IVCMP0, IVCMP1 pins		-0.3		V_{DD} + 0.3	V
Output delay	td	AV_{DD} = 3.0 V Input slew rate > 50 mV/μs	Comparator high-speed mode, standard mode			1.2	μs
			Comparator high-speed mode, window mode			2.0	μs
			Comparator low-speed mode, standard mode		3.0		μs
			Comparator low-speed mode, window mode		4		μs
Operation stabilization wait time	t_{CMP}			100			μs

Note In window mode, make sure that Vref1 - Vref0 ≥ 0.2 V.

2.6.4 Operational amplifier characteristics

(T_A = -40 to +85°C, 1.8 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V)
(T_A = +85 to +105°C, 2.4 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Common mode input range	Vicm1	Low-power consumption mode		0.2		AV_{DD} - 0.5	V
	Vicm2	High-speed mode		0.3		AV_{DD} - 0.6	V
Output voltage range	Vo1	Low-power consumption mode		0.1		AV_{DD} - 0.1	V
	Vo2	High-speed mode		0.1		AV_{DD} - 0.1	V
Input offset voltage	Vioff			-10		10	mV
Open gain	Av			60	120		dB
Gain-bandwidth (GB) product	GBW1	Low-power consumption mode			0.04		MHz
	GBW2	High-speed mode			1.7		MHz
Phase margin	PM	CL = 20 pF		50			deg
Gain margin	GM	CL = 20 pF		10			dB
Equivalent input noise	Vnoise1	f = 1 kHz	Low-power consumption mode		230		nV/√Hz
	Vnoise2	f = 10 kHz			200		nV/√Hz
	Vnoise3	f = 1 kHz	High-speed mode		90		nV/√Hz
	Vnoise4	f = 2 kHz			70		nV/√Hz
Power supply reduction ratio	PSRR				90		dB
Common mode signal reduction ratio	CMRR				90		dB
Operation stabilization wait time	Tstd1	CL = 20 pF Only operational amplifier is activated [Note]	Low-power consumption mode	650			μs
	Tstd2		High-speed mode	13			μs
	Tstd3	CL = 20 pF Operational amplifier and reference current circuit are activated simultaneously	Low-power consumption mode	650			μs
	Tstd4		High-speed mode	13			μs
Settling time	Tset1	CL = 20 pF	Low-power consumption mode			750	μs
	Tset2		High-speed mode			13	μs
Slew rate	Tslew1	CL = 20 pF	Low-power consumption mode		0.02		V/μs
	Tslew2		High-speed mode		1.1		V/μs
Load current	Iload1	Low-power consumption mode		-100		100	μA
	Iload2	High-speed mode		-100		100	μA
Load capacitance	CL					20	pF

Note When the operational amplifier reference current circuit is activated in advance.

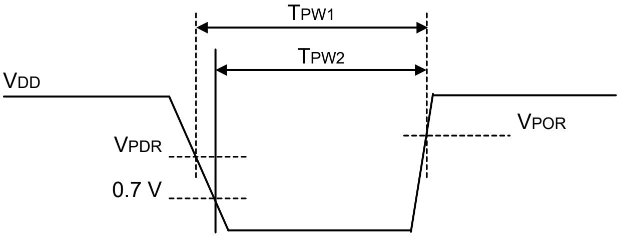
2.6.5 POR circuit characteristics

(T_A = -40 to +105°C, V_{SS} = AV_{SS} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Detection voltage	V_{POR}	The power supply voltage is rising.	T_A = -40 to +85°C	1.47	1.51	1.55	V
			T_A = +85 to +105°C	1.45	1.51	1.57	V
	V_{PDR}	The power supply voltage is falling. Note 1	T_A = -40 to +85°C	1.46	1.50	1.54	V
			T_A = +85 to +105°C	1.44	1.50	1.56	V
Minimum pulse width Note 2	T_{PW1}	Other than STOP/SUB HALT/SUB RUN	T_A = +40 to +105°C	300			μs
	T_{PW2}	STOP/SUB HALT/SUB RUN	T_A = +40 to +105°C	300			μs

Note 1. However, when the operating voltage falls while the LVD is off, enter STOP mode, or enable the reset status using the external reset pin before the voltage falls below the operating voltage range shown in 2.4 AC Characteristics.

Note 2. Minimum time required for a POR reset when V_{DD} exceeds below V_{PDR}. This is also the minimum time required for a POR reset from when V_{DD} exceeds below 0.7 V to when V_{DD} exceeds V_{POR} while STOP mode is entered or the main system clock is stopped through setting bit 0 (HIOSTOP) and bit 7 (MSTOP) in the clock operation status control register (CSC).



2.6.6 LVD circuit characteristics

(1) LVD Detection Voltage of Reset Mode and Interrupt Mode

(T_A = -40 to +85°C, $V_{PDR} \leq AV_{DD} = V_{DD} \leq 3.6$ V, $V_{SS} = AV_{SS} = 0$ V)

Parameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	Supply voltage level	V_{LVD2}	The power supply voltage is rising.	3.07	3.13	3.19	V
			The power supply voltage is falling.	3.00	3.06	3.12	V
		V_{LVD3}	The power supply voltage is rising.	2.96	3.02	3.08	V
			The power supply voltage is falling.	2.90	2.96	3.02	V
		V_{LVD4}	The power supply voltage is rising.	2.86	2.92	2.97	V
			The power supply voltage is falling.	2.80	2.86	2.91	V
		V_{LVD5}	The power supply voltage is rising.	2.76	2.81	2.87	V
			The power supply voltage is falling.	2.70	2.75	2.81	V
		V_{LVD6}	The power supply voltage is rising.	2.66	2.71	2.76	V
			The power supply voltage is falling.	2.60	2.65	2.70	V
		V_{LVD7}	The power supply voltage is rising.	2.56	2.61	2.66	V
			The power supply voltage is falling.	2.50	2.55	2.60	V
		V_{LVD8}	The power supply voltage is rising.	2.45	2.50	2.55	V
			The power supply voltage is falling.	2.40	2.45	2.50	V
		V_{LVD9}	The power supply voltage is rising.	2.05	2.09	2.13	V
			The power supply voltage is falling.	2.00	2.04	2.08	V
		V_{LVD10}	The power supply voltage is rising.	1.94	1.98	2.02	V
			The power supply voltage is falling.	1.90	1.94	1.98	V
		V_{LVD11}	The power supply voltage is rising.	1.84	1.88	1.91	V
			The power supply voltage is falling.	1.80	1.84	1.87	V
		V_{LVD12}	The power supply voltage is rising.	1.74	1.77	1.81	V
			The power supply voltage is falling.	1.70	1.73	1.77	V
		V_{LVD13}	The power supply voltage is rising.	1.64	1.67	1.70	V
			The power supply voltage is falling.	1.60	1.63	1.66	V
Minimum pulse width		t_{LW}		300			μs
Detection delay time						300	μs

(T_A = +85 to +105°C, $V_{PDR} \leq AV_{DD} = V_{DD} \leq 3.6$ V, $V_{SS} = AV_{SS} = 0$ V)

Parameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	Supply voltage level	V_{LVD2}	The power supply voltage is rising.	3.01	3.13	3.25	V
			The power supply voltage is falling.	2.94	3.06	3.18	V
		V_{LVD3}	The power supply voltage is rising.	2.90	3.02	3.14	V
			The power supply voltage is falling.	2.85	2.96	3.07	V
		V_{LVD4}	The power supply voltage is rising.	2.81	2.92	3.03	V
			The power supply voltage is falling.	2.75	2.86	2.97	V
		V_{LVD5}	The power supply voltage is rising.	2.71	2.81	2.92	V
			The power supply voltage is falling.	2.64	2.75	2.86	V
		V_{LVD6}	The power supply voltage is rising.	2.61	2.71	2.81	V
			The power supply voltage is falling.	2.55	2.65	2.75	V
		V_{LVD7}	The power supply voltage is rising.	2.51	2.61	2.71	V
			The power supply voltage is falling.	2.45	2.55	2.65	V
Minimum pulse width		t_{LW}		300			μs
Detection delay time						300	μs

(2) LVD Detection Voltage of Interrupt & Reset Mode

(T_A = -40 to +85°C, $V_{PDR} \leq AV_{DD} = V_{DD} \leq 3.6$ V, $V_{SS} = AV_{SS} = 0$ V)

Parameter	Symbol	Conditions			MIN.	TYP.	MAX.	Unit
Interrupt and reset mode	V_{LVDA0}	V_{POC0}, V_{POC1}, V_{POC2} = 0, 0, 0, falling reset voltage			1.60	1.63	1.66	V
	V_{LVDA1}		LVIS0, LVIS1 = 1, 0	Rising release reset voltage	1.74	1.77	1.81	V
				Falling interrupt voltage	1.70	1.73	1.77	V
	V_{LVDA2}		LVIS0, LVIS1 = 0, 1	Rising release reset voltage	1.84	1.88	1.91	V
				Falling interrupt voltage	1.80	1.84	1.87	V
	V_{LVDA3}		LVIS0, LVIS1 = 0, 0	Rising release reset voltage	2.86	2.92	2.97	V
				Falling interrupt voltage	2.80	2.86	2.91	V
	V_{LVDB0}	V_{POC0}, V_{POC1}, V_{POC2} = 0, 0, 1, falling reset voltage			1.80	1.84	1.87	V
	V_{LVDB1}		LVIS0, LVIS1 = 1, 0	Rising release reset voltage	1.94	1.98	2.02	V
				Falling interrupt voltage	1.90	1.94	1.98	V
	V_{LVDB2}		LVIS0, LVIS1 = 0, 1	Rising release reset voltage	2.05	2.09	2.13	V
				Falling interrupt voltage	2.00	2.04	2.08	V
	V_{LVDB3}		LVIS0, LVIS1 = 0, 0	Rising release reset voltage	3.07	3.13	3.19	V
				Falling interrupt voltage	3.00	3.06	3.12	V
	V_{LVDC0}	V_{POC0}, V_{POC1}, V_{POC2} = 0, 1, 0, falling reset voltage			2.40	2.45	2.50	V
	V_{LVDC1}		LVIS0, LVIS1 = 1, 0	Rising release reset voltage	2.56	2.61	2.66	V
				Falling interrupt voltage	2.50	2.55	2.60	V
	V_{LVDC2}		LVIS0, LVIS1 = 0, 1	Rising release reset voltage	2.66	2.71	2.76	V
				Falling interrupt voltage	2.60	2.65	2.70	V
	V_{LVDD0}	V_{POC0}, V_{POC1}, V_{POC2} = 0, 1, 1, falling reset voltage			2.70	2.75	2.81	V
	V_{LVDD1}		LVIS0, LVIS1 = 1, 0	Rising release reset voltage	2.86	2.92	2.97	V
				Falling interrupt voltage	2.80	2.86	2.91	V
	V_{LVDD2}		LVIS0, LVIS1 = 0, 1	Rising release reset voltage	2.96	3.02	3.08	V
				Falling interrupt voltage	2.90	2.96	3.02	V

(T_A = +85 to +105°C, $V_{PDR} \leq AV_{DD} = V_{DD} \leq 3.6$ V, $V_{SS} = AV_{SS} = 0$ V)

Parameter	Symbol	Conditions			MIN.	TYP.	MAX.	Unit
Interrupt and reset mode	V_{LVDD0}	V_{POC0}, V_{POC1}, V_{POC2} = 0, 1, 1, falling reset voltage			2.64	2.75	2.86	V
	V_{LVDD1}		LVIS0, LVIS1 = 1, 0	Rising release reset voltage	2.81	2.92	3.03	V
				Falling interrupt voltage	2.75	2.86	2.97	V
	V_{LVDD2}		LVIS0, LVIS1 = 0, 1	Rising release reset voltage	2.90	3.02	3.14	V
				Falling interrupt voltage	2.85	2.96	3.07	V

2.6.7 Power supply voltage rising slope characteristics

(T_A = -40 to +105°C, $V_{SS} = AV_{SS} = 0$ V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power supply voltage rising slope	S_{VDD}				54	V/ms

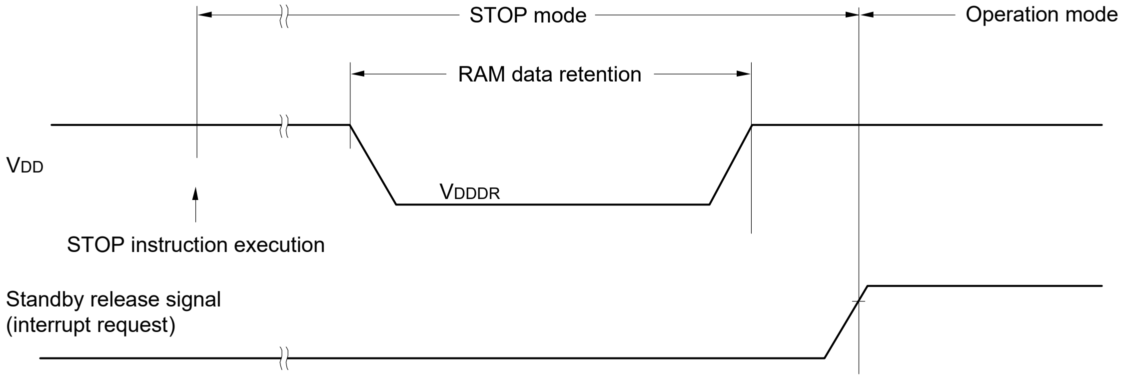
Caution **Make sure to keep the internal reset state by the LVD circuit or an external reset until V_{DD} reaches the operating voltage range shown in 2.4 AC Characteristics.**

2.7 RAM Data Retention Characteristics

(T_A = -40 to +85°C, 1.8 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V)
(T_A = +85 to +105°C, 2.4 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	V_{DDDR}	T_A = -40 to +85°C	1.46 Note		3.6	V
		T_A = +85 to +105°C	1.44 Note		3.6	V

Note The value depends on the POR detection voltage. When the voltage drops, the data is retained before a POR reset is effected, but data is not retained when a POR reset is effected.



2.8 Flash Memory Programming Characteristics

(T_A = -40 to +85°C, 1.8 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V)
(T_A = +85 to +105°C, 2.4 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
System clock frequency	f_{CLK}		1		24	MHz
Number of code flash rewrites Notes 1, 2, 3	C_{erwr}	Retained for 20 years T_A = 85°C Note 4	1,000			Times
Number of data flash rewrites Notes 1, 2, 3		Retained for 1 year T_A = 25°C Note 4		1,000,000		
		Retained for 5 years T_A = 85°C Note 4	100,000			
		Retained for 20 years T_A = 85°C Note 4	10,000			

Note 1. 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.

Note 2. When using flash memory programmer and Renesas Electronics self-programming library

Note 3. These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.

Note 4. This temperature is the average value at which data are retained.

2.9 Dedicated Flash Memory Programmer Communication (UART)

(T_A = -40 to +85°C, 1.8 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V)
(T_A = +85 to +105°C, 2.4 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115,200		1,000,000	bps

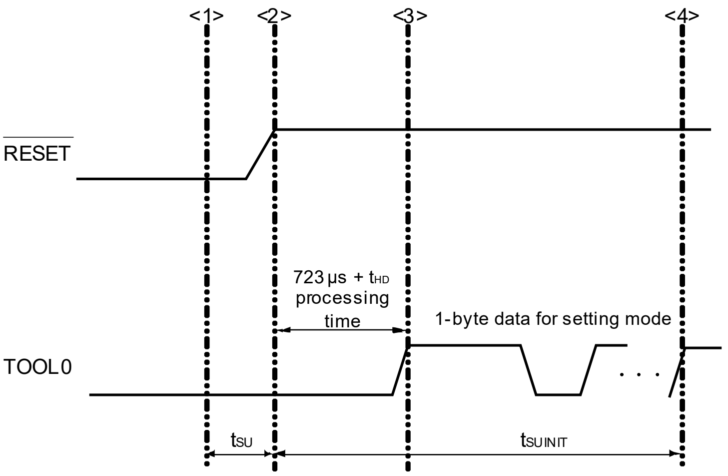
2.10 Timing of Entry to Flash Memory Programming Modes

(T_A = -40 to +85°C, 1.8 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V)
(T_A = +85 to +105°C, 2.4 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
How long from when an external reset ends until the initial communication settings are specified Note 1	t_{SUINIT}	POR and LVD reset must end before the external reset ends.			100	ms
How long from when the TOOL0 pin is placed at the low level until an external reset ends Note 1	t_{SU}	POR and LVD reset must end before the external reset ends.	10			μs
How long the TOOL0 pin must be kept at the low level after an external reset ends (excluding the processing time of the firmware to control the flash memory) Notes 1, 2	t_{HD}	POR and LVD reset must end before the external reset ends.	1			ms

Note 1. Deassertion of the POR and LVD reset signals must precede deassertion of the pin reset signal.

Note 2. This excludes the flash firmware processing time (723 μs).



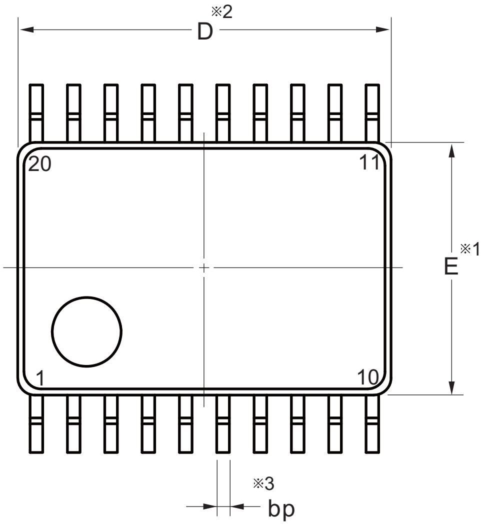
<1> The low level is input to the TOOL0 pin.
<2> The external reset ends (POR and LVD reset must end before the external reset ends).
<3> The TOOL0 pin is set to the high level.
<4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.

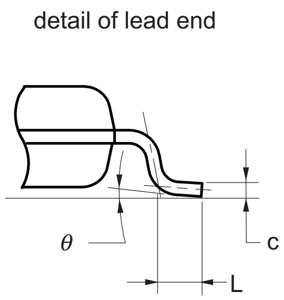
Remark t_{SUINIT}: The segment shows that it is necessary to finish specifying the initial communication settings within 100 ms from when the external resets end.
t_{SU}: How long from when the TOOL0 pin is placed at the low level until a pin reset ends
t_{HD}: How long to keep the TOOL0 pin at the low level from when the external resets end (excluding the processing time of the firmware to control the flash memory)

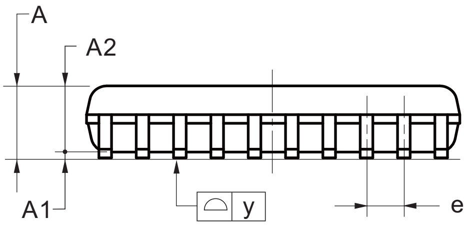
3. PACKAGE DRAWINGS

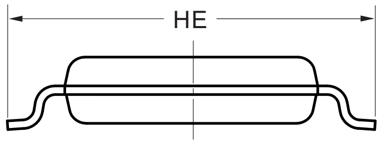
3.1 20-pin package

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LSSOP20-4.4x6.5-0.65	PLSP0020JB-A	P20MA-65-NAA-1	0.1









(UNIT:mm)

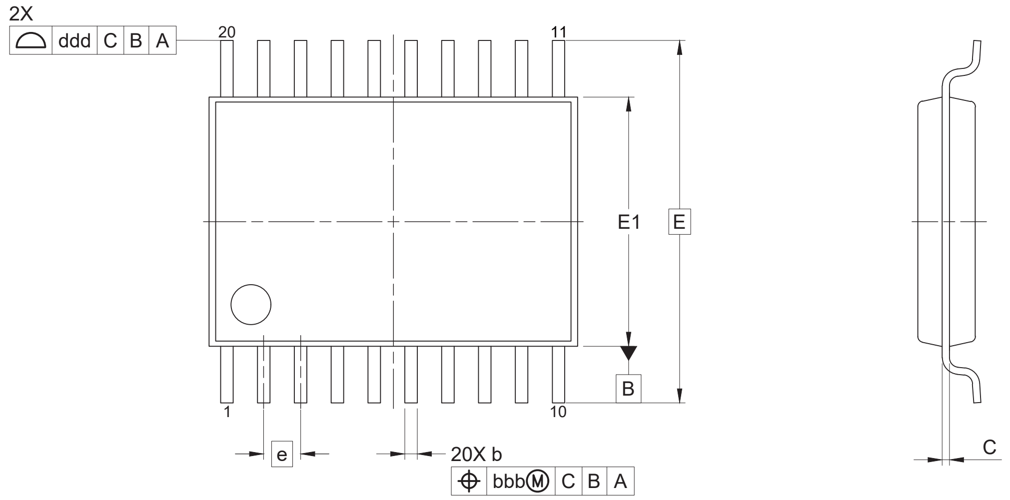
ITEM	DIMENSIONS
D	6.50±0.10
E	4.40±0.10
HE	6.40±0.20
A	1.45 MAX.
A1	0.10±0.10
A2	1.15
e	0.65±0.12
bp	$0.22^{+0.10}_{-0.05}$
c	$0.15^{+0.05}_{-0.02}$
L	0.50±0.20
y	0.10
θ	0° to 10°

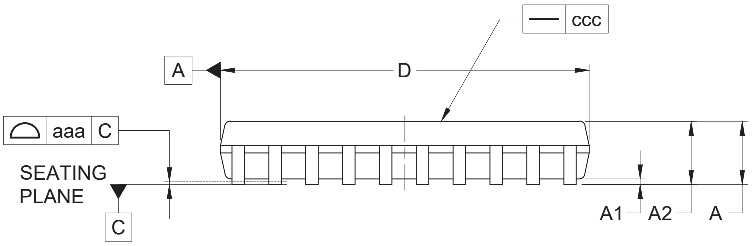
NOTE

1.Dimensions “※1” and “※2” do not include mold flash.

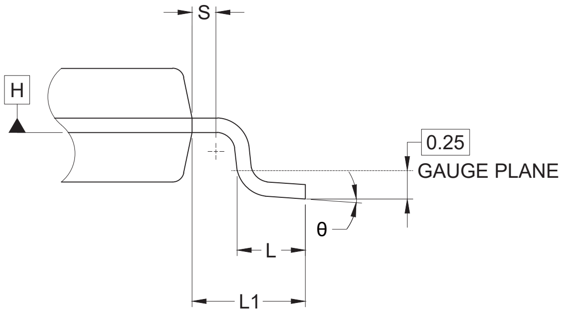
2.Dimension “※3” does not include trim offset.

JEITA Package code	RENESAS code	MASS(TYP.)[g]
P-TSSOP20-4.40x6.50-0.65	PTSP0020JI-A	0.08





Detail of Lead End

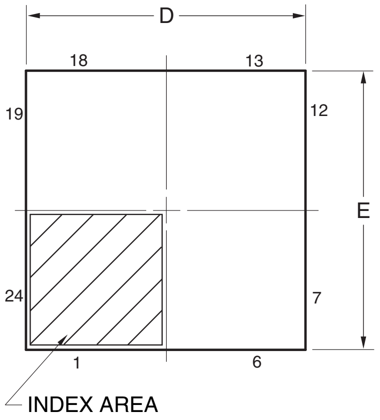


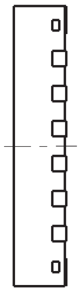
Reference Symbol	Dimension in Millimeters		
	Min.	Nom.	Max.
A	–	–	1.20
A1	0.05	–	0.15
A2	0.80	1.00	1.05
b	0.19	–	0.30
C	0.09	0.127	0.20
D	6.40	6.50	6.60
E1	4.30	4.40	4.50
E	6.40 BSC		
e	0.65 BSC		
L1	1.00 REF		
L	0.50	0.60	0.75
S	0.20	–	–
θ	0°	–	8°
aaa	0.10		
bbb	0.10		
ccc	0.05		
ddd	0.20		

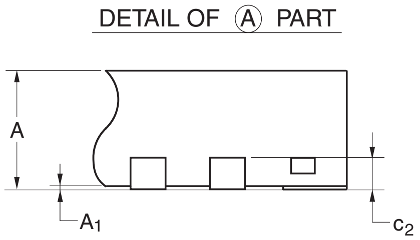
NOTES:
1.DIMENSION 'D' AND 'E1' DOES NOT INCLUDE MOLD FLASH.
2.DIMENSION 'b' DOES NOT INCLUDE TRIM OFFSET.
3.DIMENSION 'D' AND 'E1' TO BE DETERMINED AT DATUM PLANE H.

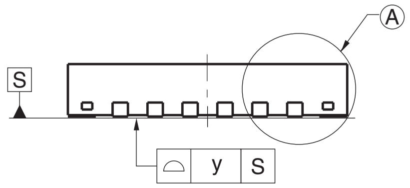
3.2 24-pin package

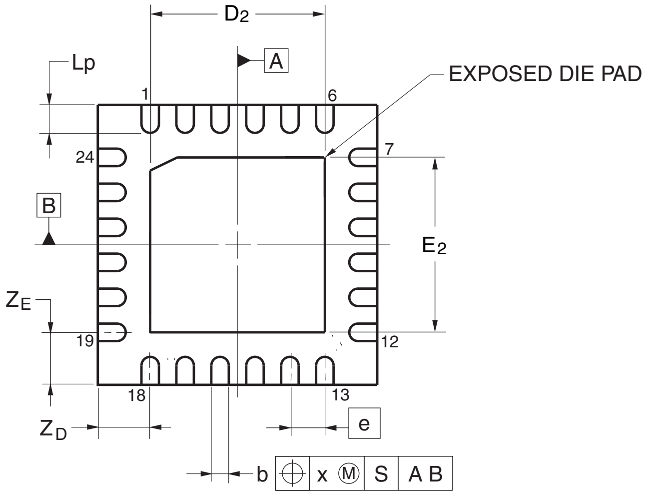
JEITA Package code	RENESAS code	Previous code	MASS(TYP.)[g]
P-HWQFN24-4x4-0.50	PWQN0024KE-A	P24K8-50-CAB-3	0.04





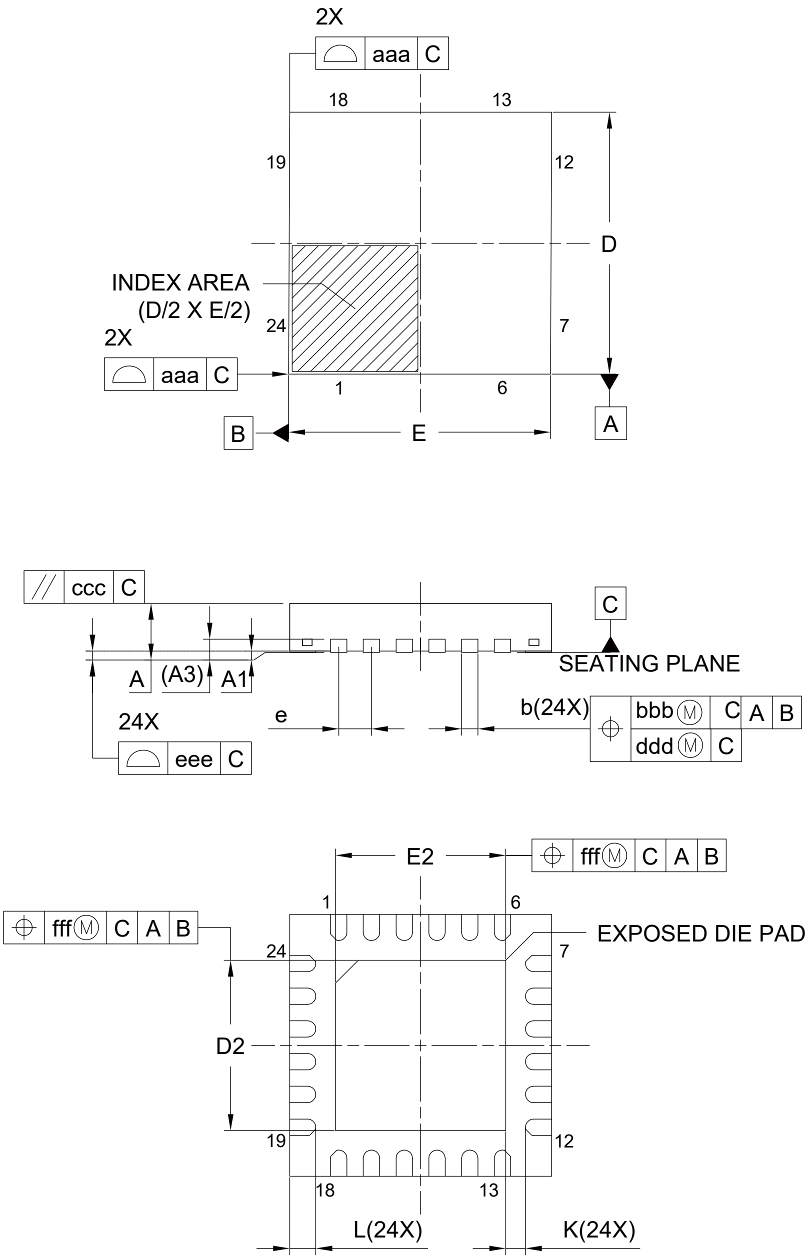






Referance Symbol	Dimension in Millimeters		
	Min	Nom	Max
D	3.95	4.00	4.05
E	3.95	4.00	4.05
A	—	—	0.80
A_1	0.00	—	—
b	0.18	0.25	0.30
e	—	0.50	—
Lp	0.30	0.40	0.50
x	—	—	0.05
y	—	—	0.05
Z_D	—	0.75	—
Z_E	—	0.75	—
c_2	0.15	0.20	0.25
D_2	—	2.50	—
E_2	—	2.50	—

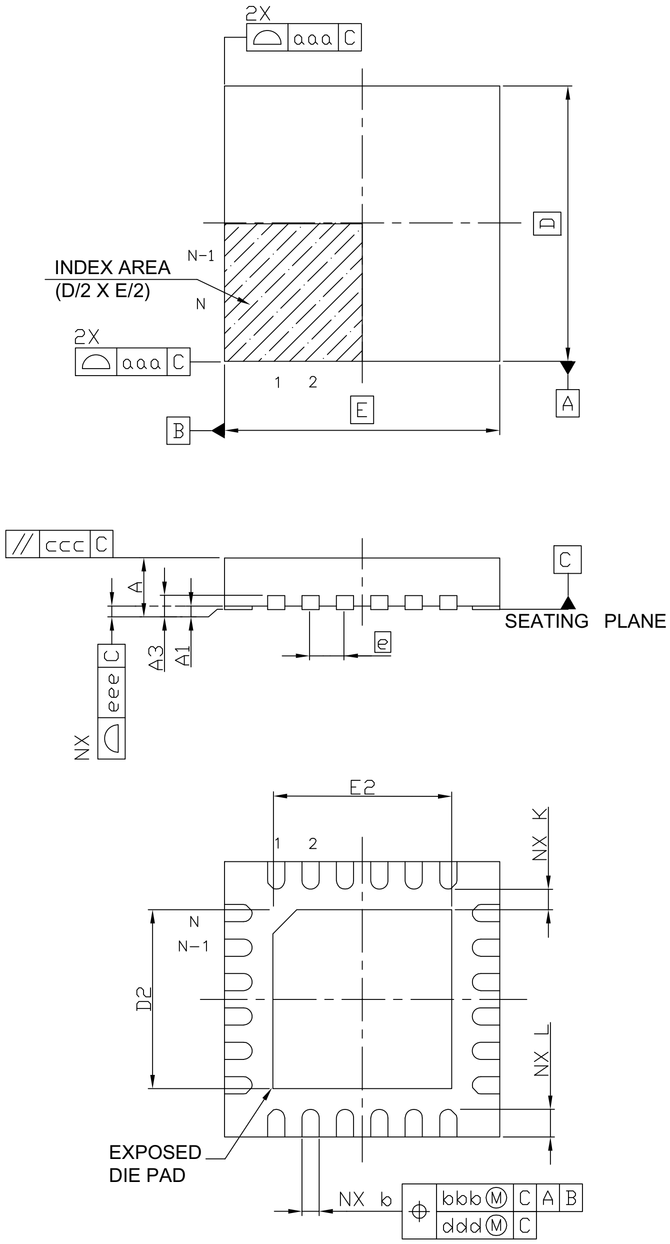
JEITA Package code	RENESAS code	MASS(TYP.)[g]
P-HWQFN024-4x4-0.50	PWQN0024KF-A	0.04



Reference Symbol	Dimension in Millimeters		
	Min.	Nom.	Max.
A	–	0.80	
A1	0.00	0.02	0.05
A3	0.203 REF.		
b	0.18	0.25	0.30
D	4.00 BSC		
E	4.00 BSC		
e	0.50 BSC		
L	0.35	0.40	0.45
K	0.20	–	–
D2	2.55	2.60	2.65
E2	2.55	2.60	2.65
aaa	0.15		
bbb	0.10		
ccc	0.10		
ddd	0.05		
eee	0.08		
fff	0.10		

<R>

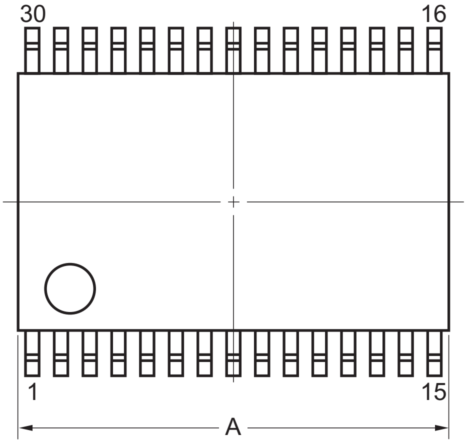
JEITA Package Code	RENESAS Code	MASS(Typ.)[g]
P-HWQFN24-4×4-0.50	PWQN0024KH-A	0.04



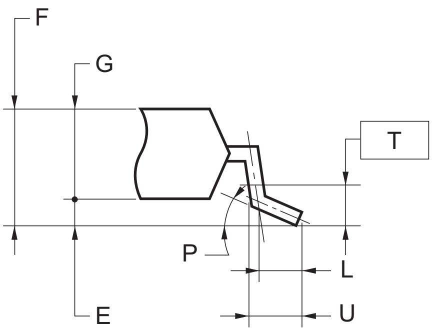
Reference Symbol	Dimension in Millimeters		
	Min.	Nom.	Max.
A	—	—	0.80
A_1	0.00	—	0.05
A_3	0.20 REF.		
b	0.20	0.25	0.30
D	—	4.00	—
E	—	4.00	—
e	—	0.50	—
N	24		
L	0.30	0.40	0.50
K	0.20	—	—
D_2	2.50	2.60	2.70
E_2	2.50	2.60	2.70
aaa	—	—	0.15
bbb	—	—	0.10
ccc	—	—	0.10
ddd	—	—	0.05
eee	—	—	0.08

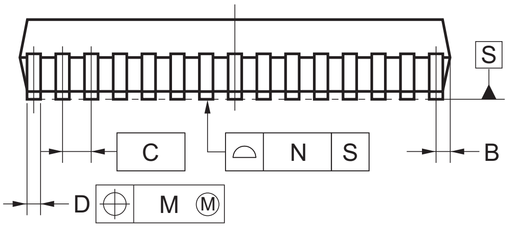
3.3 30-pin package

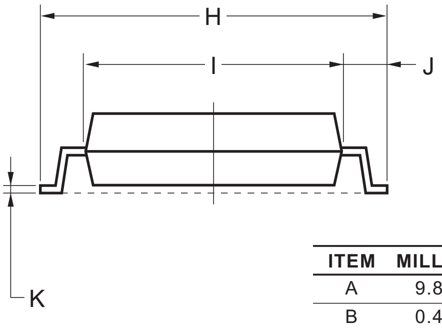
JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LSSOP30-0300-0.65	PLSP0030JB-B	S30MC-65-5A4-3	0.18



detail of lead end







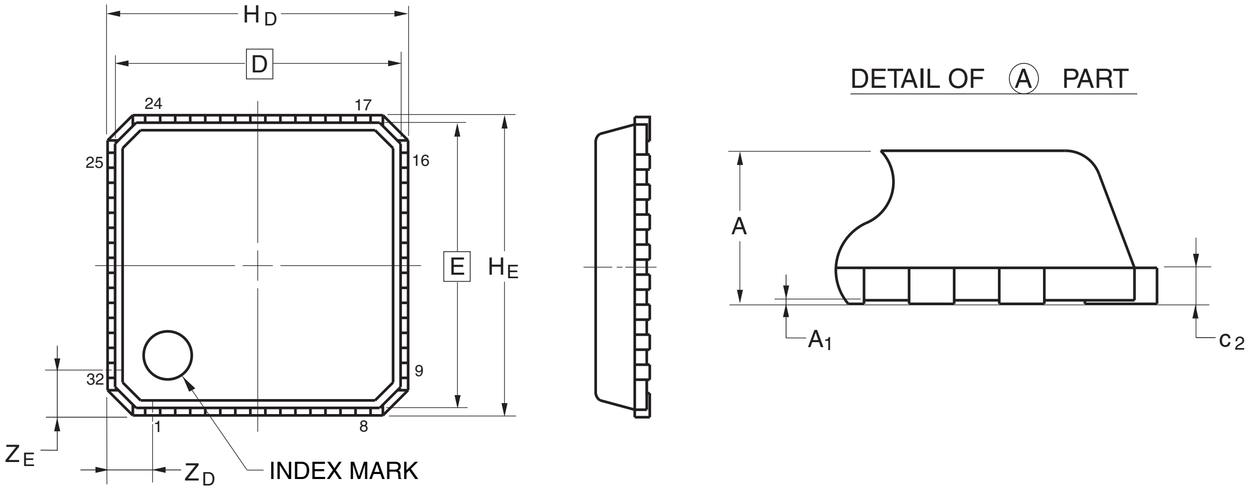
NOTE

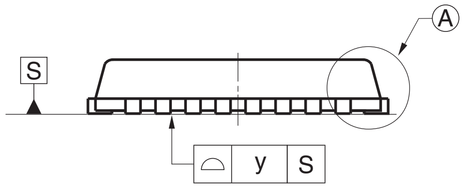
Each lead centerline is located within 0.13 mm of its true position (T.P.) at maximum material condition.

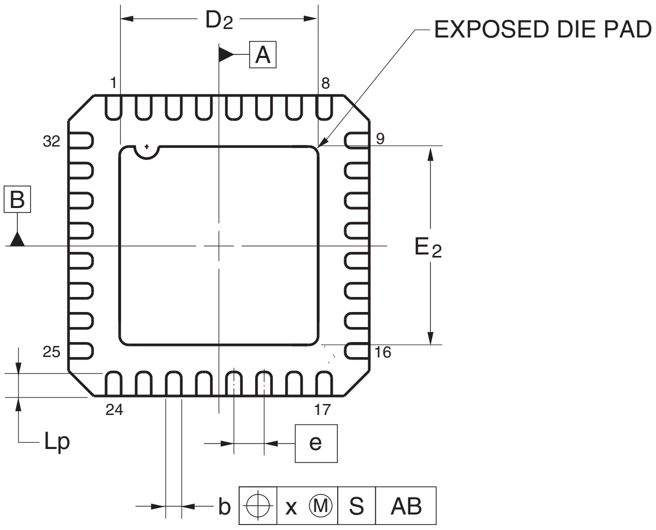
ITEM	MILLIMETERS
A	9.85±0.15
B	0.45 MAX.
C	0.65 (T.P.)
D	$0.24^{+0.08}_{-0.07}$
E	0.1±0.05
F	1.3±0.1
G	1.2
H	8.1±0.2
I	6.1±0.2
J	1.0±0.2
K	0.17±0.03
L	0.5
M	0.13
N	0.10
P	$3^{\circ}{}^{+5^{\circ}}_{-3^{\circ}}$
T	0.25
U	0.6±0.15

3.4 32-pin package

JEITA Package code	RENESAS code	Previous code	MASS(TYP.)[g]
P-HVQFN32-5x5-0.50	PVQN0032KE-A	P32K9-50B-BAH	0.058

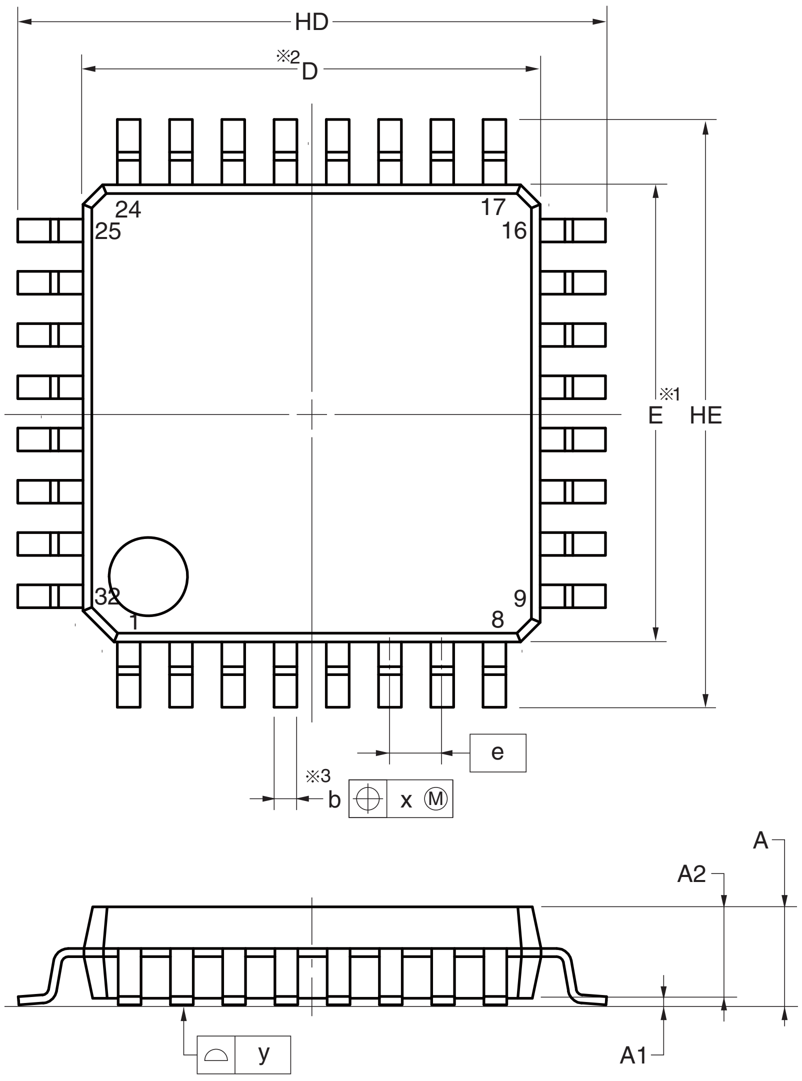


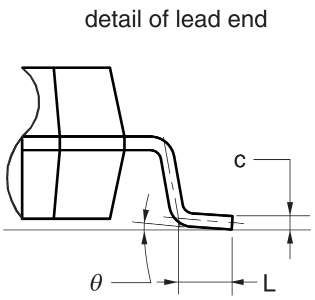




Referance Symbol	Dimension in Millimeters		
	Min	Nom	Max
D	—	4.75	—
E	—	4.75	—
A	—	—	0.90
A_1	0.00	—	—
b	0.20	0.25	0.30
e	—	0.50	—
Lp	0.30	0.40	0.50
x	—	—	0.10
y	—	—	0.05
H_D	4.95	5.00	5.05
H_E	4.95	5.00	5.05
Z_D	—	0.75	—
Z_E	—	0.75	—
c_2	0.19	0.20	0.21
D_2	—	3.30	—
E_2	—	3.30	—

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP32-7x7-0.80	PLQP0032GB-A	P32GA-80-GBT-1	0.2





(UNIT:mm)

ITEM	DIMENSIONS
D	7.00±0.10
E	7.00±0.10
HD	9.00±0.20
HE	9.00±0.20
A	1.70 MAX.
A1	0.10±0.10
A2	1.40
b	0.37±0.05
c	0.145±0.055
L	0.50±0.20
θ	0° to 8°
e	0.80
x	0.20
y	0.10

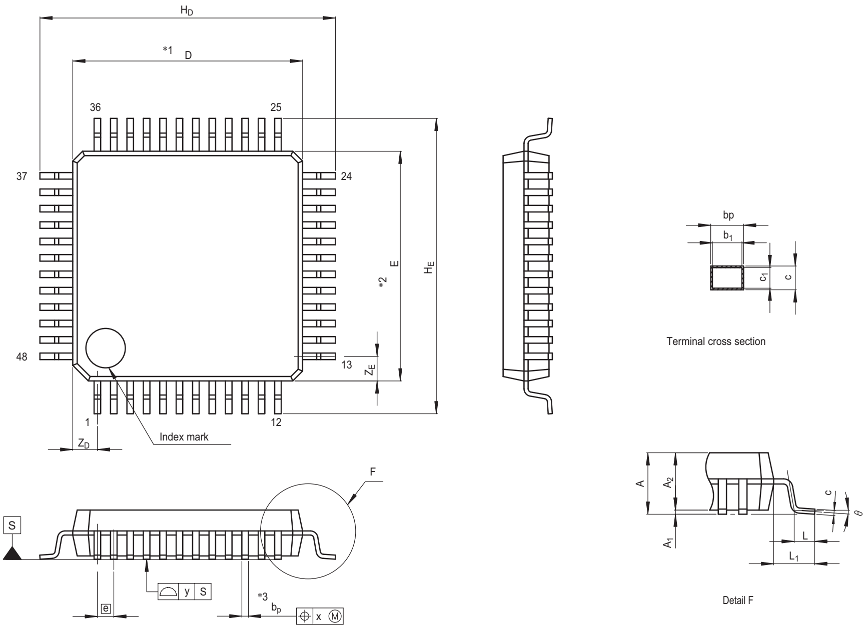
NOTE

1.Dimensions “※1” and “※2” do not include mold flash.

2.Dimension “※3” does not include trim offset.

3.5 48-pin package

JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
P-LFQFP48-7x7-0.50	PLQP0048KB-A	48P6Q-A	0.2g



NOTE)
1. DIMENSIONS "*1" AND "*2" DO NOT INCLUDE MOLD FLASH.
2. DIMENSION "*3" DOES NOT INCLUDE TRIM OFFSET.

Reference Symbol	Dimension in Millimeters		
	Min	Nom	Max
D	6.9	7.0	7.1
E	6.9	7.0	7.1
A_2	—	1.4	—
H_D	8.8	9.0	9.2
H_E	8.8	9.0	9.2
A	—	—	1.7
A_1	0	0.1	0.2
b_p	0.17	0.22	0.27
b_1	—	0.20	—
c	0.09	0.145	0.20
c_1	—	0.125	—
θ	0°	—	8°
e	—	0.5	—
x	—	—	0.08
y	—	—	0.10
Z_D	—	0.75	—
Z_E	—	0.75	—
L	0.35	0.5	0.65
L_1	—	1.0	—

REVISION HISTORY	RL78/I1D Datasheet

Rev.	Date	Description	
		Page	Summary
1.00	Aug 29, 2014	—	First Edition issued
2.00	Jan 16, 2015	24, 25, 27	Addition of note 7 in 2.3.2 Supply current characteristics
		24, 26	Addition of description in 2.3.2 Supply current characteristics
		26, 28	Modification of description in 2.3.2 Supply current characteristics
		28	Correction of error in 2.3.2 Supply current characteristics
		95	Modification of package drawing in 3.2 24-pin products
2.20	Feb 20, 2017	ALL	The function name changed from real-time clock to real-time clock 2
		5	Addition of product name in 1.3.1 20-pin products
		6	Addition of product name in 1.3.2 24-pin products
		7	Addition of product name in 1.3.3 30-pin products
		8	Addition of product name in 1.3.4 32-pin products
		9	Change of description and addition of product name in 1.3.4 32-pin products
		10	Addition of product name in 1.3.5 48-pin products
		13, 14	Change of description in 1.6 Outline of Functions
		16	Change of 2.1 Absolute Maximum Ratings
		22	Change of 2.3.1 Pin characteristics
		24	Change of conditions in 2.3.2 Supply current characteristics
		25, 27, 28	Change of note 1 in 2.3.2 Supply current characteristics
		26	Change of conditions and unit in 2.3.2 Supply current characteristics
		30	Change of note 3 in 2.3.2 Supply current characteristics
		31	Addition of note 5 in 2.3.2 Supply current characteristics
		92	Change of table in 2.8 Flash Memory Programming Characteristics
		92	Addition of note 4 in 2.8 Flash Memory Programming Characteristics
		99	Change of package drawing in 3.5 48-pin products
2.30	Jun 30, 2020	1	Change of description in 1.1 Features
		3	Change of Figure 1 - 1 Part Number, Memory Size, and Package of RL78/I1D and addition of note 1
		4	Change of table in 1.2 Ordering Information
		5	Change of description in 1.3.1 20-pin products
		93	Change of the figure in 2.10 Timing of Entry to Flash Memory Programming Modes
		95	Addition of package drawing in 3.1 20-pin package
		97	Addition of package drawing in 3.2 24-pin package
2.40	Mar 20, 2023	ALL	“3-wire serial” was modified to “simplified SPI”.
		2	1.1 Features: Note was added.
		5	1.2 Ordering Information: 24-pin RENESAS code was added.
		26	2.3.2 Supply current characteristics: Notes 1, 4, and 5 were modified.
		28	2.3.2 Supply current characteristics: Notes 1 and 5 were modified.
		29	2.3.2 Supply current characteristics: Note 1 was modified and note 2 was deleted.
		99	3.2 24-pin package: RENESAS code PWQN0024KH-A was added.

General Precautions in the Handling of Microprocessing Unit and Microcontroller Unit Products

The following usage notes are applicable to all Microprocessing unit and Microcontroller unit products from Renesas. For detailed usage notes on the products covered by this document, refer to the relevant sections of the document as well as any technical updates that have been issued for the products.

1. Precaution against Electrostatic Discharge (ESD)
   A strong electrical field, when exposed to a CMOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop the generation of static electricity as much as possible, and quickly dissipate it when it occurs. Environmental control must be adequate. When it is dry, a humidifier should be used. This is recommended to avoid using insulators that can easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors must be grounded. The operator must also be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions must be taken for printed circuit boards with mounted semiconductor devices.
2. Processing at power-on
   The state of the product is undefined at the time when power is supplied. The states of internal circuits in the LSI are indeterminate and the states of register settings and pins are undefined at the time when power is supplied. In a finished product where the reset signal is applied to the external reset pin, the states of pins are not guaranteed from the time when power is supplied until the reset process is completed. In a similar way, the states of pins in a product that is reset by an on-chip power-on reset function are not guaranteed from the time when power is supplied until the power reaches the level at which resetting is specified.
3. Input of signal during power-off state
   Do not input signals or an I/O pull-up power supply while the device is powered off. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Follow the guideline for input signal during power-off state as described in your product documentation.
4. Handling of unused pins
   Handle unused pins in accordance with the directions given under handling of unused pins in the manual. The input pins of CMOS products are generally in the high-impedance state. In operation with an unused pin in the open-circuit state, extra electromagnetic noise is induced in the vicinity of the LSI, an associated shoot-through current flows internally, and malfunctions occur due to the false recognition of the pin state as an input signal become possible.
5. Clock signals
   After applying a reset, only release the reset line after the operating clock signal becomes stable. When switching the clock signal during program execution, wait until the target clock signal is stabilized. When the clock signal is generated with an external resonator or from an external oscillator during a reset, ensure that the reset line is only released after full stabilization of the clock signal. Additionally, when switching to a clock signal produced with an external resonator or by an external oscillator while program execution is in progress, wait until the target clock signal is stable.
6. Voltage application waveform at input pin
   Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between V_{IL} (Max.) and V_{IH} (Min.) due to noise, for example, the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between V_{IL} (Max.) and V_{IH} (Min.).
7. Prohibition of access to reserved addresses
   Access to reserved addresses is prohibited. The reserved addresses are provided for possible future expansion of functions. Do not access these addresses as the correct operation of the LSI is not guaranteed.
8. Differences between products
   Before changing from one product to another, for example to a product with a different part number, confirm that the change will not lead to problems. The characteristics of a microprocessing unit or microcontroller unit products in the same group but having a different part number might differ in terms of internal memory capacity, layout pattern, and other factors, which can affect the ranges of electrical characteristics, such as characteristic values, operating margins, immunity to noise, and amount of radiated noise. When changing to a product with a different part number, implement a system-evaluation test for the given product.

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